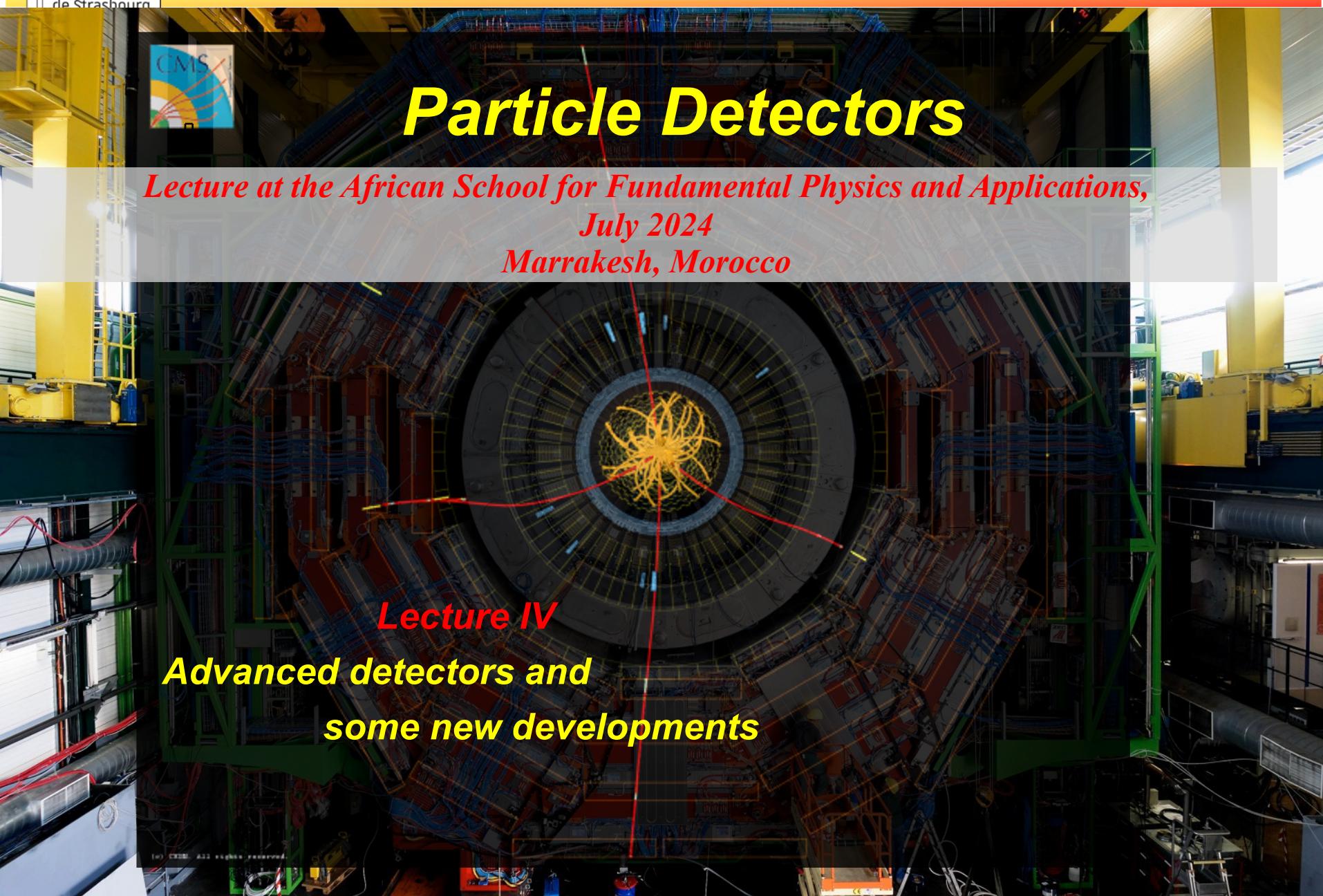


# Particle Detectors

*Lecture at the African School for Fundamental Physics and Applications,  
July 2024  
Marrakesh, Morocco*

**Lecture IV**  
**Advanced detectors and**  
**some new developments**



# Particle Detectors

*Lecture at the African School for Fundamental Physics  
Marrakesh, Morocco, July 2024*

Goal this lecture:

to discuss some examples

Looking at recent technological developments  
infinite number of ideas for new detectors

## Lecture IV

- LHC detectors
- Recent developments of CMOS pixel detectors
- Fast detectors for time of flight measurements
- High granularity calorimeters
- High purity segmented Ge-detectors for Nuclear physics
- A glimpse at cryogenic detectors for particle and astrophysics

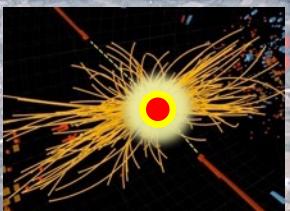
*Don't forget the Exercises!!!!*

# *The LHC*

Large Hadron Collider

*7 TeV protons + 7 TeV protons*

CMS



Large Hadron Collider

- Proton beams circulate 11,245 times/sec
- 100's of millions of proton-proton collisions/second
- 65 pp collisions every 25 ns
- new particles are created ( $E = mc^2$ )

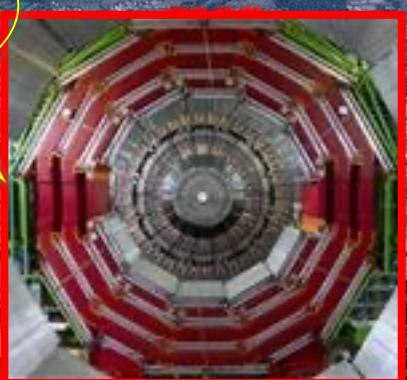
# The LHC

Large Hadron Collider

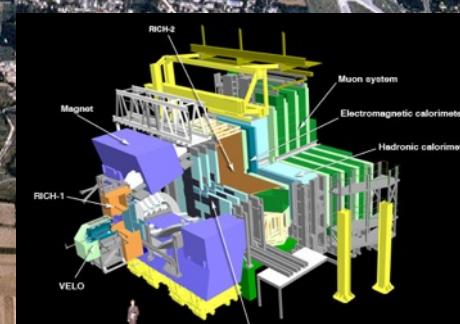
*7 TeV protons + 7 TeV protons*

**CMS**

- Protons circulate 11,245 times/sec
- 100's of millions of proton-proton collisions/second
- 65 pp collisions every 25 ns

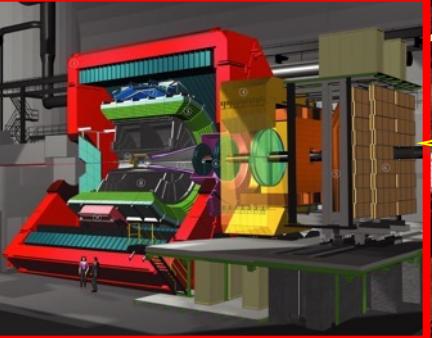


Large Hadron Collider

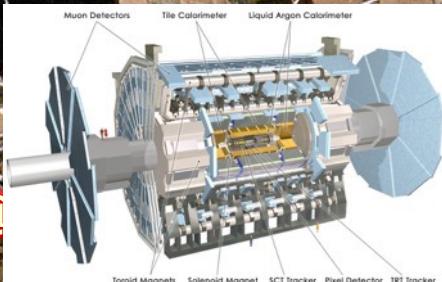


new particles are created ( $E = mc^2$ )

**ALICE**



CMS Centre @

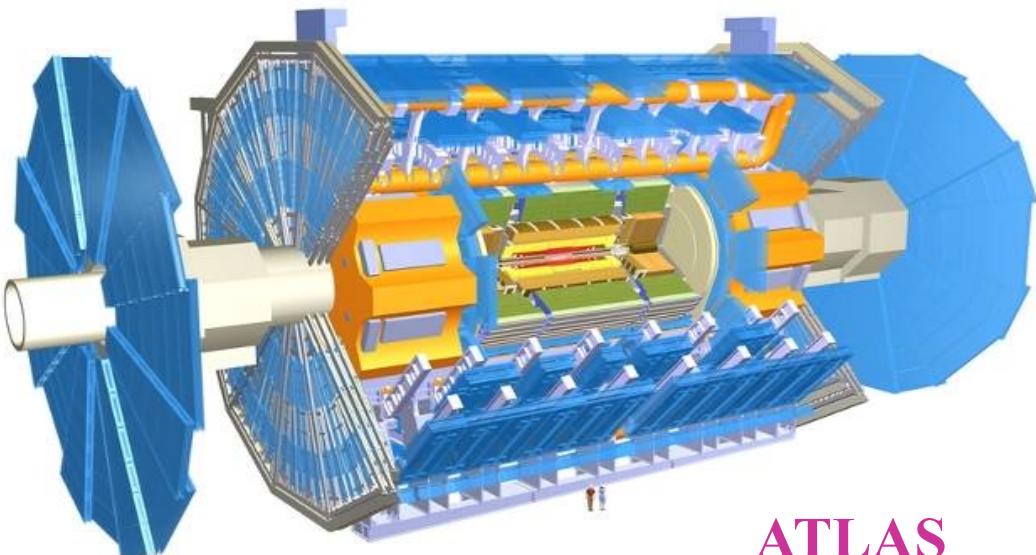
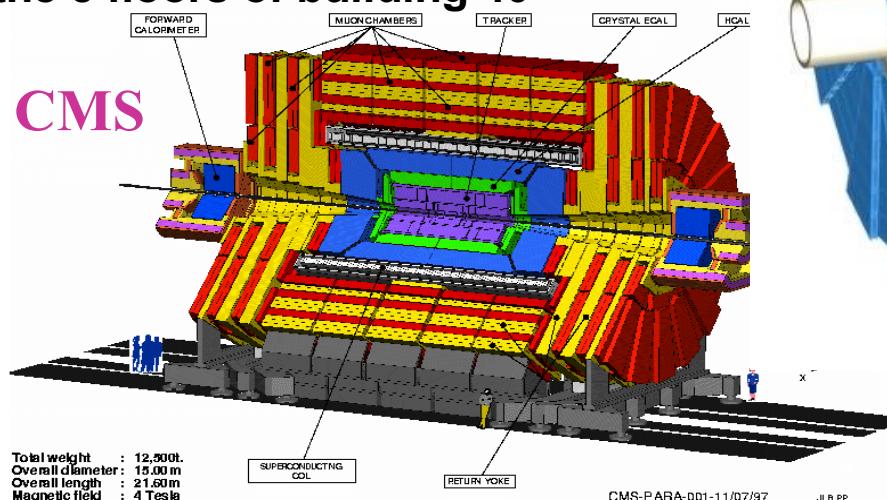


Computer Centre



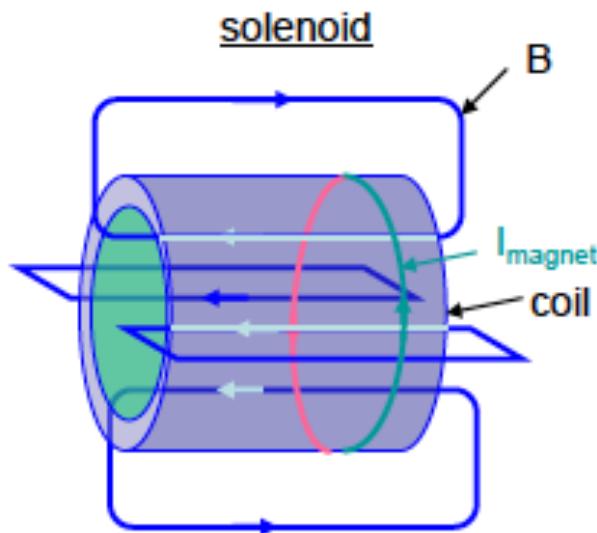
# How huge are ATLAS and CMS?

ATLAS superimposed to  
the 5 floors of building 40



	<u>ATLAS</u>	<u>CMS</u>
<i>Overall weight (tons)</i>	<b>7000</b>	<b>12500</b>
<i>Diameter</i>	<b>22 m</b>	<b>15 m</b>
<i>Length</i>	<b>46 m</b>	<b>22 m</b>
<i>Solenoid field</i>	<b>2 T</b>	<b>4 T</b>

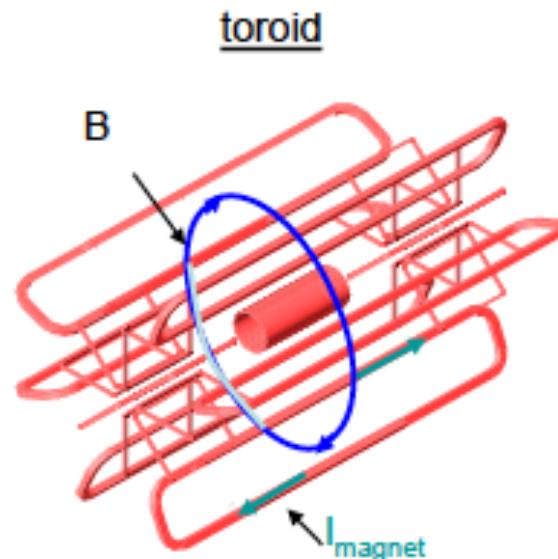
## Magnetic field configurations:



- + Large homogenous field inside coil
- weak opposite field in return yoke
- Size limited (cost)
- rel. high material budget

### Examples:

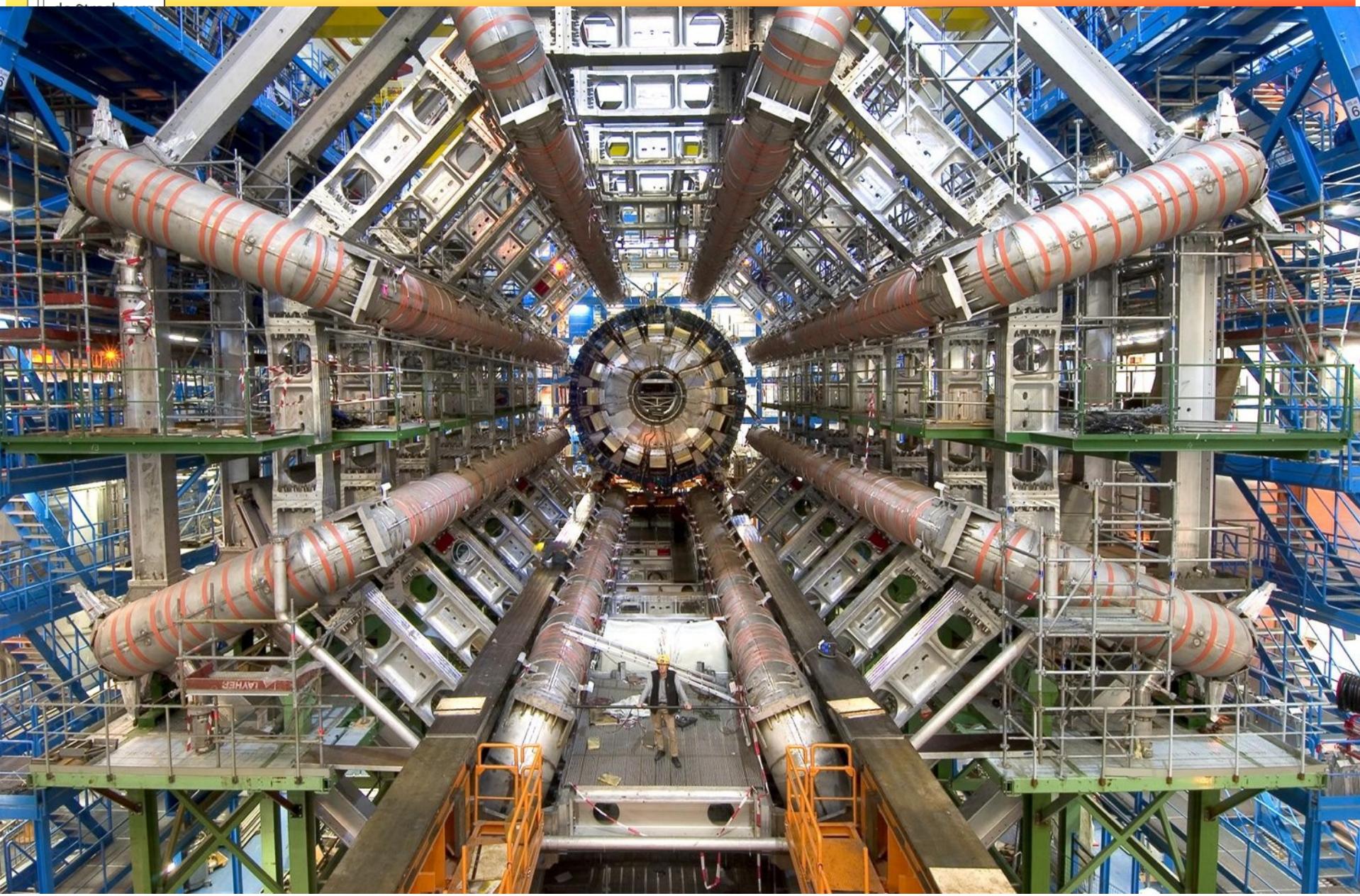
- DELPHI (SC, 1.2T)
- L3 (NC, 0.5T)
- CMS (SC, 4T)

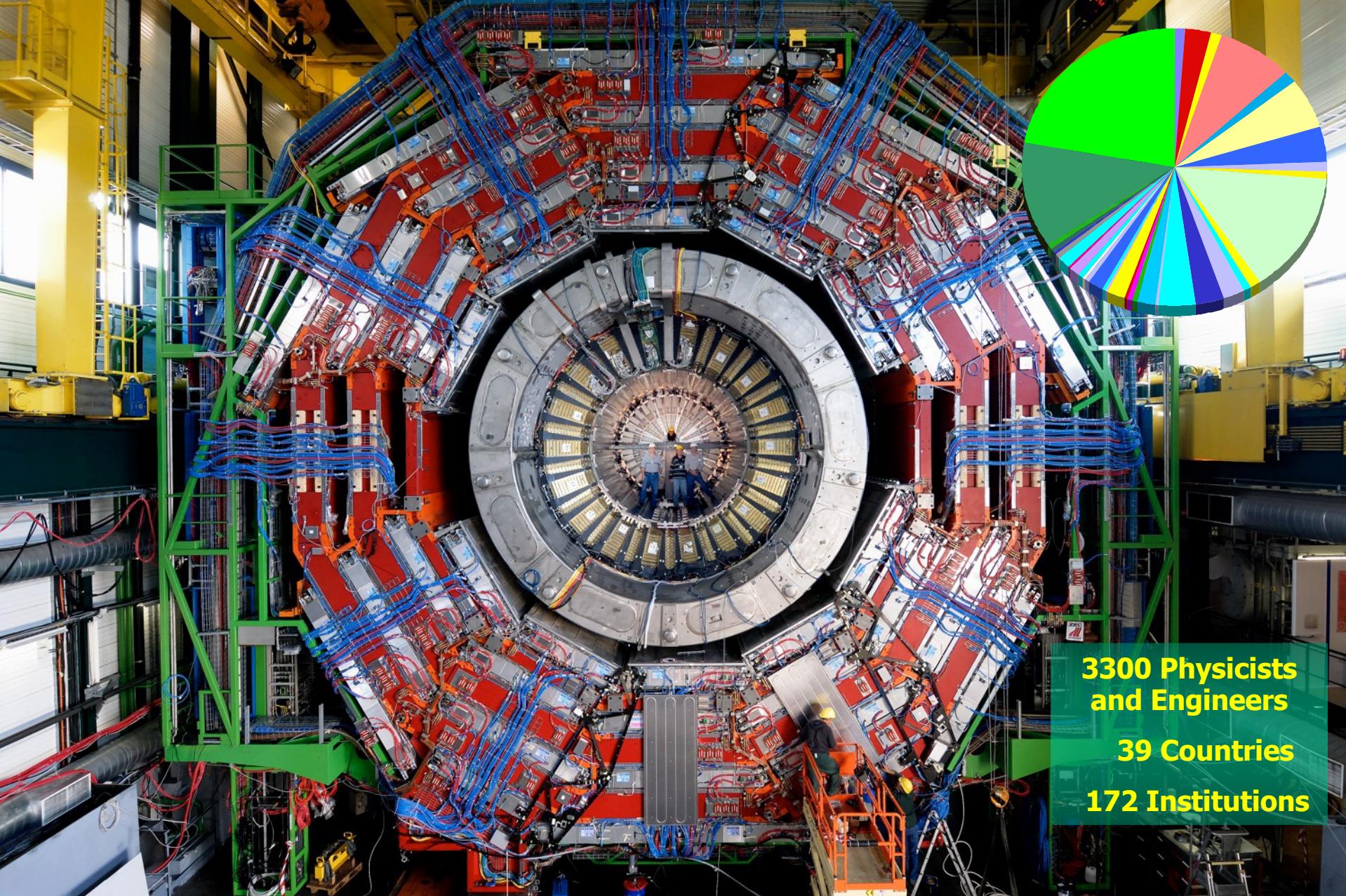


- + Rel. large fields over large volume
- + Rel. low material budget
- non-uniform field
- complex structure

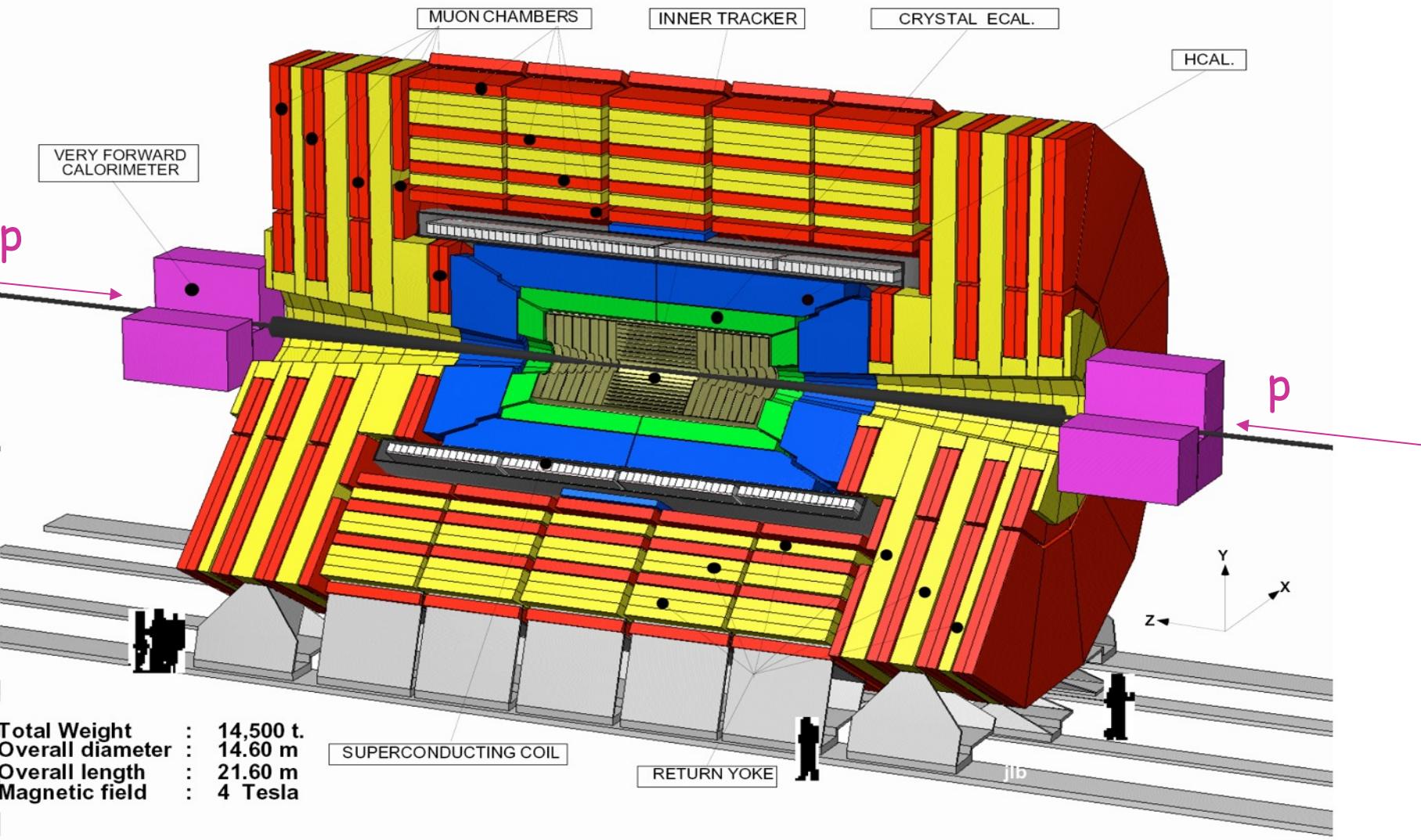
### Example:

- ATLAS (Barrel air toroid, SC, 0.6T)

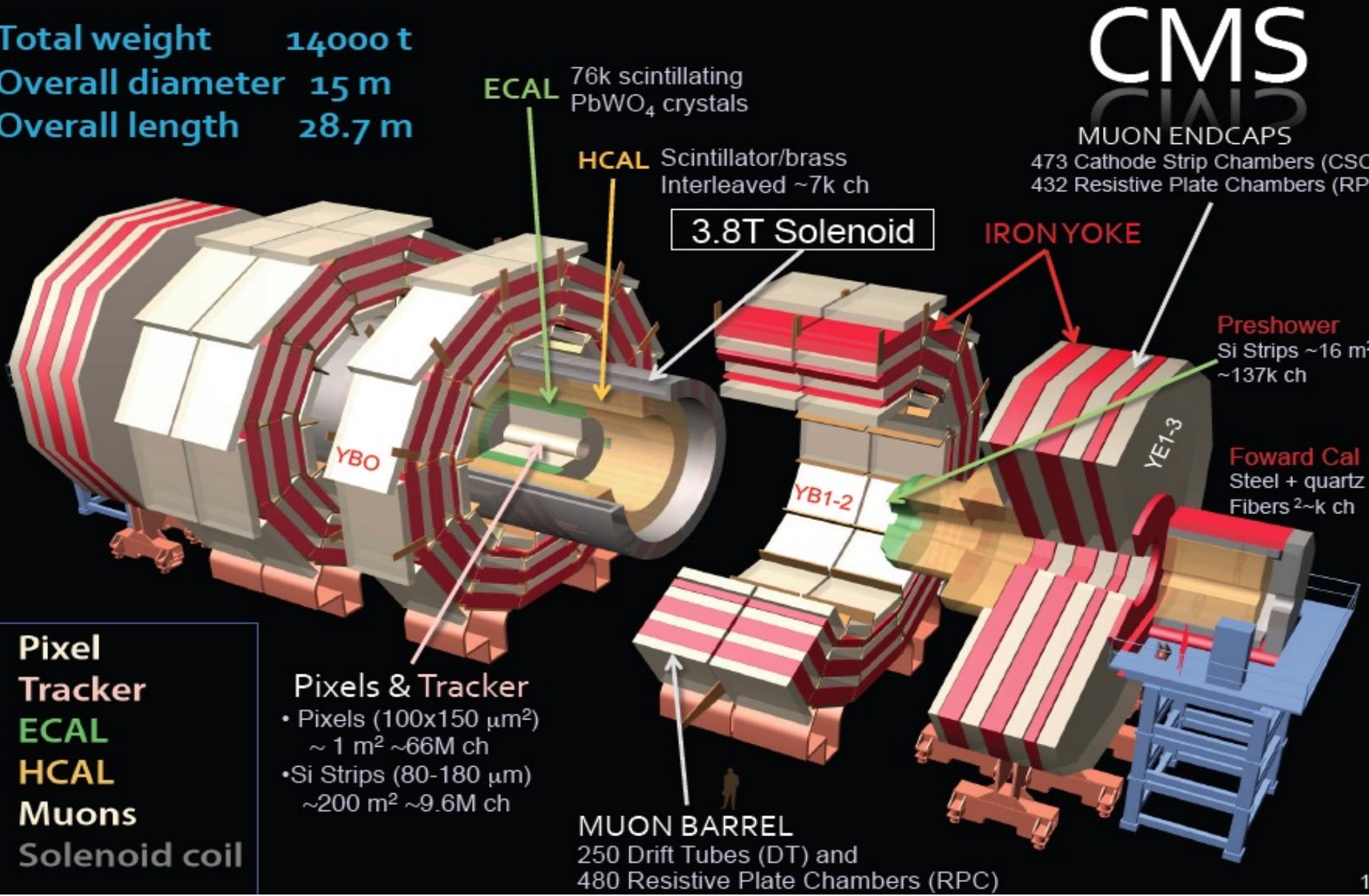




# Compact Muon Solenoid

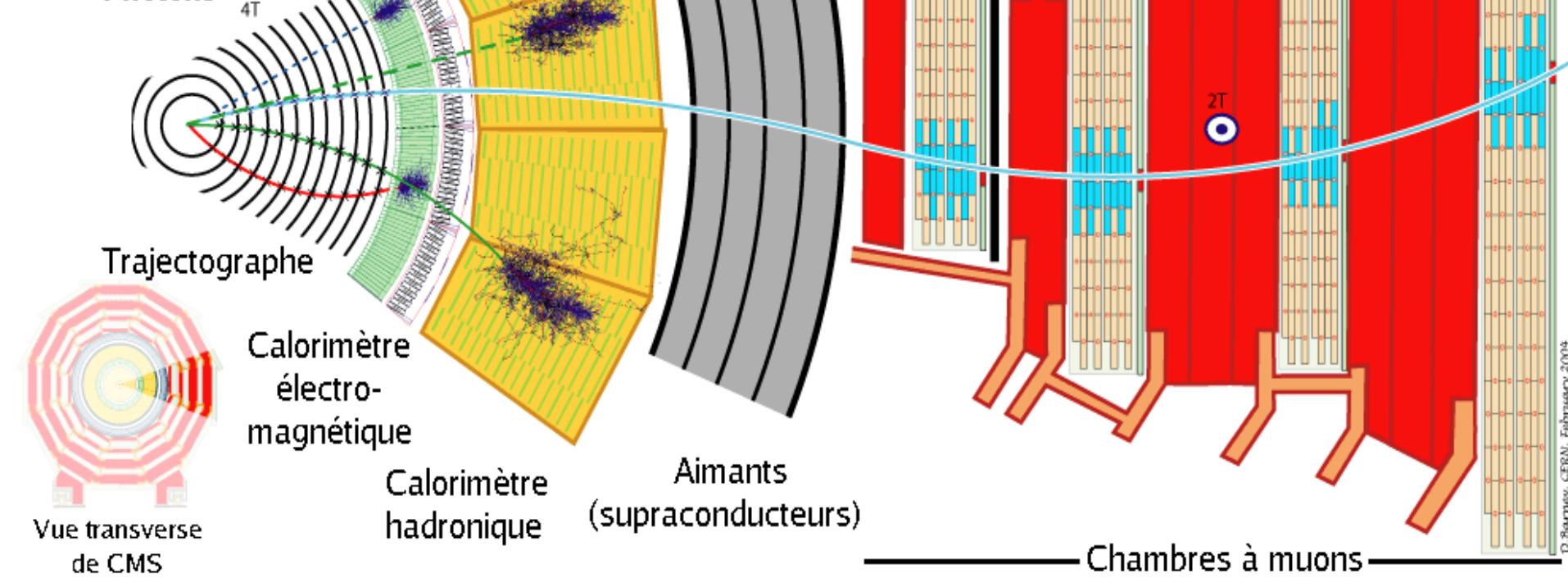


**Total weight 14000 t**  
**Overall diameter 15 m**  
**Overall length 28.7 m**

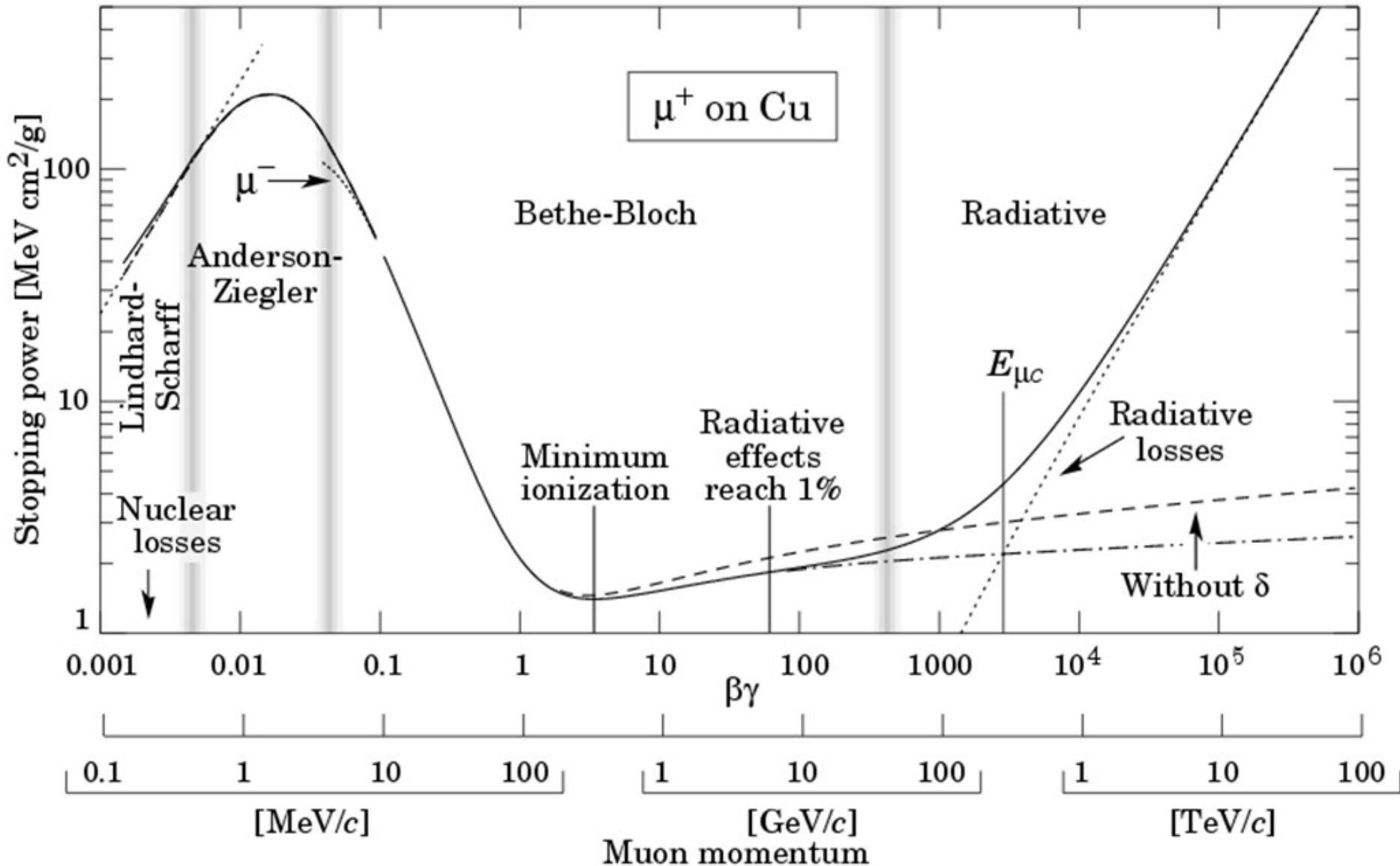


Legende :

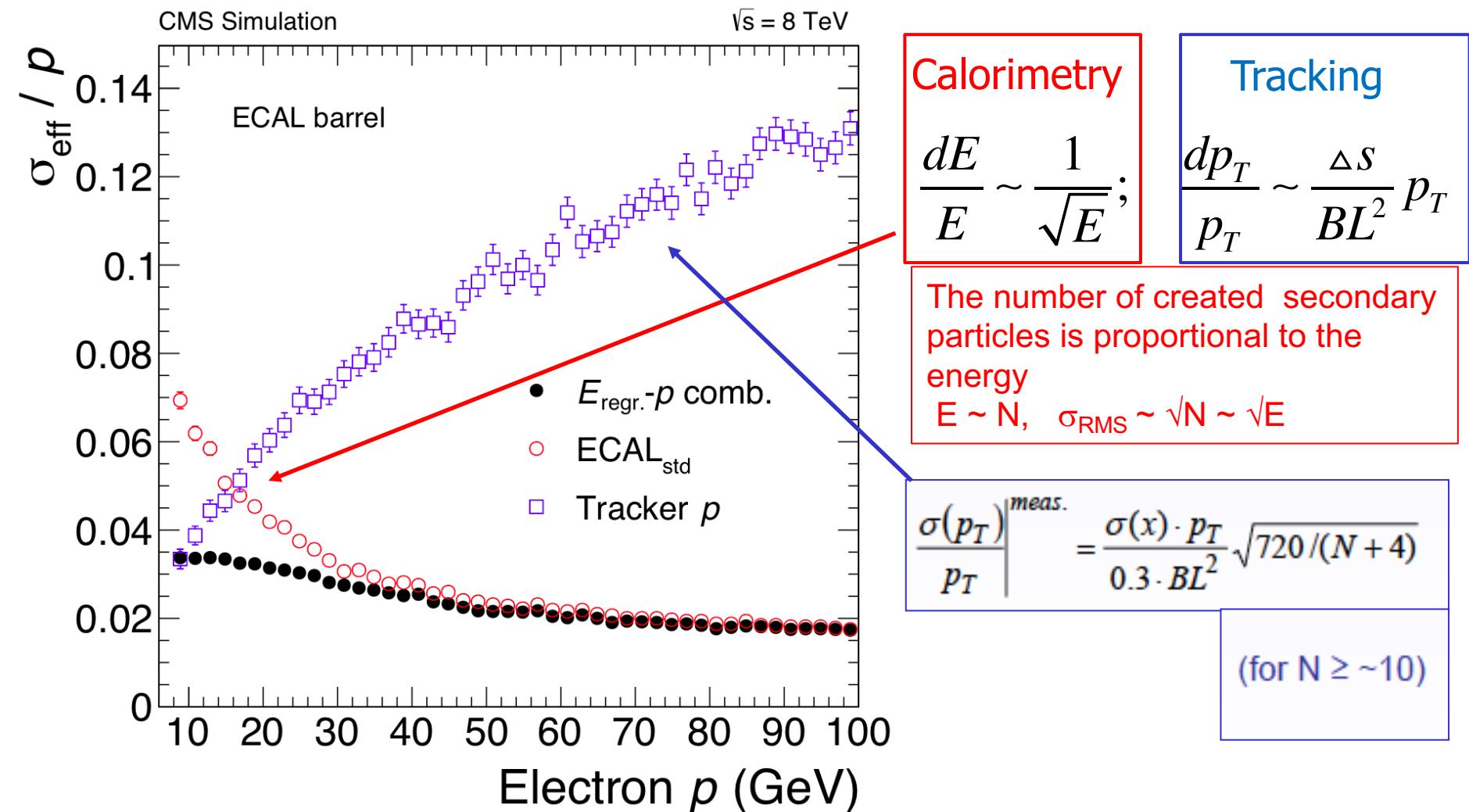
- Muons
- Électrons
- Hadron chargé
- Hadron neutre
- Photons 



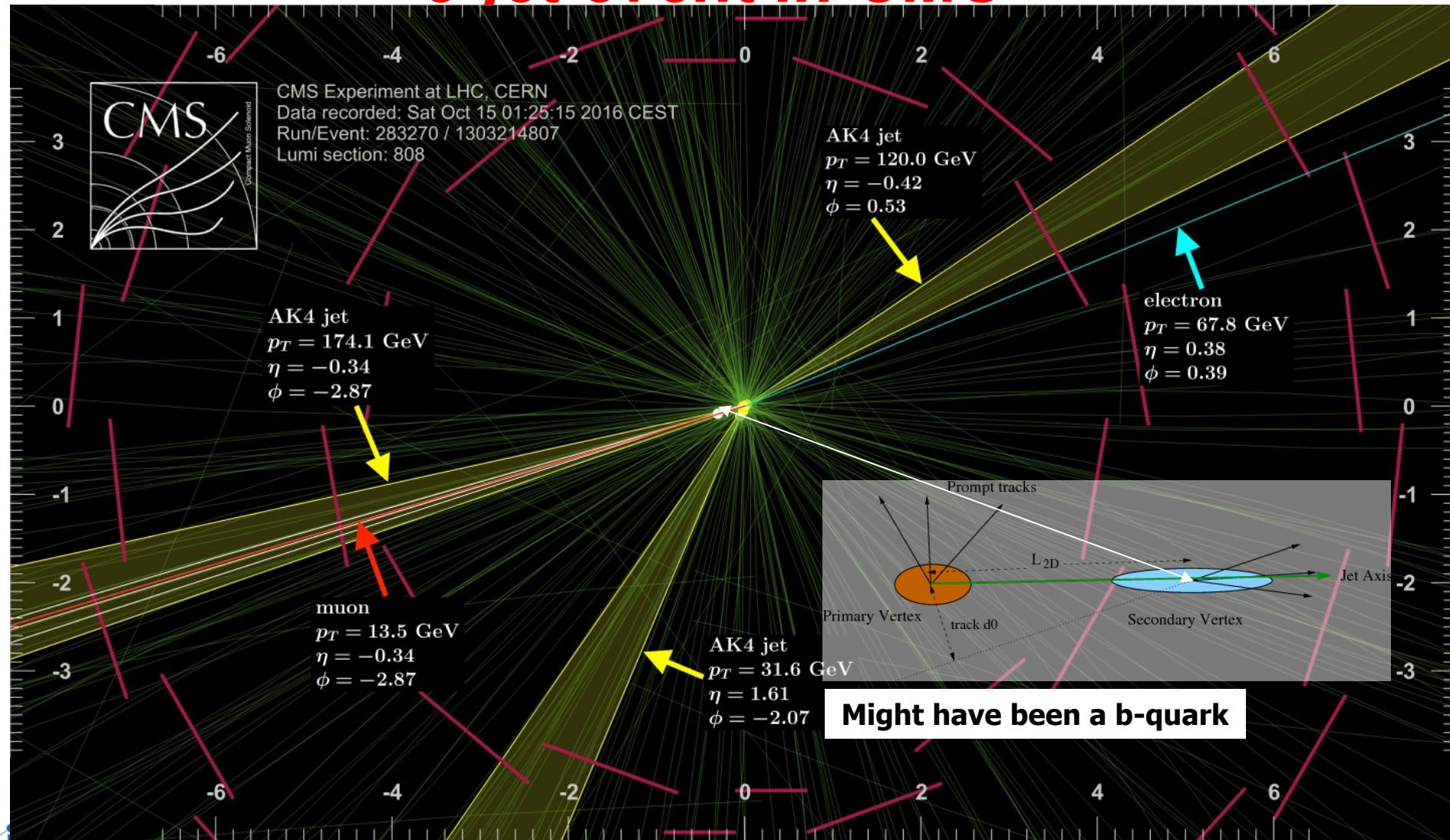
## Transverse slice through CMS detector



# Energy / momentum resolution



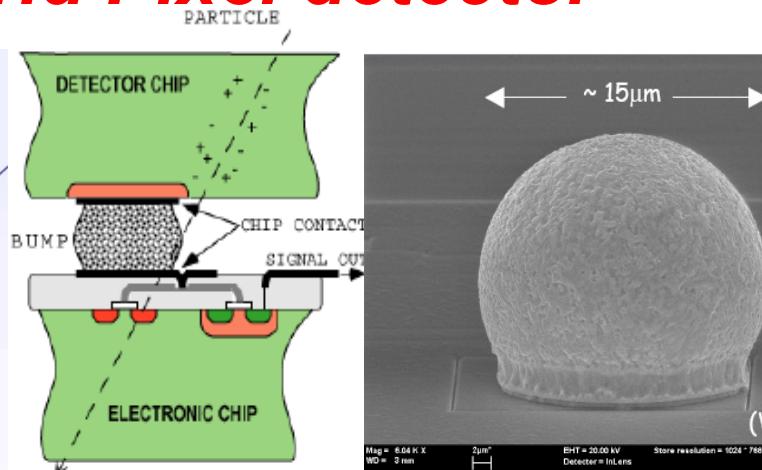
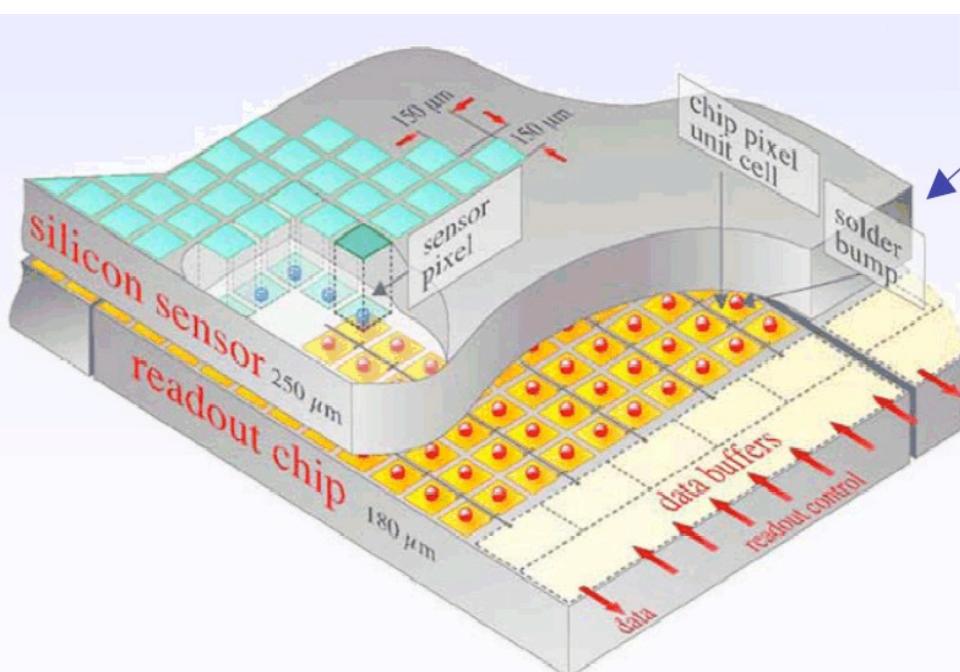
# 3-jet event in CMS



# **CMOS Pixel detectors**

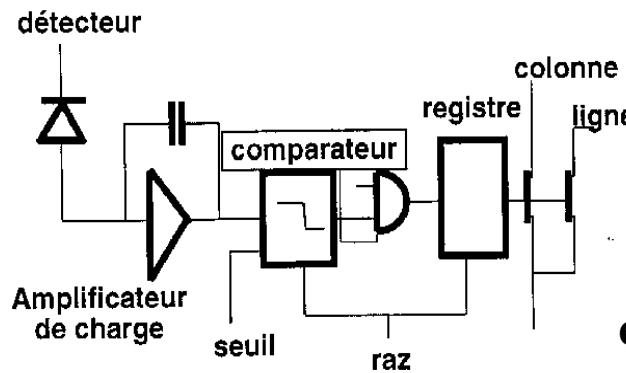
- **Powerful vertex detectors**
- **For high resolution tracking**
- **Industrial processes**
- **Very small material budget (thin detectors)**
  - Remember multiple scattering !
  - Photon conversion to  $e^+ e^-$
  - Bremsstrahlung of electrons
- **MAPS = Monolithic Active Pixel Sensors**

# Classical Hybrid Pixel detector

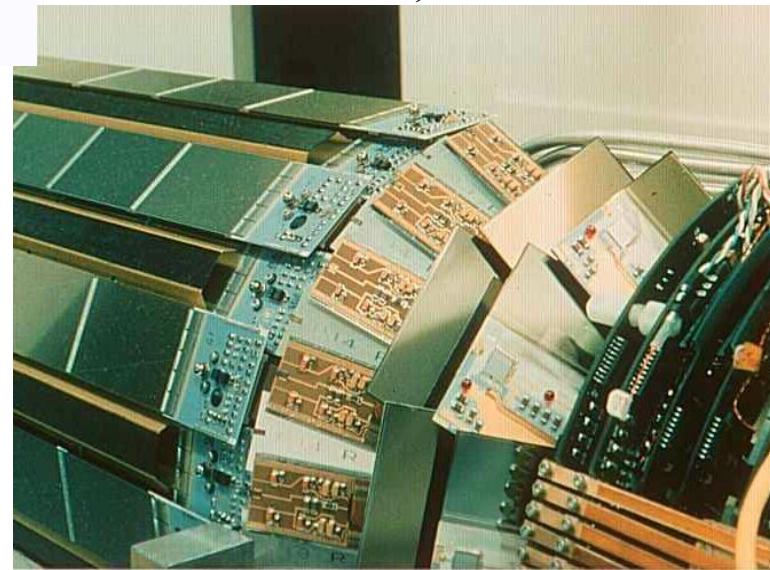


**DELPHI-LEP-CERN**

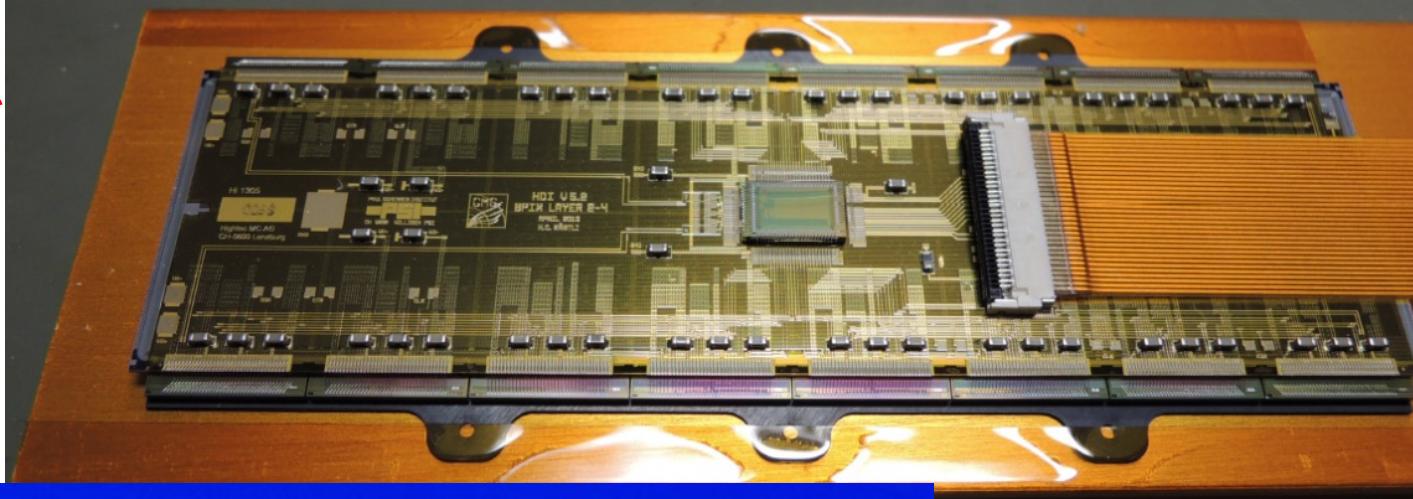
Pixels :  $330 \times 330 \mu\text{m}^2$   
152 modules, 1.22 M channels



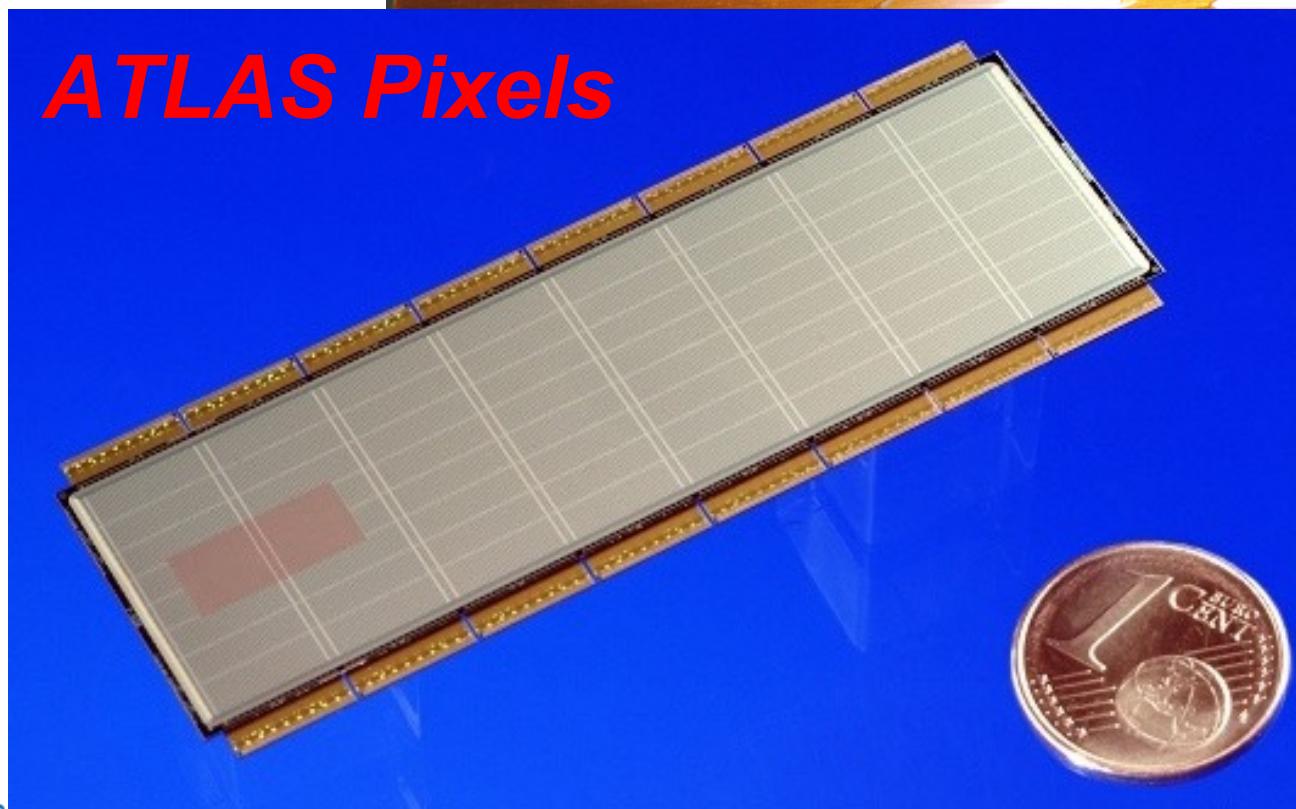
Pixel  
electronics:  
complex!



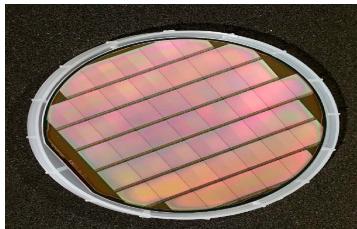
# CMS Pixels



# ATLAS Pixels

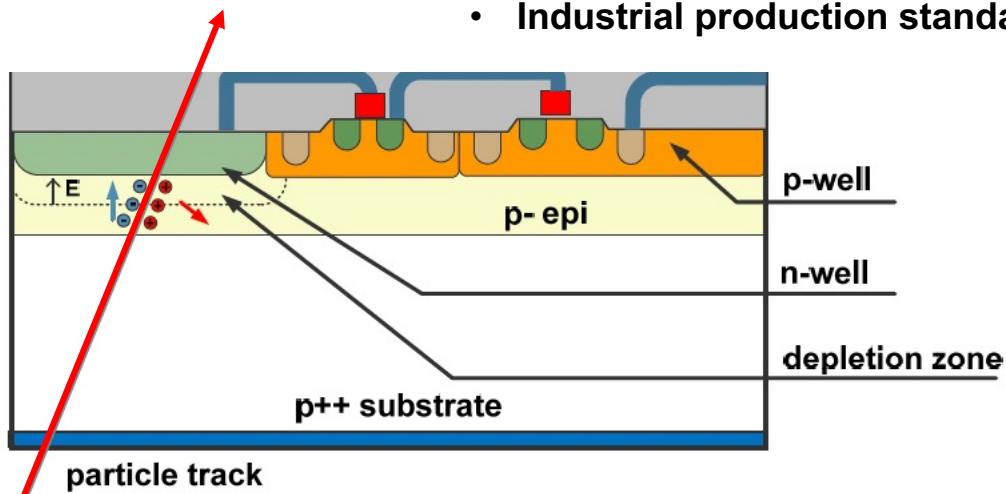


# CMOS (*Complementary metal-oxide-semiconductor*) Detectors



Avantages of CMOS VLSI technology:

- $\mu$ -circuits integrated but still
- 100% fill factor
- Small sensitive volume ( $\approx$  épitaxial layer)  $\approx 10 \mu\text{m}$  thick detectors can be very thin
- Industrial production standards  $\Rightarrow$  « modestes » costs,

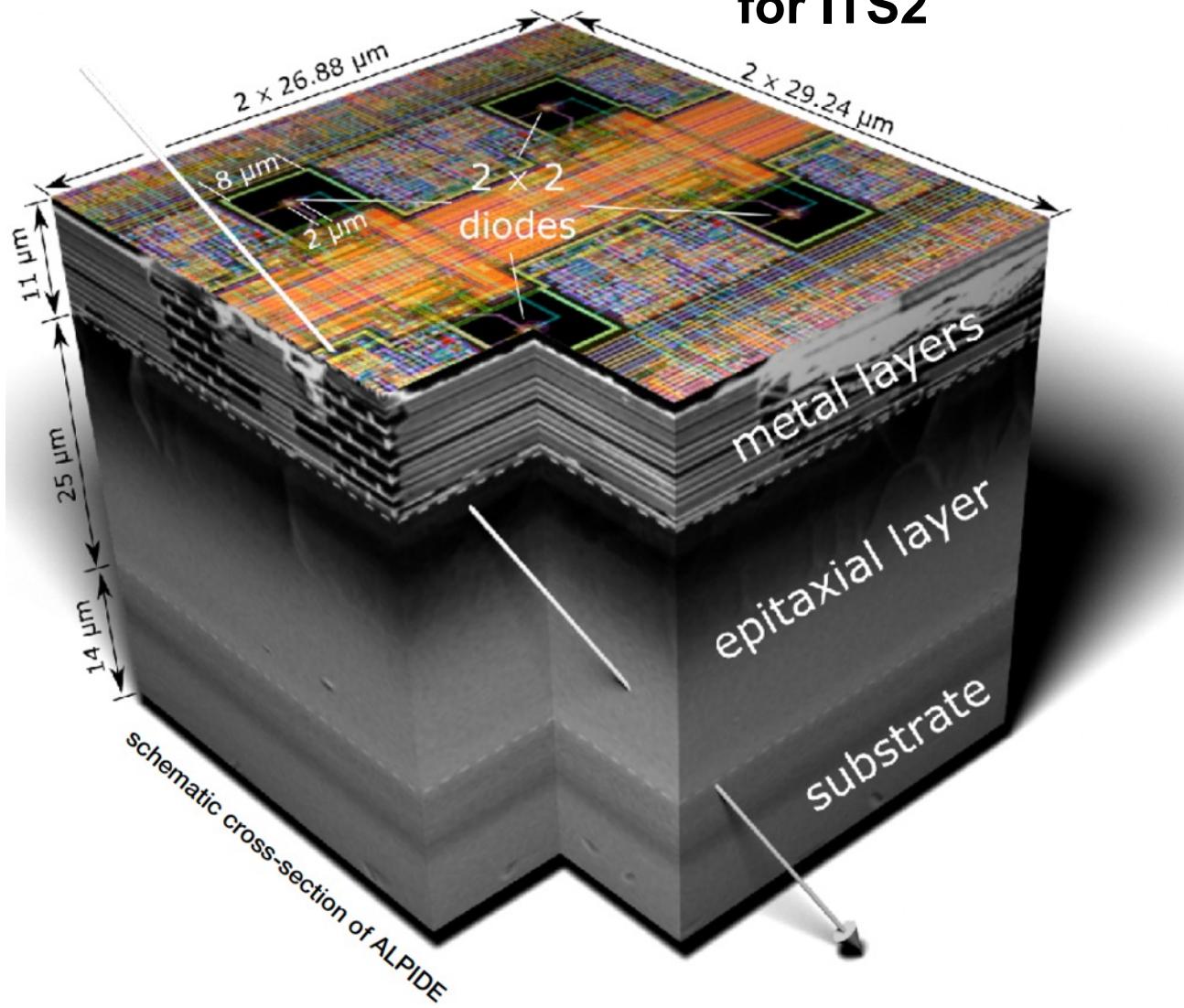


- Signal is created in p-epitaxial layer (lower doping):  
 $Q \approx 80 \text{ e-h} / \mu\text{m} \Rightarrow \text{signal} < 1000 \text{ e}^-$
- e<sup>-</sup> diffusent (thermiquement) to the junction helped by reflexions at the boundaries formed by the p-well and the substrat (higher doping)
- Diffusion time < 100ns
- Charge is collected by the diode formed by the junction n-well/p-epitaxial layer

## Short coming:

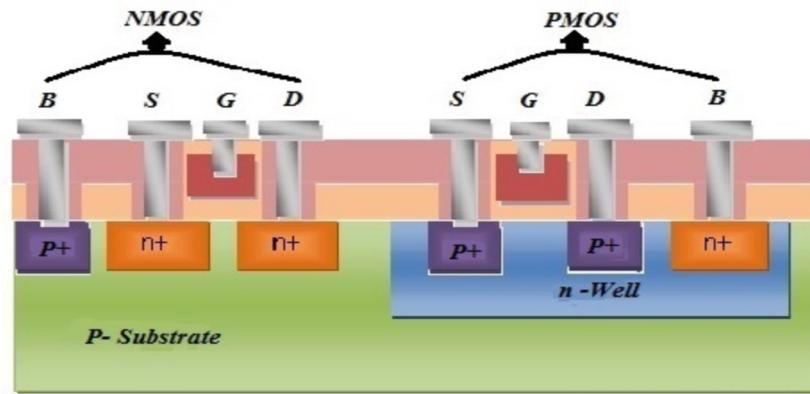
Circuitry of the electronic circuit is limited to only NMOS transistors.

# ALPIDE — the Monolithic Active Pixel Sensor (MAPS) for ITS2



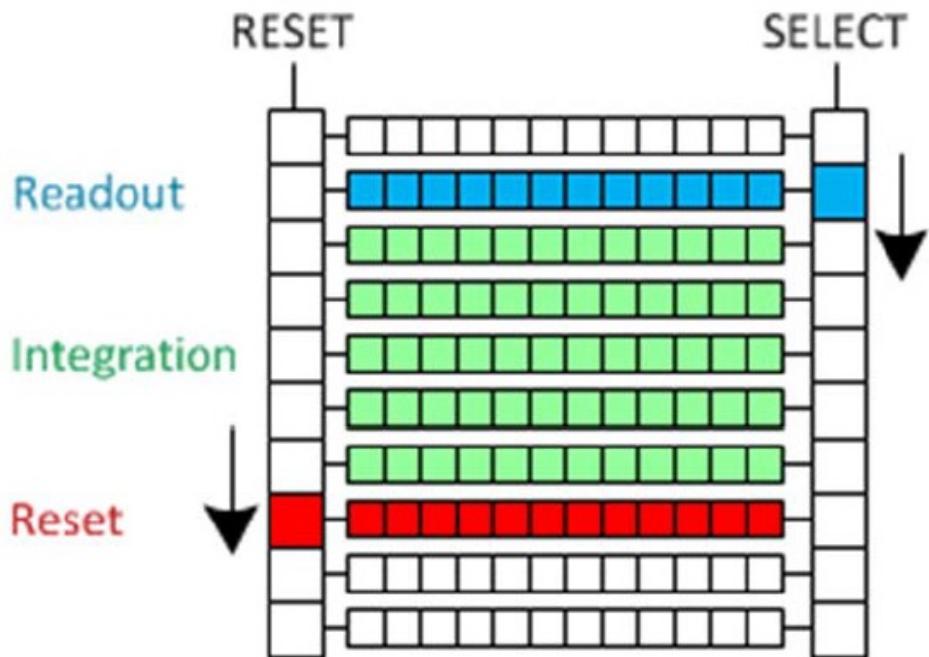
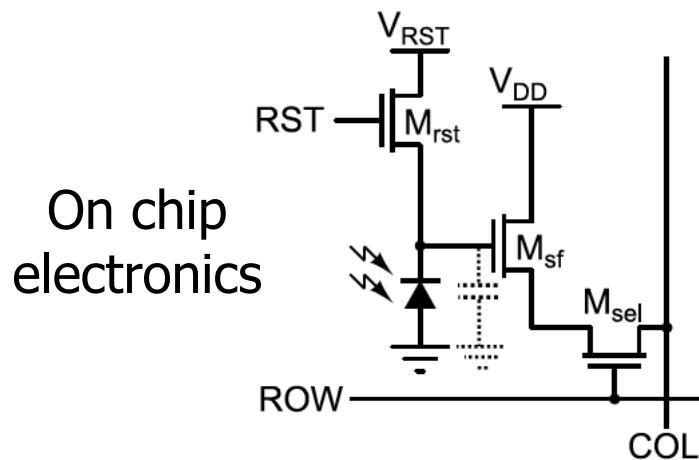
# Characteristics:

- Pixel detector could be made very thin, low material budget!
- Thin epitaxial layer → Small signals
- Small pixel size possible ( $10 \times 10 \mu\text{m}^2$ ) to obtain very good spatial resolution, but then limited space for electronic circuit available
- (Only n-well Transistors)
- Simple on pixel-cell electronics → slow Read Out (next slide)



©Elprocus.com

# Overview of Rolling Shutter Architecture



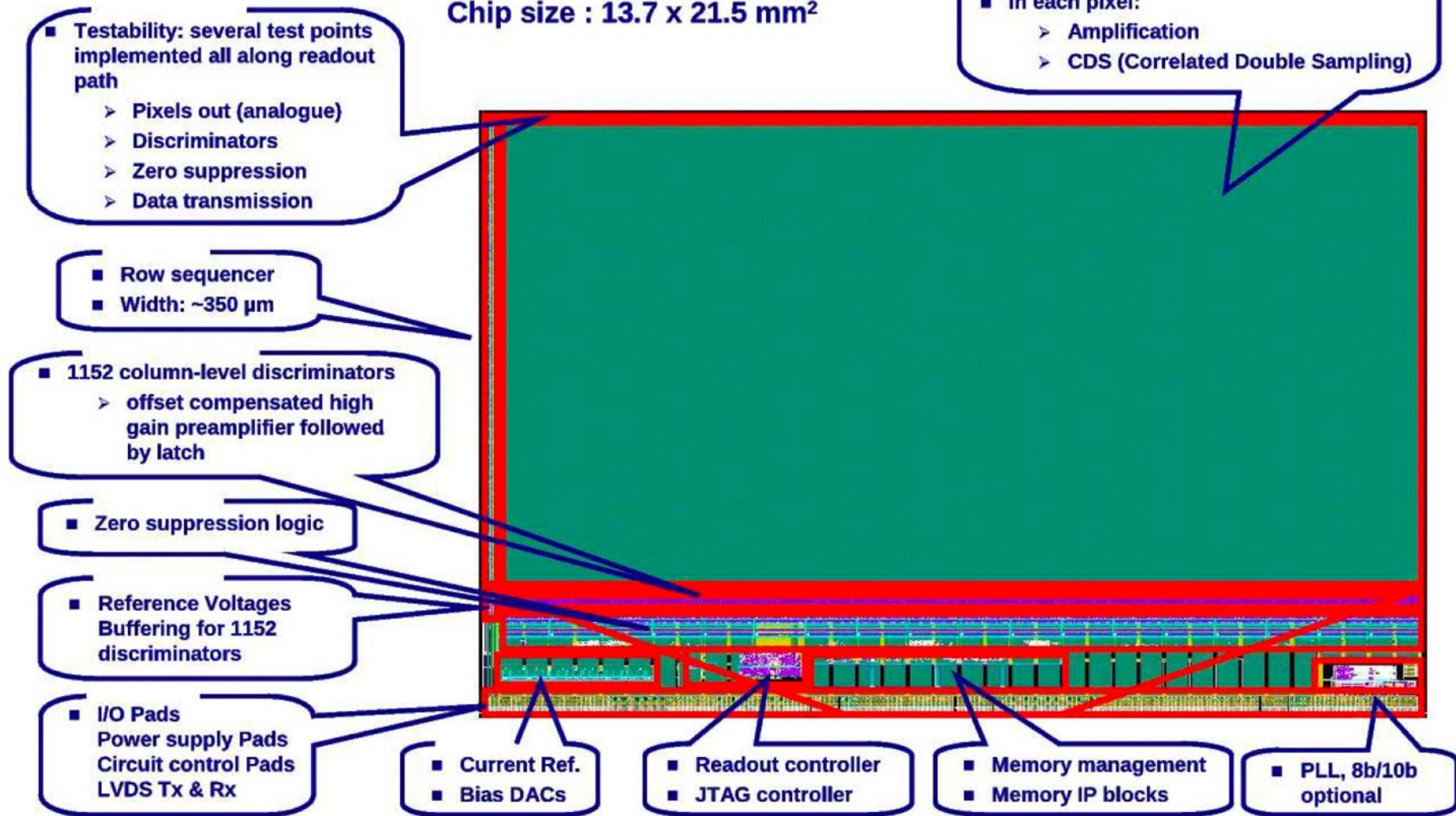
**Rolling shutter readout concept where the integrated signal is read out and reset row by row:**

- In this case all pixel outputs in the column are connected.
- Only one row of pixels is selected at a time for readout and/or reset.
- The column outputs can be multiplexed at the periphery in case of limited analog outputs.
- The recorded values can be digitized by external or internal components

# Typical layout of a MAPS chip

CMOS 0.35  $\mu\text{m}$  OPTO technology  
Chip size : 13.7 x 21.5 mm<sup>2</sup>

- Pixel array: 576 x 1152, pitch: 18.4  $\mu\text{m}$
- Active area: ~10.6 x 21.2 mm<sup>2</sup>
- In each pixel:
  - > Amplification
  - > CDS (Correlated Double Sampling)



courtesy of Ch. Hu-Guo / TWEPP-2010

## ***Developments to improve performance for different experiments***

- Several labs develop CMOS pixel sensors : Italy (INFN, Univ.), UK (RAL), CERN, France (IPHC, Saclay), USA, ...
- Increase and speed up collected charge by drift in depleted silicon
- Use of high resistivity silicon wafers
- Use of different (more complicated) CMOS processes
- Change layout to use the complete design potential (use of p-MOS transistors)
- Speed up Read Out architecture
- Large area (wafer size) devices (stitching)
- Curved thin detector layers without additional support material
- ....

# Depleted Monolithic Active Pixels (HV-MAPS or D-MAPS)

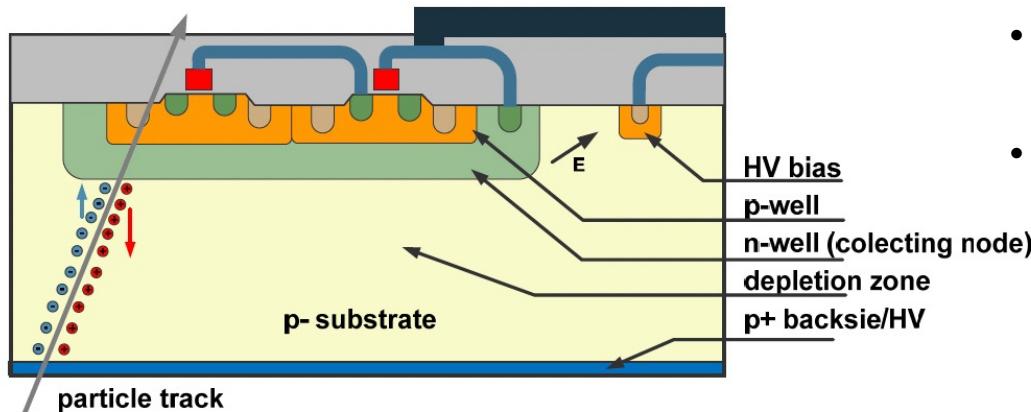
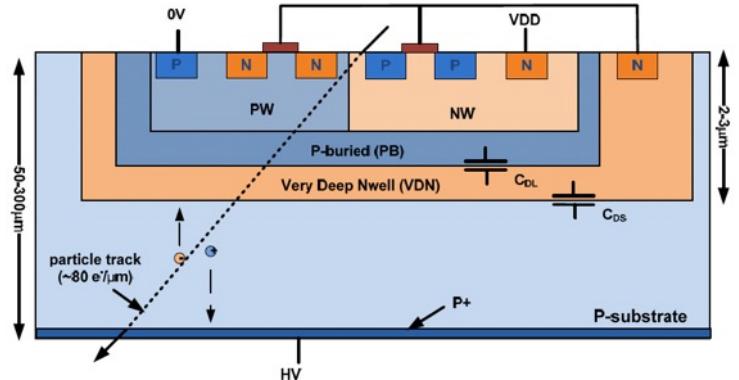


Figure 1-4 Cross section of a depleted MAPS detector with fully depleted bulk with backside contact where charge is collected by drift.

## Goals:

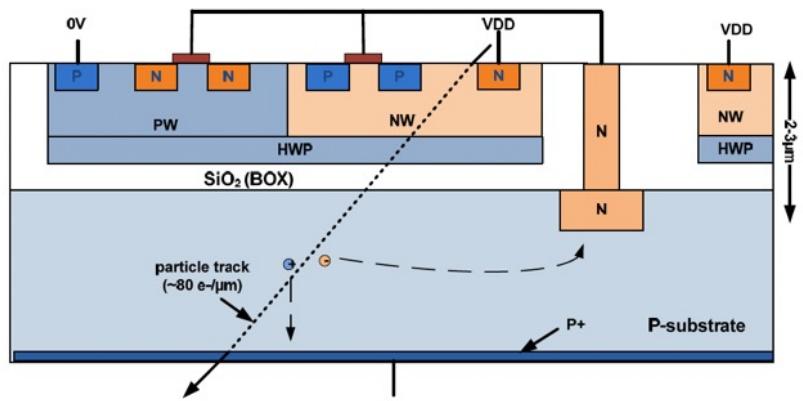
- large signals
- fast charge collection by drift in a 50 $\mu$ m – 200 $\mu$ m thick depleted layer
- the use of PMOS and NMOS transistors in the pixel cell (full CMOS),
- The entire CMOS pixel electronics is placed inside the deep n-well.
- This way, the pixel contains only one deep n-well without any inactive secondary wells that could attract the signal charge and cause detection inefficiency.
- it is reversely biased with respect to the substrate from the front side.
- By applying high voltage reverse bias (>60V) it is possible to create a depletion depth of a few to tens of microns
- implementation in a commercial technology

Tomasz Hemperek, PhD thesis



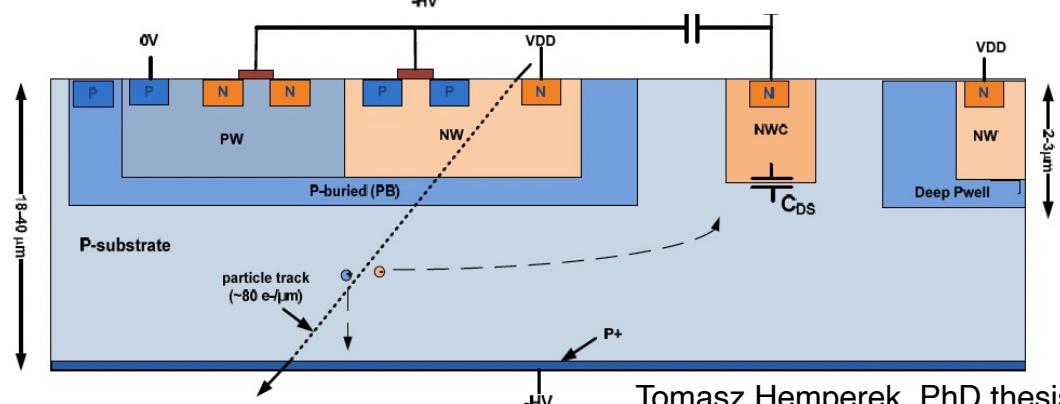
**Depleted MAPS, logic inside collecting node**

*Many different designs are being explored and tested*



**Depleted MAPS, HV-SOI**

(BOX = buried layer of silicon oxide)



**Depleted MAPS,**

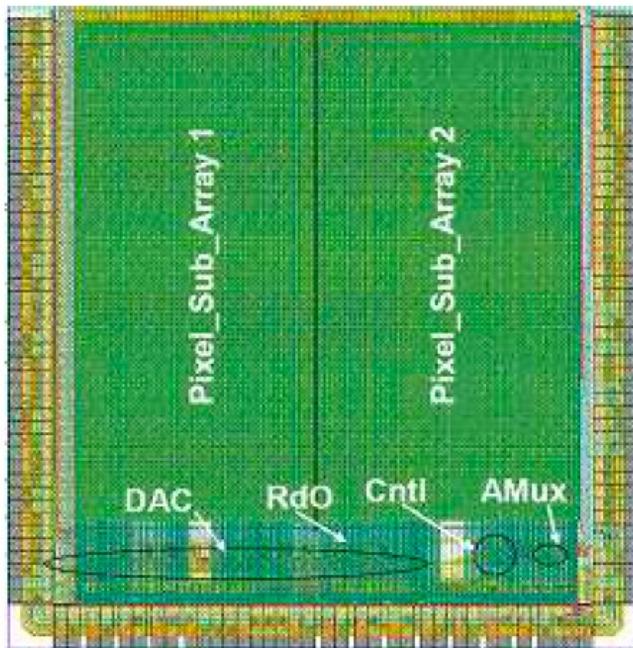
Logic located outside collecting node

# *Building Vertex detectors with MAPS*

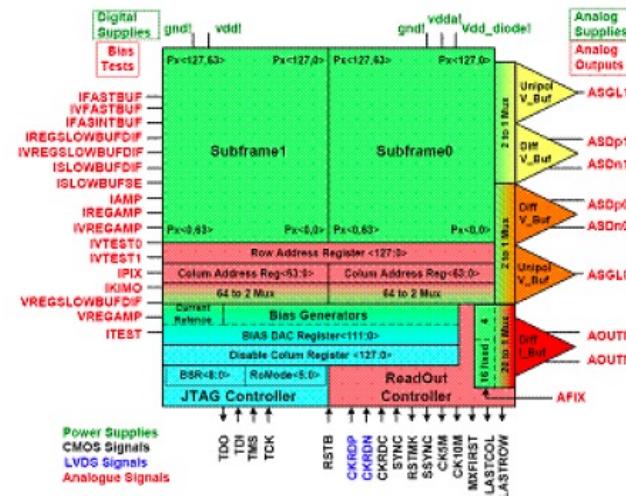
## STAR experiment at RHIC, BNL

First large scale application of MAPS in an experiment

- 2 layers of MAPS for pixel vertex detector



(a) chip layout



(b) functional diagram of the chip

M. A. Szelezniak PhD thesis 2008

Figure 6.3: MIMOSTAR chip - layout, (a), and a functional schematic diagram, (b).

# STAR experiment at RHIC, BNL

*First large scale application of MAPS in an experiment*

- 2 layers of MAPS for pixel vertex detector



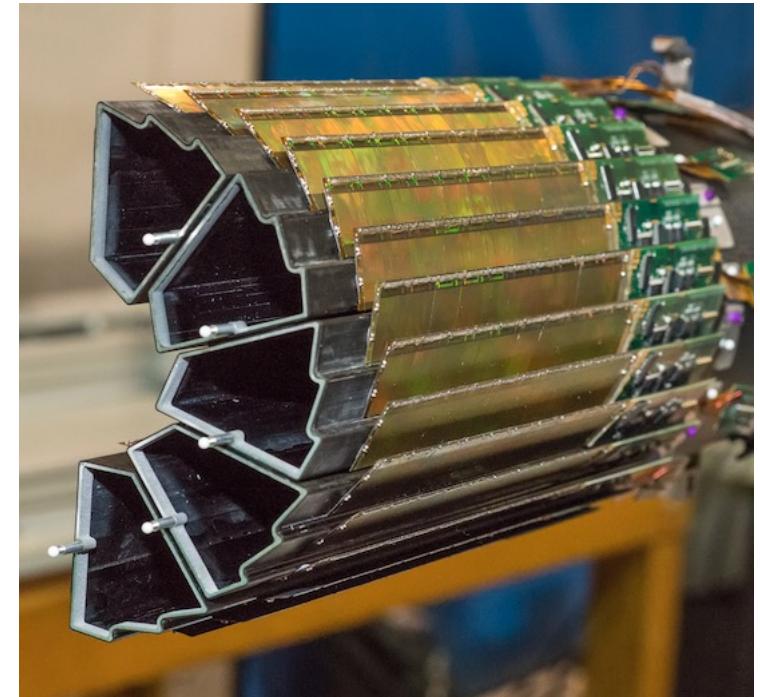
356 M pixels in 2 layers ~0.16 m<sup>2</sup>

R=28mm, 80mm

Pixels size 20.7x20.7 μm<sup>2</sup>

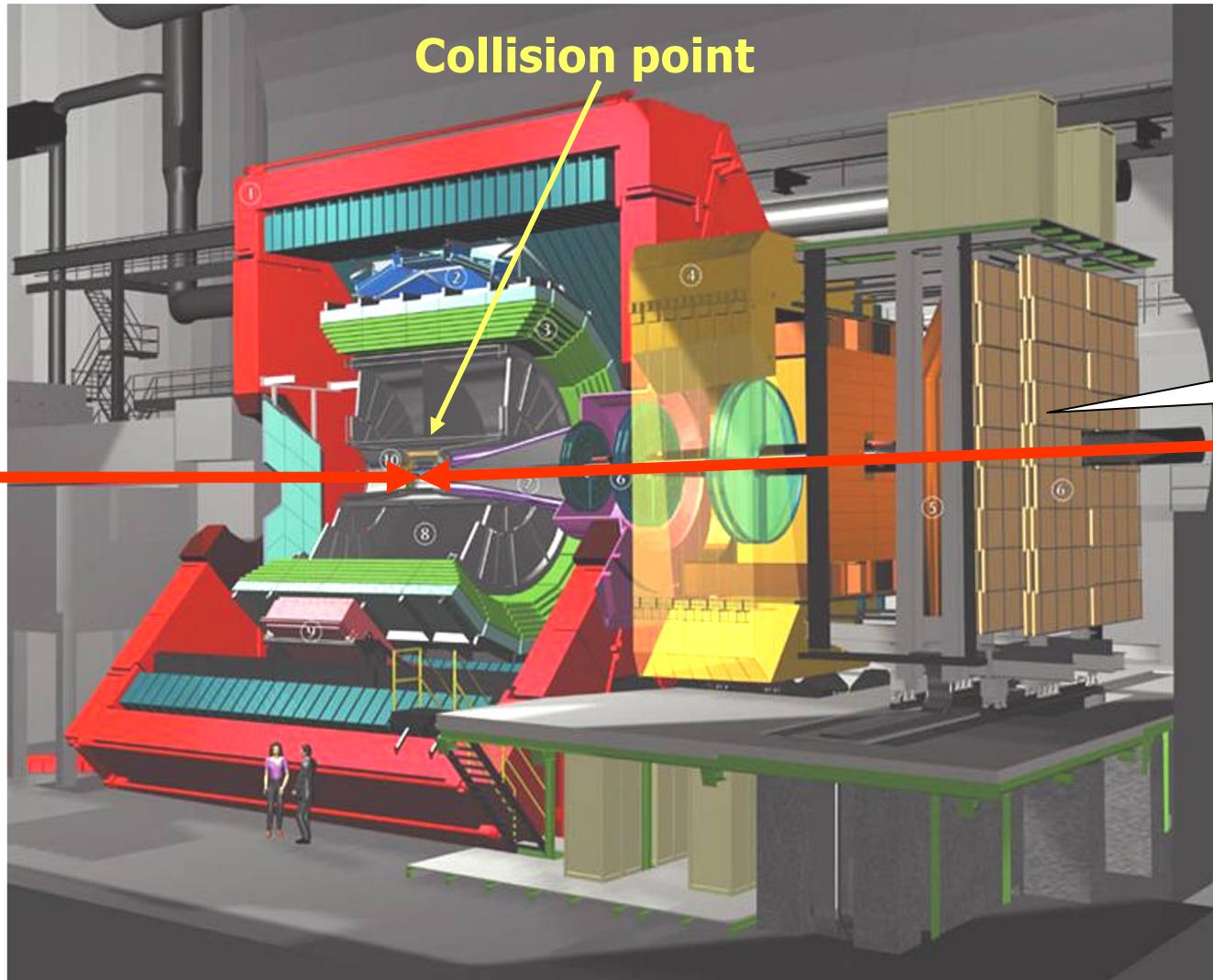
X/X<sub>0</sub> = 0.39% for layer 1

Integration time 185.6 μs



carbon fiber sector tubes (~ 200 μm thick)

# ALICE



Over 1000  
physicists

Muon  
spectrometer

**Dimensions :**  
**Length : 26m.**  
**• Height : 16m.**  
**• Weight : 10000 tonnes.**

# Building Vertex detectors with MAPS

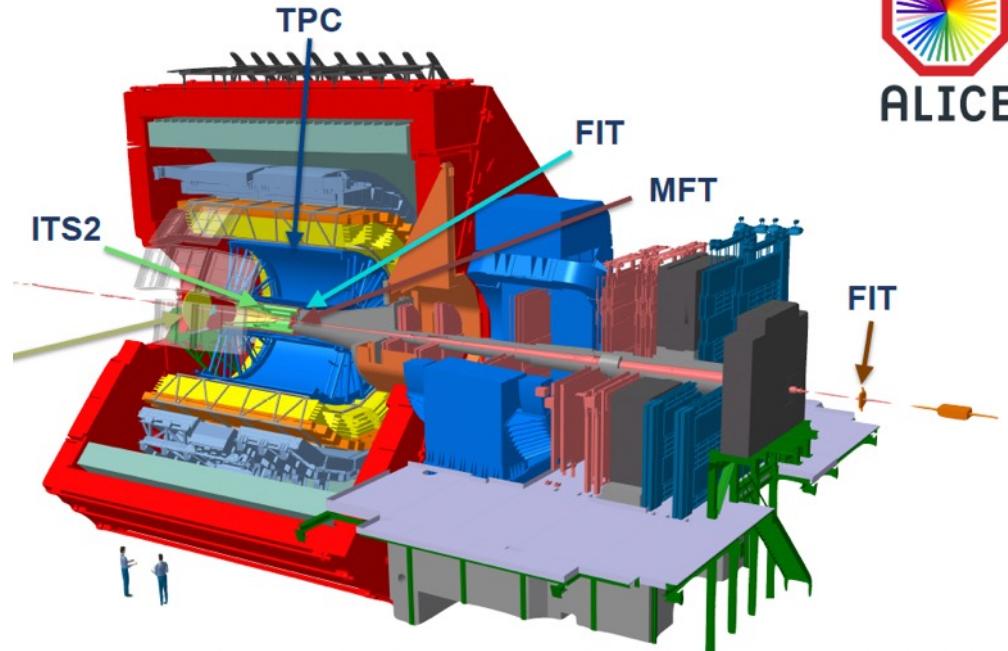
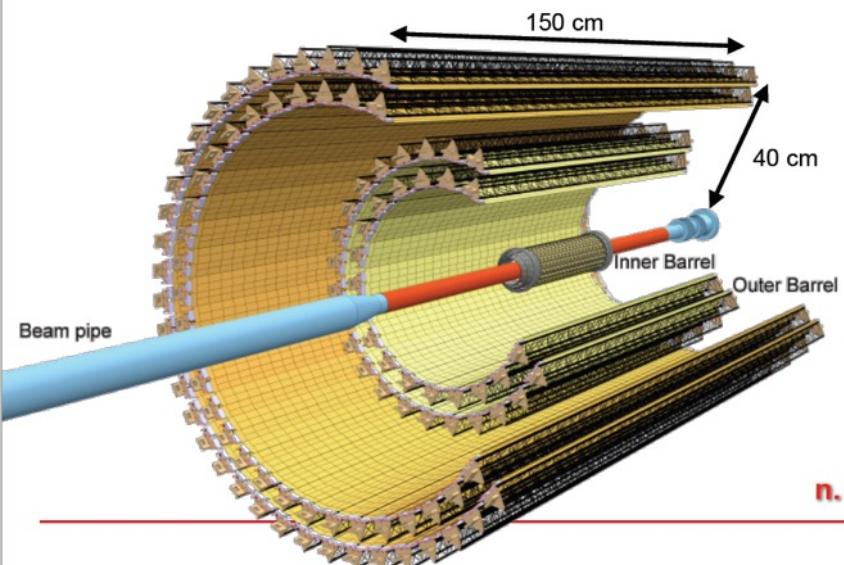
## ALICE (LHC-CERN)

A Large Ion Collider Experiment

### ITS2 layout

- 7 layers (inner/middle/outer): 3/2/2 from R = 23 mm to R = 400 mm
- 192 staves (IL/ML/OL): 48/54/90
- Ultra-lightweight support structure and cooling

**10 m<sup>2</sup> active silicon area, 12.5×10<sup>9</sup> pixels**



**CMOS MAPS:**

Spatial resolution  $\approx 5 \mu\text{m}$

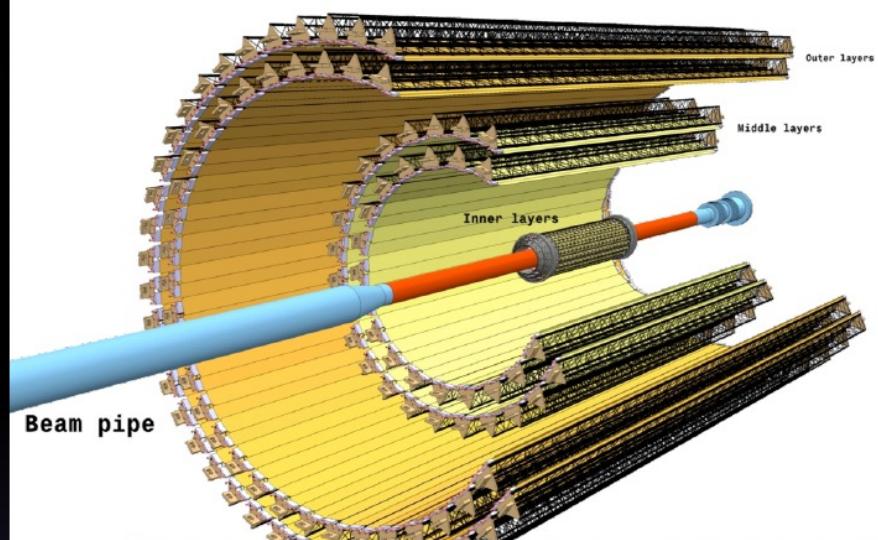
Integration time  $< 10 \mu\text{s}$

high-resistivity silicon epitaxial layer

UNIVERSITY OF  
OXFORD

# ALICE: MAPS

- Improve impact parameter resolution by a factor of  $\sim 3$  in  $(r\phi)$  and  $\sim 5$  in  $(z)$ 
  - Closer to IP: 39 mm  $\rightarrow$  21 mm (layer 0)
  - Reduce beampipe radius: 29 mm  $\rightarrow$  18.2 mm
  - Reduce pixel size:  $(50 \mu\text{m} \times 425 \mu\text{m}) \rightarrow O(30 \mu\text{m} \times 30 \mu\text{m})$
  - Reduce material budget:  $1.14 \% X_0 \rightarrow 0.3 \% X_0$  (inner layers)



$\sim 10 \text{ m}^2$     **12.5 G pixel**



- High tracking efficiency and  $p_T$  resolution
  - Increase granularity and radial extension  $\rightarrow$  7 pixel layers
- Fast readout of Pb-Pb interactions at 50 kHz (now 1 kHz) and 400 kHz in p-p interactions
- Rad hard to TID: 2.7 Mrad, NIEL:  $1.7 \times 10^{13} 1 \text{ MeV n}_{\text{eq}} \text{ cm}^{-2}$  (safety factor 10)
- Fast insertion/removal for maintenance

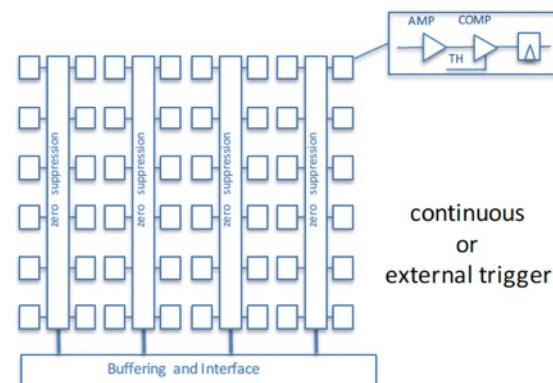
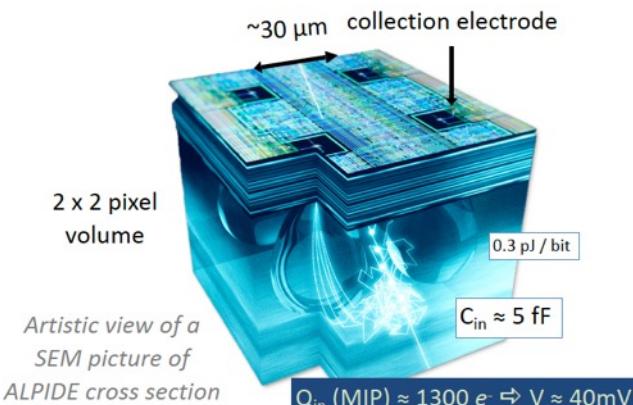
# Building Vertex detectors with MAPS

## ALICE (LHC-CERN)

A Large Ion Collider Experiment



### ALPIDE — the Monolithic Active Pixel Sensor (MAPS) for ITS2



- Developed within the ITS2 project

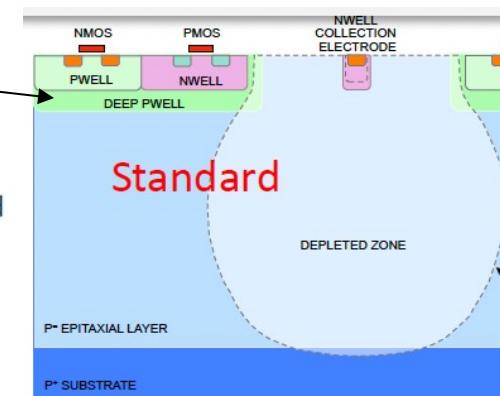
#### Technology

Technology now used in other applications

- TowerJazz 180 nm CMOS Imaging Process
- High-resistivity ( $> 1\text{k}\Omega \text{ cm}$ ) p-type epitaxial layer (25  $\mu\text{m}$ ) on p-type substrate
- Small n-well diode (2  $\mu\text{m}$  diameter),  $\sim 100$  times smaller than pixel (~30  $\mu\text{m}$ )  
→ low capacitance (~fF)
- Reverse bias voltage ( $-6 \text{ V} < V_{BB} < 0 \text{ V}$ ) to substrate to increase depletion zone around NWELL collection diode
- Deep PWELL shields NWELL of PMOS transistors  
→ full CMOS circuitry within active area

#### Key features

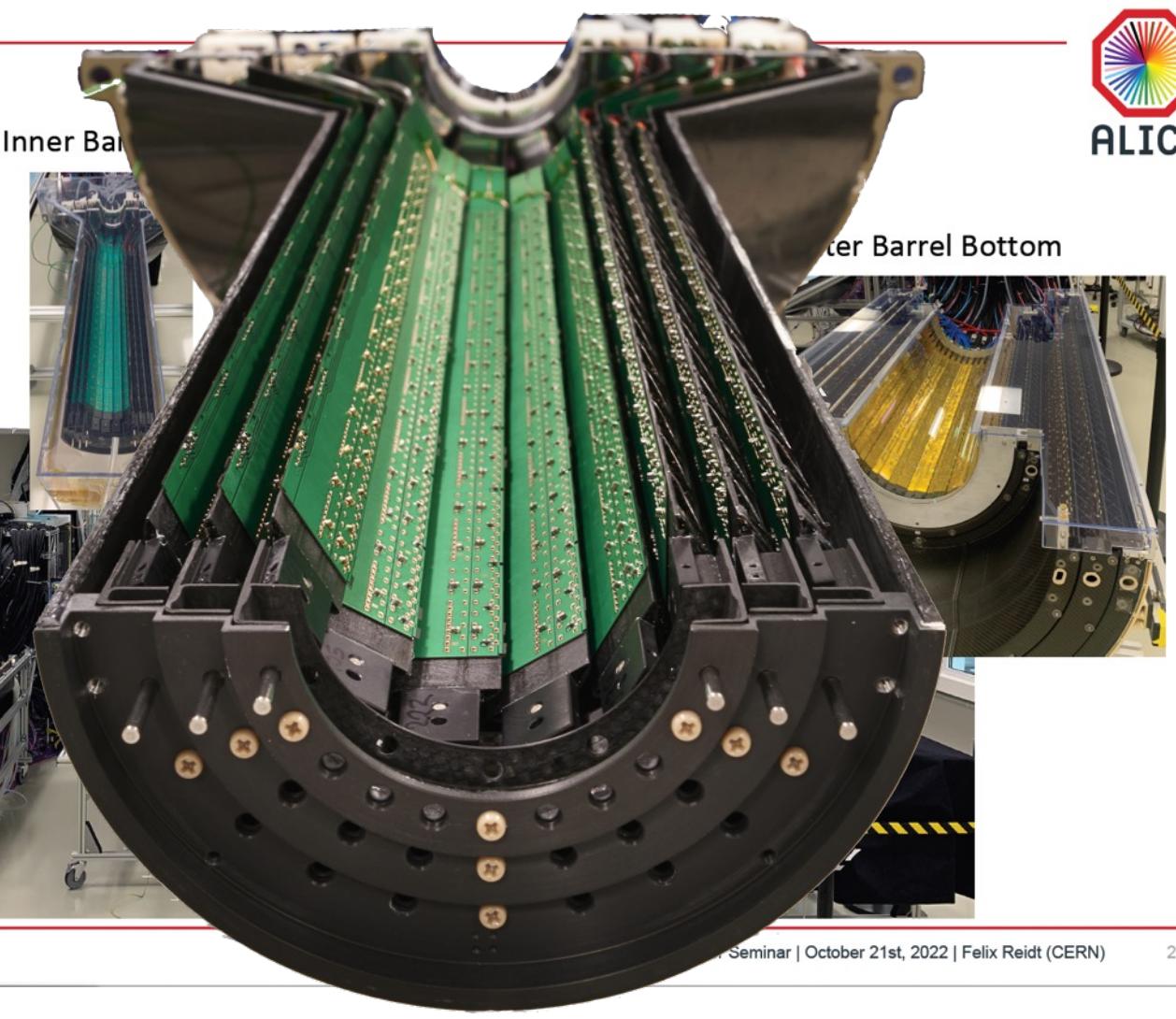
- In-pixel amplification and shaping, discrimination and Multiple-Event Buffers (MEB)
- In-matrix data sparsification
- On-chip high-speed link (1.2 Gbps)
- Low total power consumption  $< 40 \text{ mW/cm}^2$



# ALICE (LHC-CERN) ITS 2

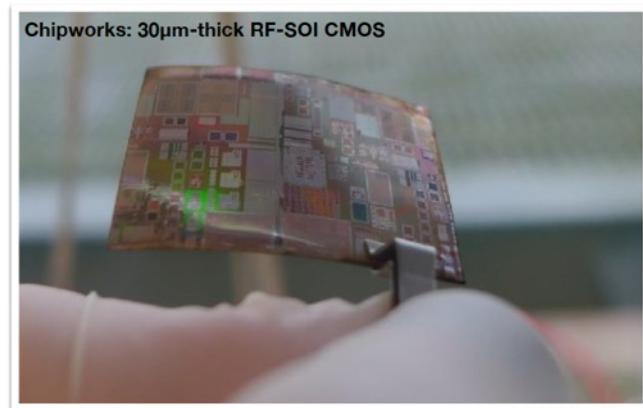
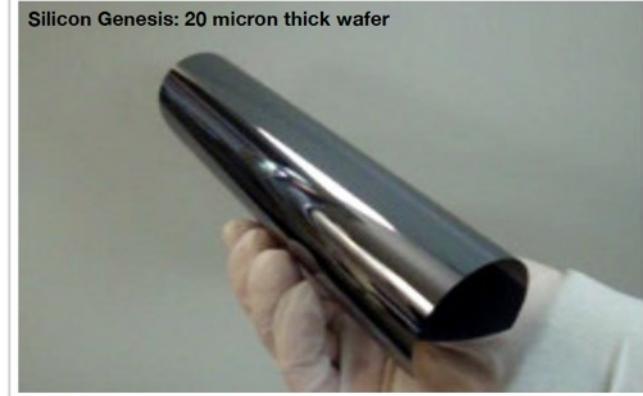
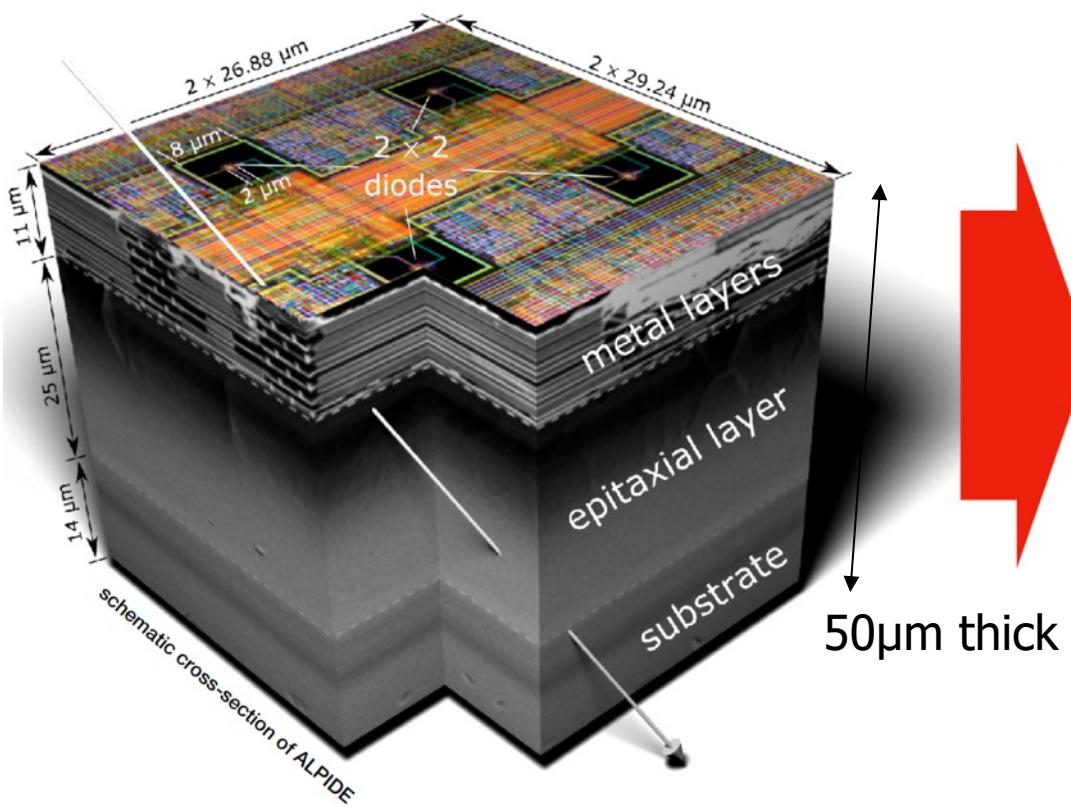
A Large Ion Collider Experiment

## On-surface commissioning



# ITS3

the idea (1): make use of the flexible nature of thin silicon

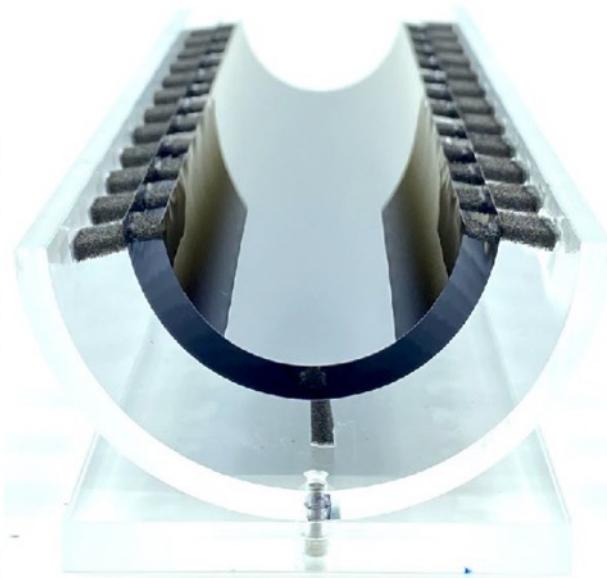


# Layer assembly

Layer 2



Layers 2+1



Layers 2+1+0



3-layer integration successful!

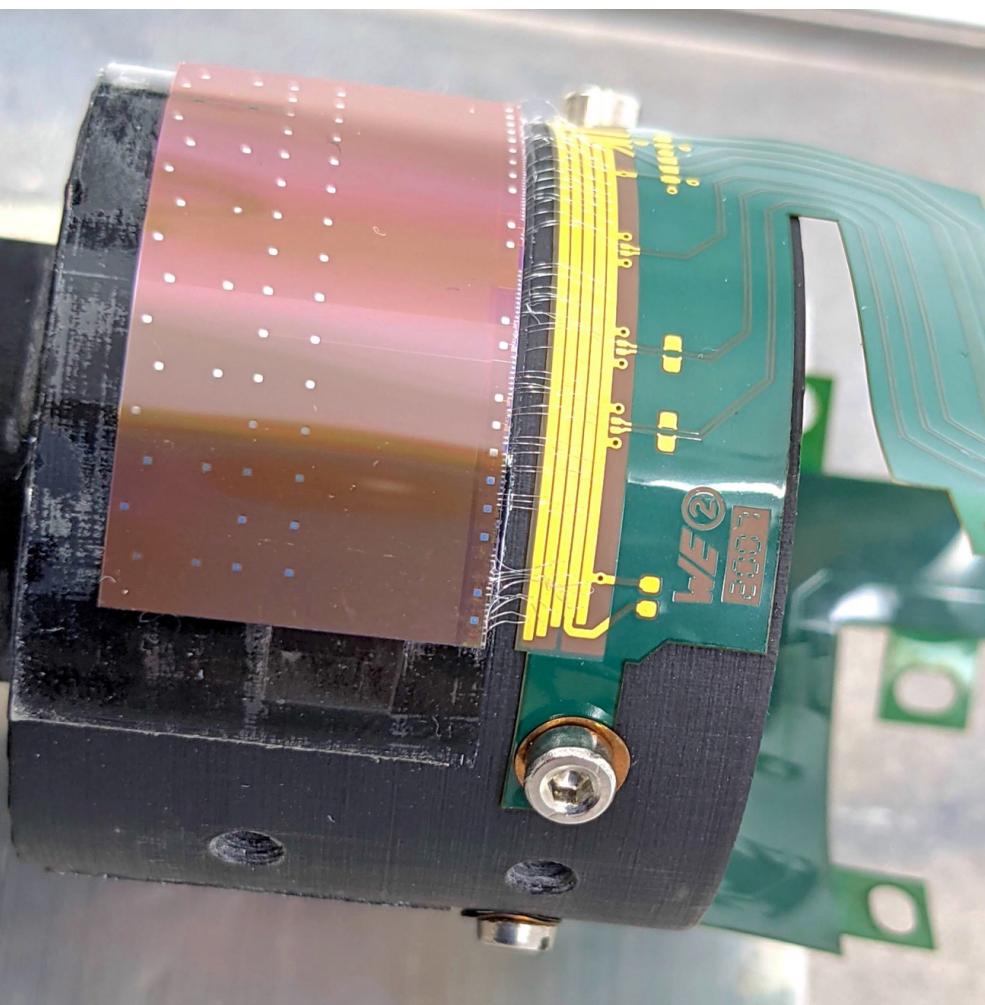
Magnus Mager (CERN) | ALICE ITS3 | CERN detector seminar | 24.09.2021 | 26

## *Development of Interconnects*

*Bonding on curved chips and circuits*

*Procedures, jigs, mandrels,  
integration*

*with bonding machine*

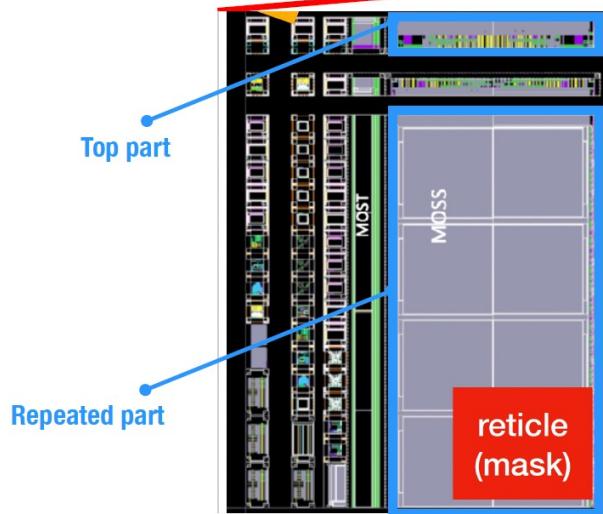


**ALICE**

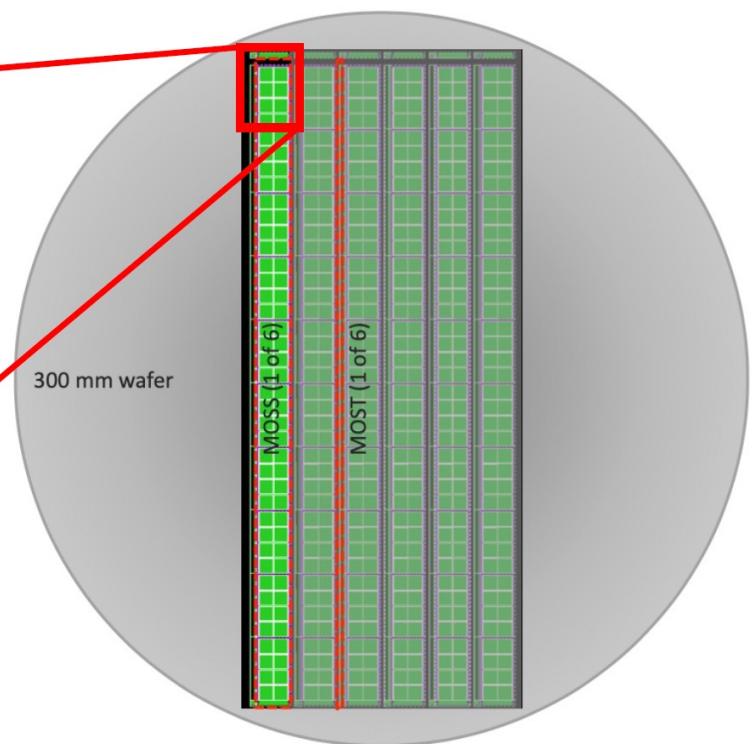
# Stitching – MOnolithic Stitched Sensor prototype

our target: ~280 x 94 mm → wafer scale sensor  
→ stitching needed: a true single piece of silicon

What we designed...



...what we want to fabricate



MOSS: 1.4 x 26 cm monolithic stitched sensor



CMS Experiment at the LHC, CERN  
Data recorded: 2016-Oct-14 09:56:16.733952 GMT  
Run / Event / LS: 283171 / 142530805 / 254

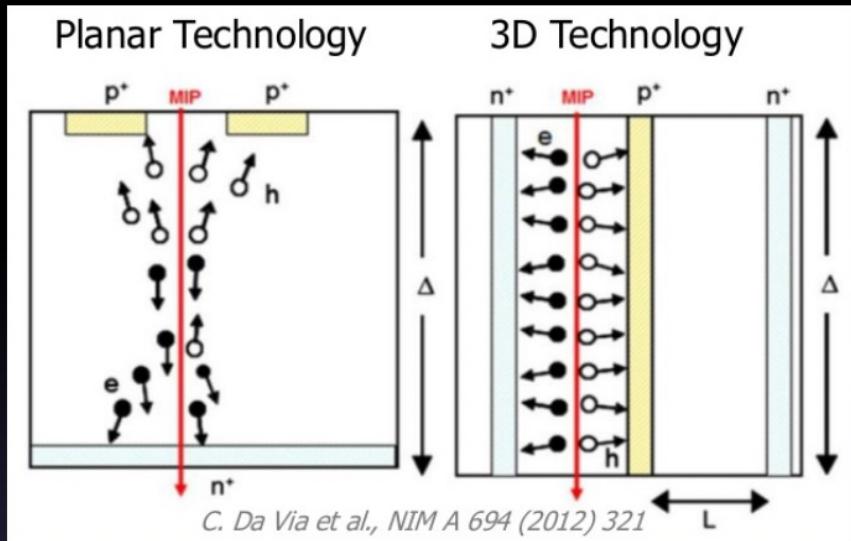


**First Tracker layer R~3cm ~0.7  
hits/BX/mm<sup>2</sup> = 2.8 GHz/cm<sup>2</sup>**



# 3D sensors

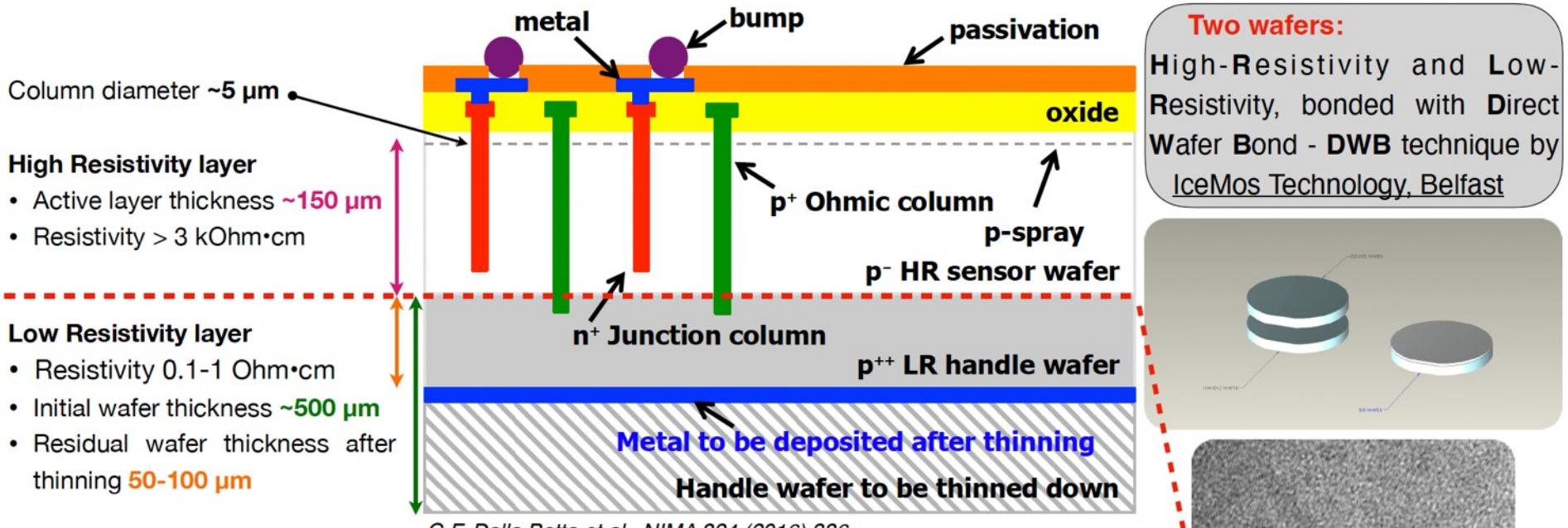
- Advantages
  - Decouple thickness from electrode distance
  - Lower depletion voltage, less power dissipation
  - Smaller drift distance, less trapping
- Disadvantage
  - More complex production process
  - Lower yield, higher costs
  - Higher capacitance (more noise)



- 3D is the most radiation hard technology to-day
- Similar performance than planar sensors, but less demanding in terms of bias voltage and cooling.
- For the HL-LHC we need :
  - More radiation hard (innermost layer(s),  $1-2E16 \text{ n}_{\text{eq}}/\text{cm}^2$ )
  - Smaller pixels (compatible with new readout chip,  $50 \mu\text{m} - 25 \mu\text{m}$ )
  - Thinner (reduce cluster size/merging,  $200 \mu\text{m} - 100 \mu\text{m}$ )

# 3D Silicon

## Silicon pixels: 3D FBK – single-side



Divide between layers →



High resolution TEM image of two bonded wafers cross section

### Columns produced by:

single-side Deep Reactive Ion Etching - **DRIE** process optimised by **FBK** (less expensive than double-side process)

# CMS Pixel upgrade for HL-LHC

- 150  $\mu\text{m}$  bulk thickness, 25x100  $\mu\text{m}^2$  pixels cells everywhere
- Planar n-in-p sensors:

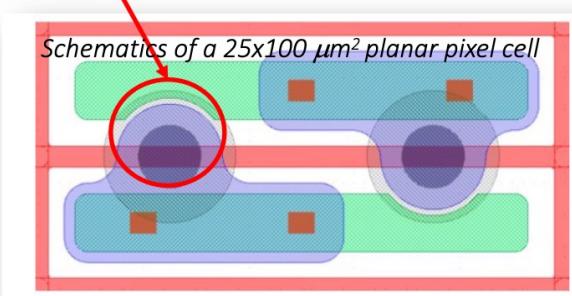
  - Bias up to 600V and spark protection between ROC and sensors
  - Three vendors qualified in the Market Survey, Tender being closed in these days
  - Bump bonding pattern is 50x50  $\mu\text{m}^2$
  - Cross-talk issues studied and minimized (i.e. bitten implant on planar)

- 3D sensors for barrel L1

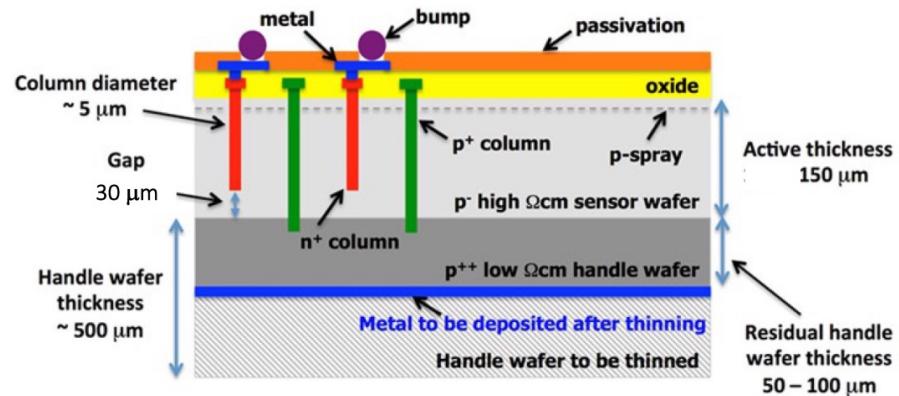
  - Short drift distance  $\sim 50 \mu\text{m}$  (3D) vs 150  $\mu\text{m}$  (Planar)
  - Slim edges (150  $\mu\text{m}$ ) vs planar ( $\sim 450 \mu\text{m}$ )  $\rightarrow$  smaller dead zone
  - Sensors produced at FBK on 6" wafers and CNM on 4" wafers

## Pixel sensors

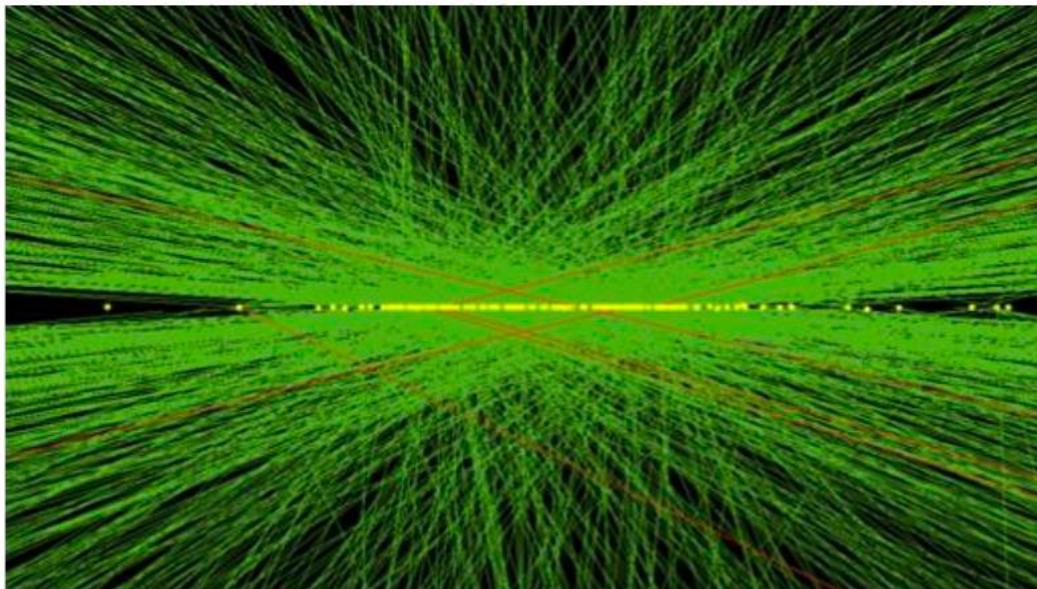
No  $n^+$  implant under metal to reduce x-talk



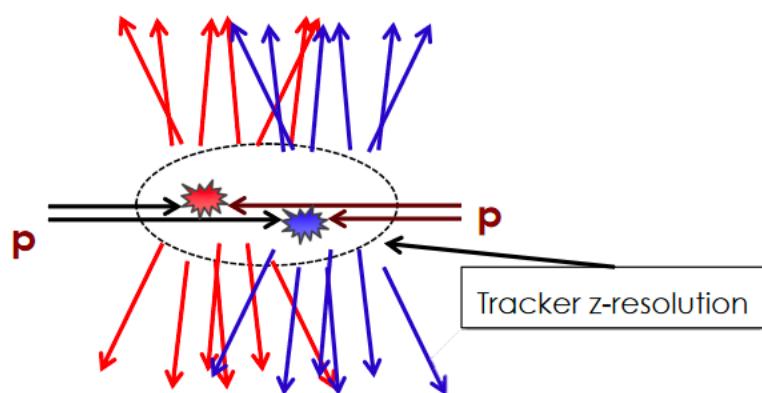
Structure of a 3D sensor – FBK process



# 4D Detectors ( $x,y,z$ and time)



Tracking z-resolution can be larger than vertex-separation: Ambiguous Track-to-vertex association



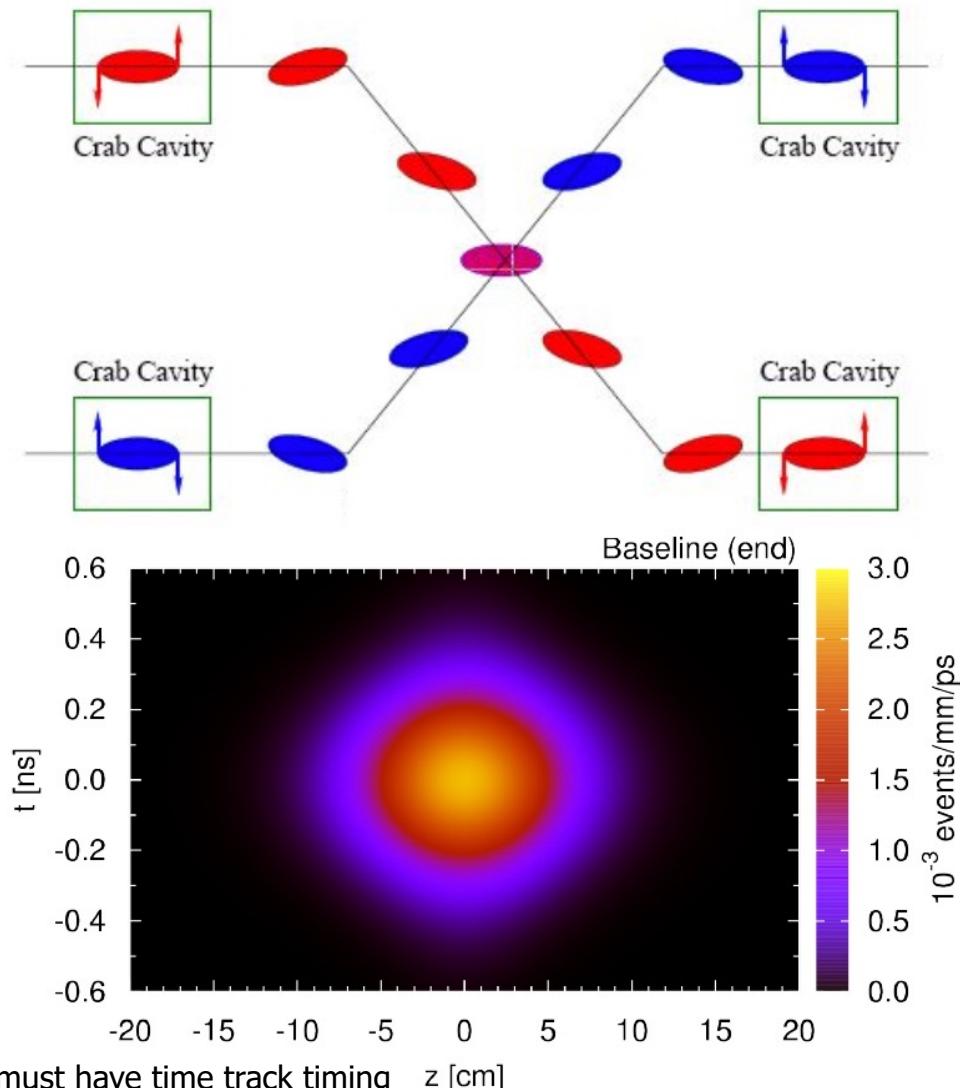
Timing at each point along the track:

- Massive simplification of pattern recognition
- Faster tracking algorithm
- Even in very dense environments by using only “time compatible points »

N. Cartiglia, INFN, Hiroshima Conference 2017

# The Time Structure of Crossing Bunches

- In addition to extent in z, there is an extent of the bunch crossing in time
- For nominal HL-LHC optics the core of the bunches pass through each other in ~300 ps
- When bunches overlap entirely, achieve maximum spread in z and maximum pileup density
- Normally an experiment only sees the integral of this distribution over time



Need to discriminate vertices with time spread of ~180 ps, must have time track timing resolution significantly smaller than beamspot spread so that tracks cluster in time.

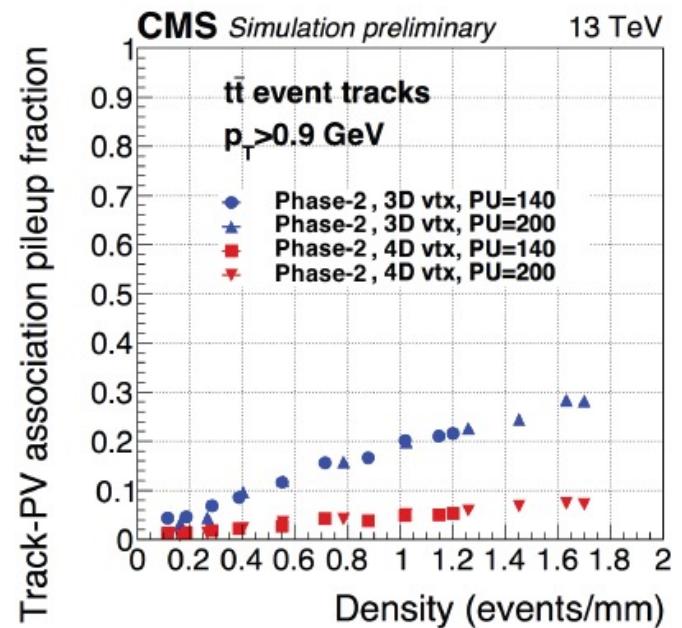
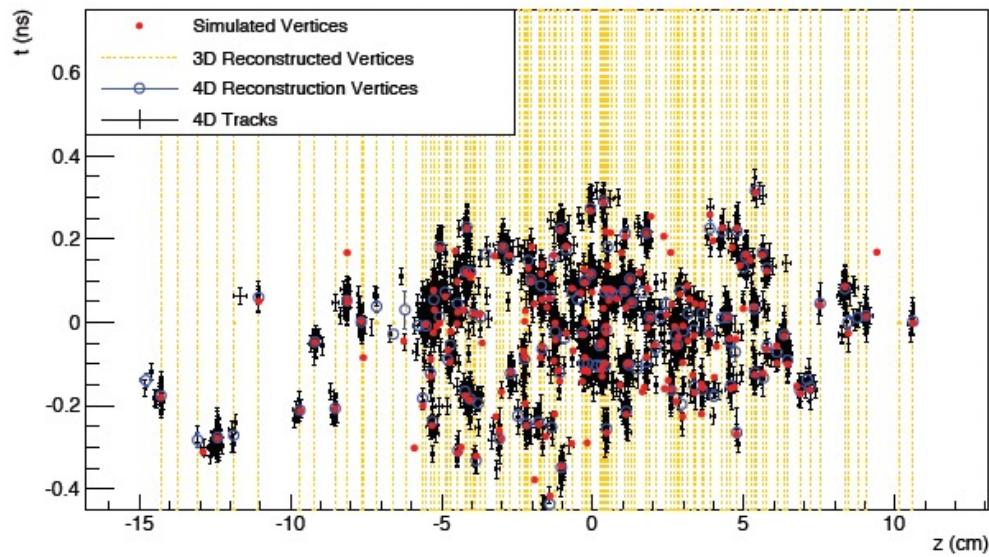
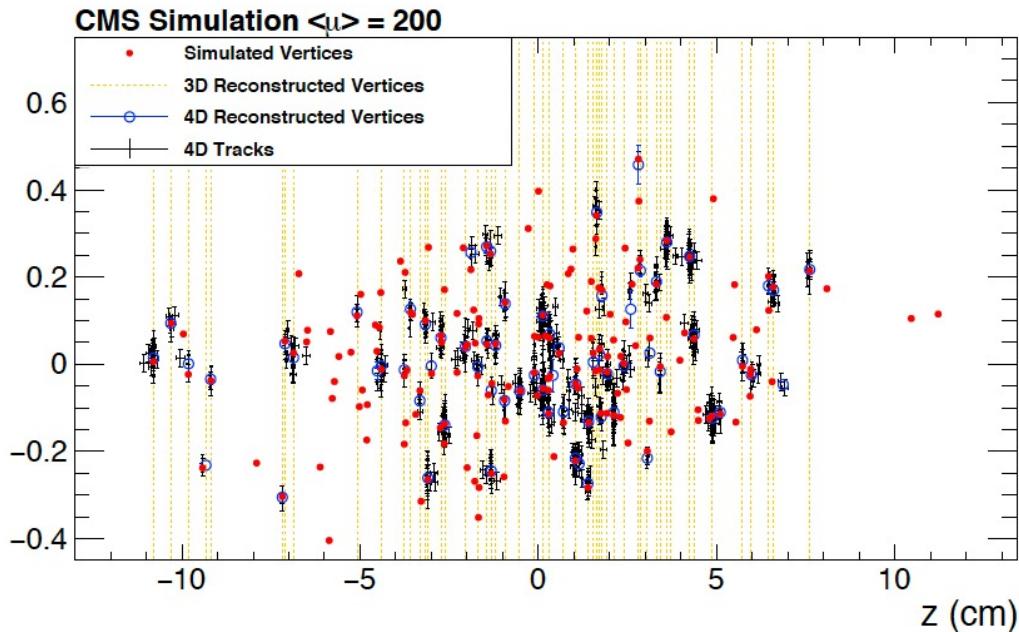


Figure 1.2: Left: Simulated and reconstructed vertices in a 200 pileup event assuming a MIP timing detector covering the barrel and endcaps. The vertical lines indicate 3D-reconstructed vertices, with instances of vertex merging visible throughout the event display. Right: Rate of tracks from pileup vertices incorrectly associated with the primary vertex of the hard interaction normalized to the total number of tracks in the vertex.

# Using the Time-at-vertex in Reconstruction

- With the track-time at distance of closest approach it becomes possible to cluster tracks in 2D into vertices
- This significantly increases the distance between vertices and hence makes them harder to confuse
- Expect 5-10x improvement in vertex merging rate (achieved 9x)
- Expect 3-5x reduction in track-vertex association false positives (achieve ~3x)

$t$  (ns)



CMS Simulation

$\langle\mu\rangle$	4D Merged Vertex Fraction	3D Merged Vertex Fraction	Ratio of 3D/4D
50	0.5%	3.3%	6.6
200	1.5%	13.4%	8.9

# Crystals

Lutetium-yttrium orthosilicate crystals activated with cerium (LYSO:Ce) read out with SiPMs. The

The barrel timing layer will cover the pseudorapidity region up to  $|h| = 1.48$  with a total active surface of about 40 m<sup>2</sup>.

The fundamental detecting cell will consist of a thin LYSO:Ce crystal with about 12→12 mm<sup>2</sup> cross-section coupled to a 4x4 mm<sup>2</sup> SiPM.

The crystal thickness will vary between about 3.7 mm ( $|h| < 0.7$ ) and 2.4 mm ( $|h| > 1.1$ ),

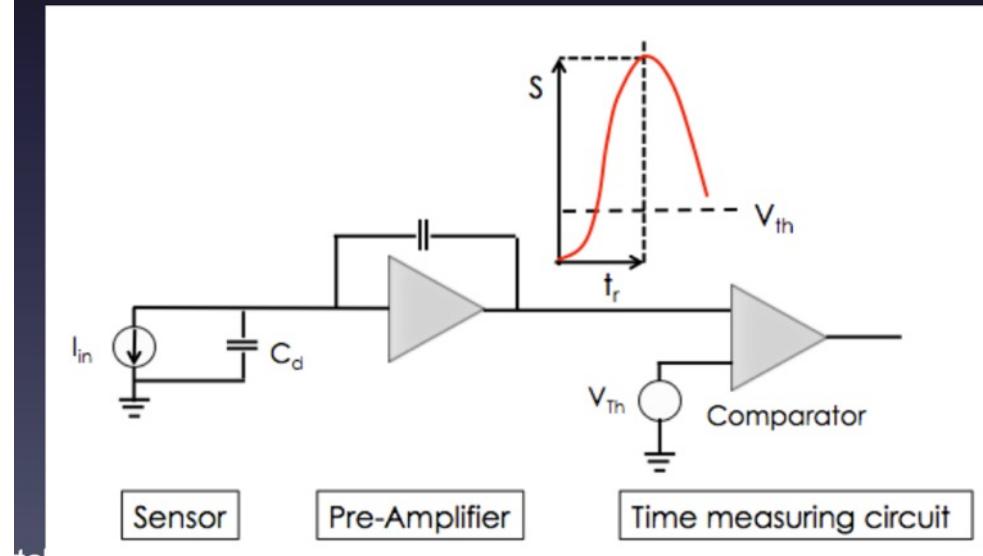
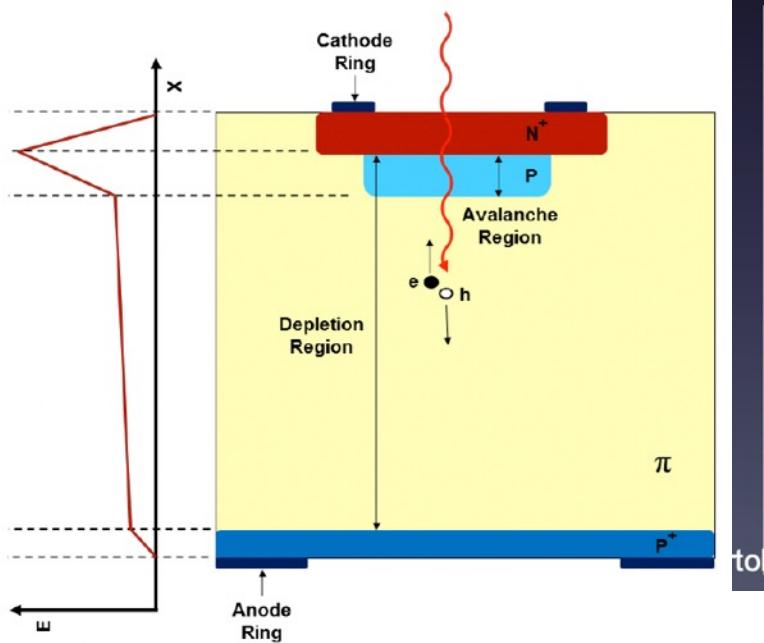


Figure 2.4: Top left: Set of  $11 \times 11 \times 3$  mm<sup>3</sup> LYSO:Ce crystals with depolished lateral faces, before and after Teflon wrapping. Bottom left:  $6 \times 6$  mm<sup>2</sup> HPK SiPMs glued on LYSO crystals. Right: Crystal+SiPM sensors plugged on the NINO board used for test beam studies.

# LGADs

Nicolo Cartiglia

- Achieve  $\approx 10$  ps timing resolution with Si detectors using charge amplification with Low-Gain Avalanche Detectors



**Lots of R&D, DC and AC coupled, chip design, test beams**

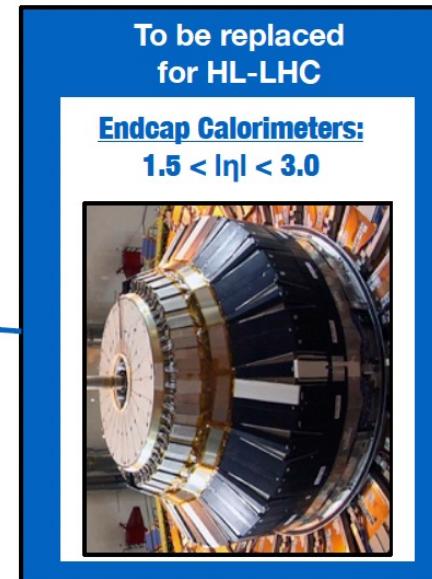
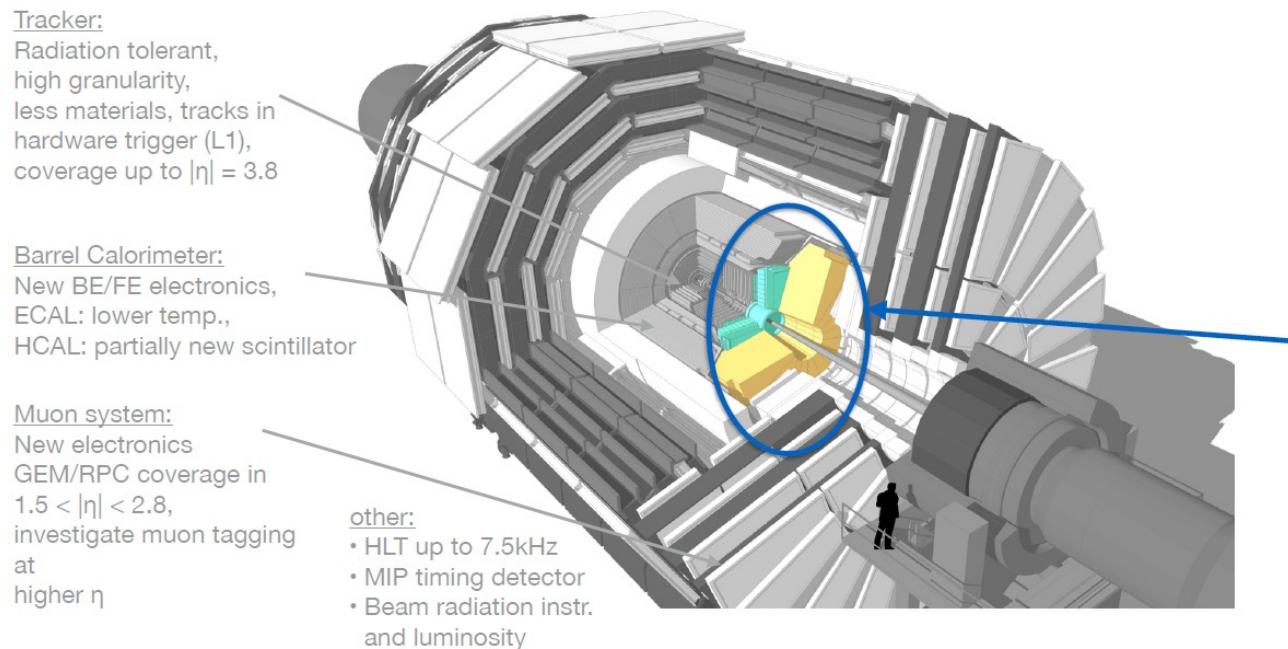
**Both ATLAS and CMS but also for Higgs factories etc**

# HL-LHC necessitates upgrades to the CMS detector

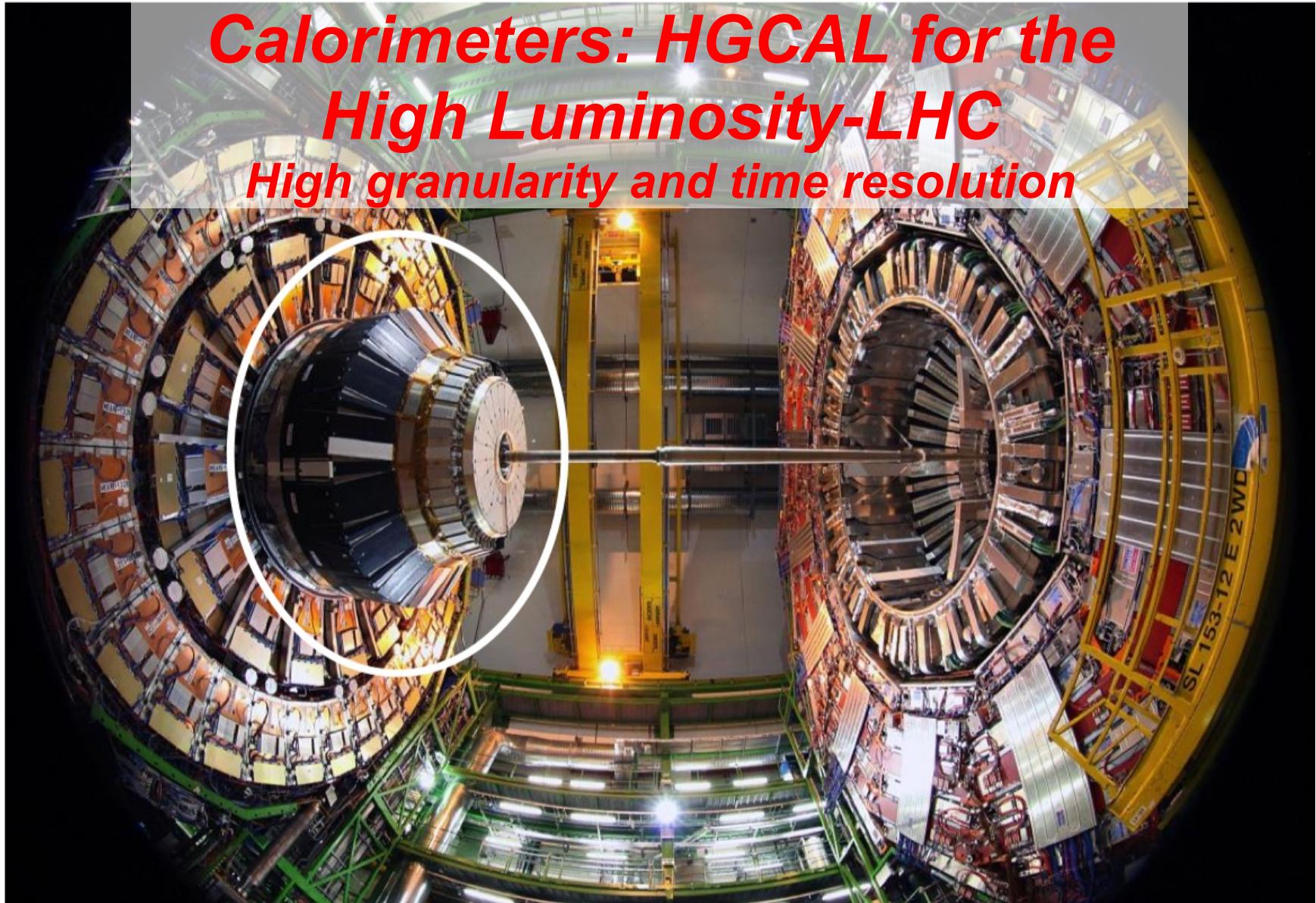
3

Experimental challenges	LHC	HL-LHC	General mitigation strategy
<ul style="list-style-type: none"> <li>inst. luminosity</li> <li>detector irradiation</li> <li>pile-up interactions</li> </ul>	$2 \times 10^{34} \text{ s}^{-1} \text{ cm}^{-2}$ $O(10^{14} \text{ neq/cm}^2)$ $O(40)$	up to $7.5 \times 10^{34} \text{ s}^{-1} \text{ cm}^{-2}$ $>O(10^{15} \text{ neq/cm}^2)$ 140-200	<ul style="list-style-type: none"> <li>improved trigger &amp; computing</li> <li>radiation-tolerant sensors &amp; electronics</li> <li>timing and increased granularity</li> </ul>

## Compact Muon Solenoid (CMS) HL-LHC Upgrades



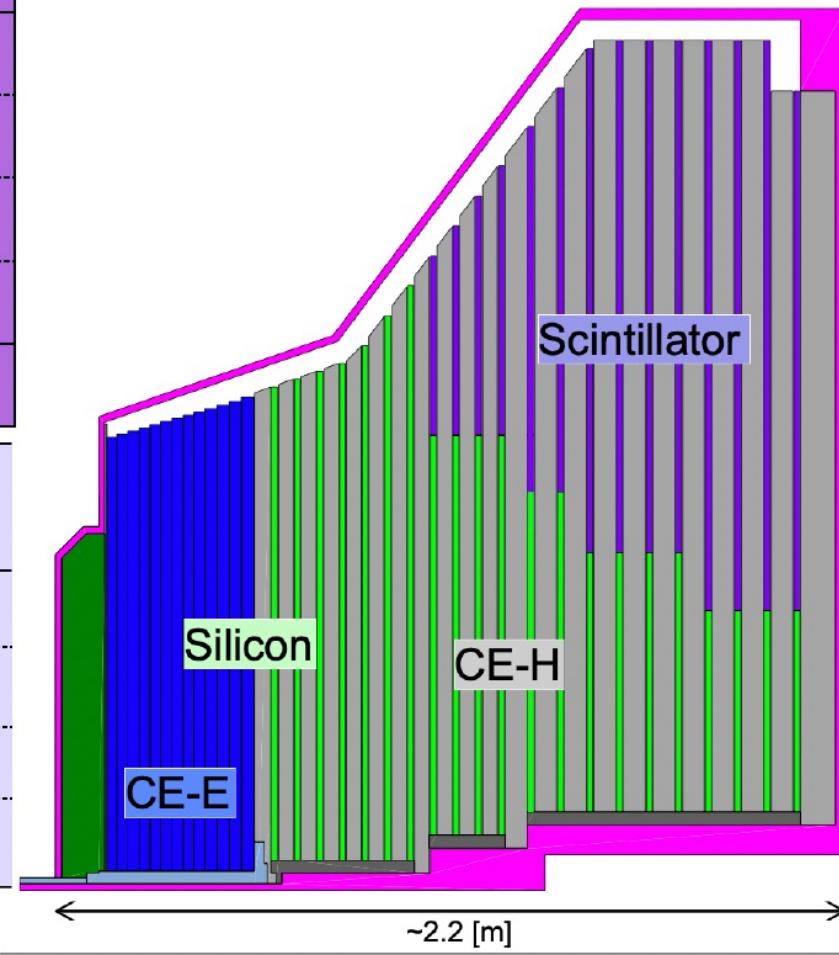
# Calorimeters: HGCAL for the High Luminosity-LHC *High granularity and time resolution*



# Technology Choices

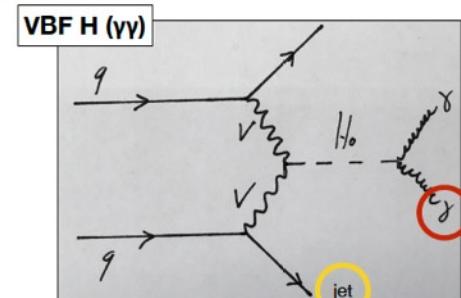
Both Endcaps	Silicon	Scintillator
Area	$\sim 620 \text{ m}^2$	$\sim 370 \text{ m}^2$
Channel Size	$0.5 - 1.2 \text{ cm}^2$	$4 - 30 \text{ cm}^2$
# Channels	$\sim 6 \text{ M}$	$\sim 240 \text{ k}$
# Modules	$\sim 27000$	$\sim 4000$
Op. Temp.	$-30 \text{ C}$	$-30 \text{ C}$

Per Endcap	CE-E	CE-H Si Si+Scint
Absorber	Pb, CuW, Cu	Stainless steel, Cu
Depth	$27.7 X_0$	$10 \lambda$
Layers	26	7      14
Weight	23 t	205 t



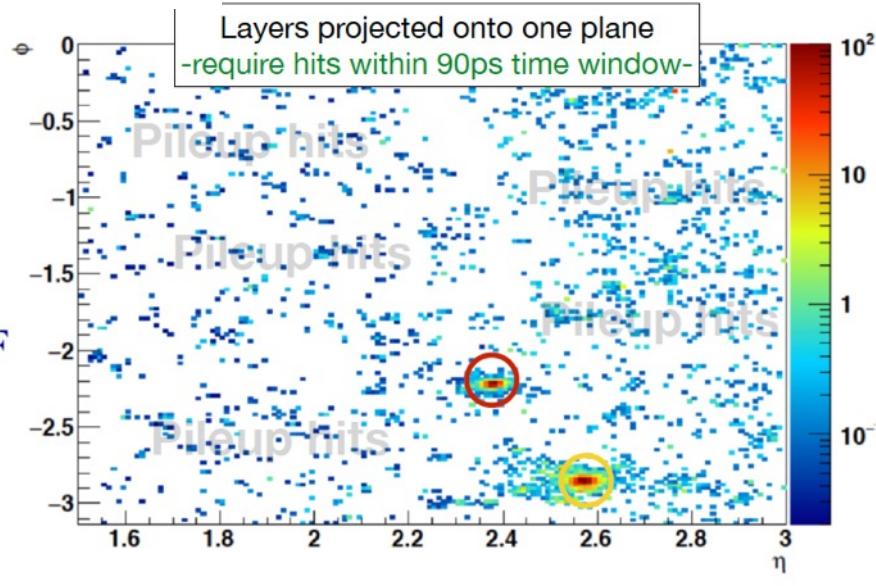
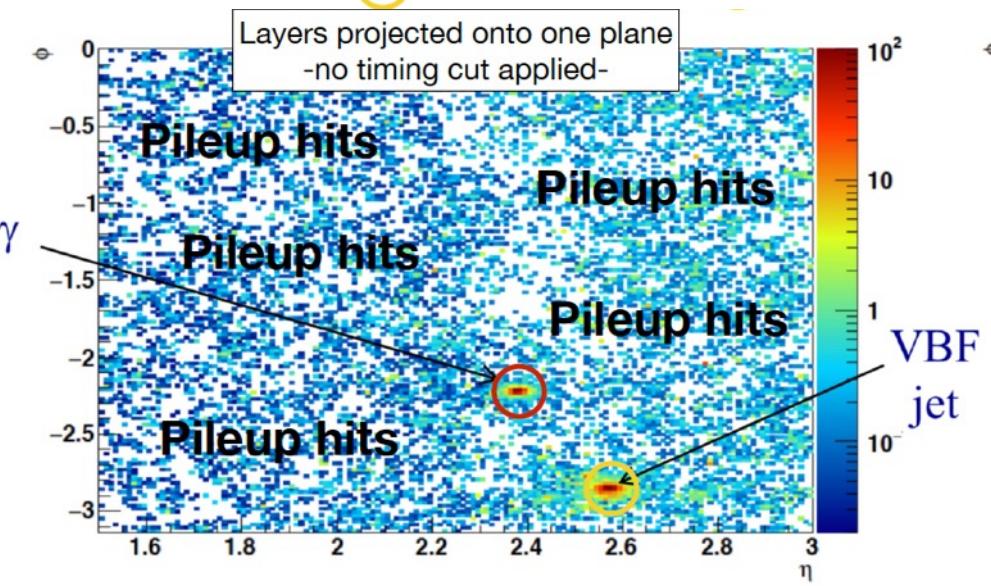
- Dissipated power  $\sim 250 \text{ kW}$
- Removed with two-phase CO<sub>2</sub> cooling operated at  $-35 \text{ C}$
- Geometry slightly adjusted since the TDR release

# Idea: HGCAL will be 3D imaging calorimeter **with timing capabilities** 8



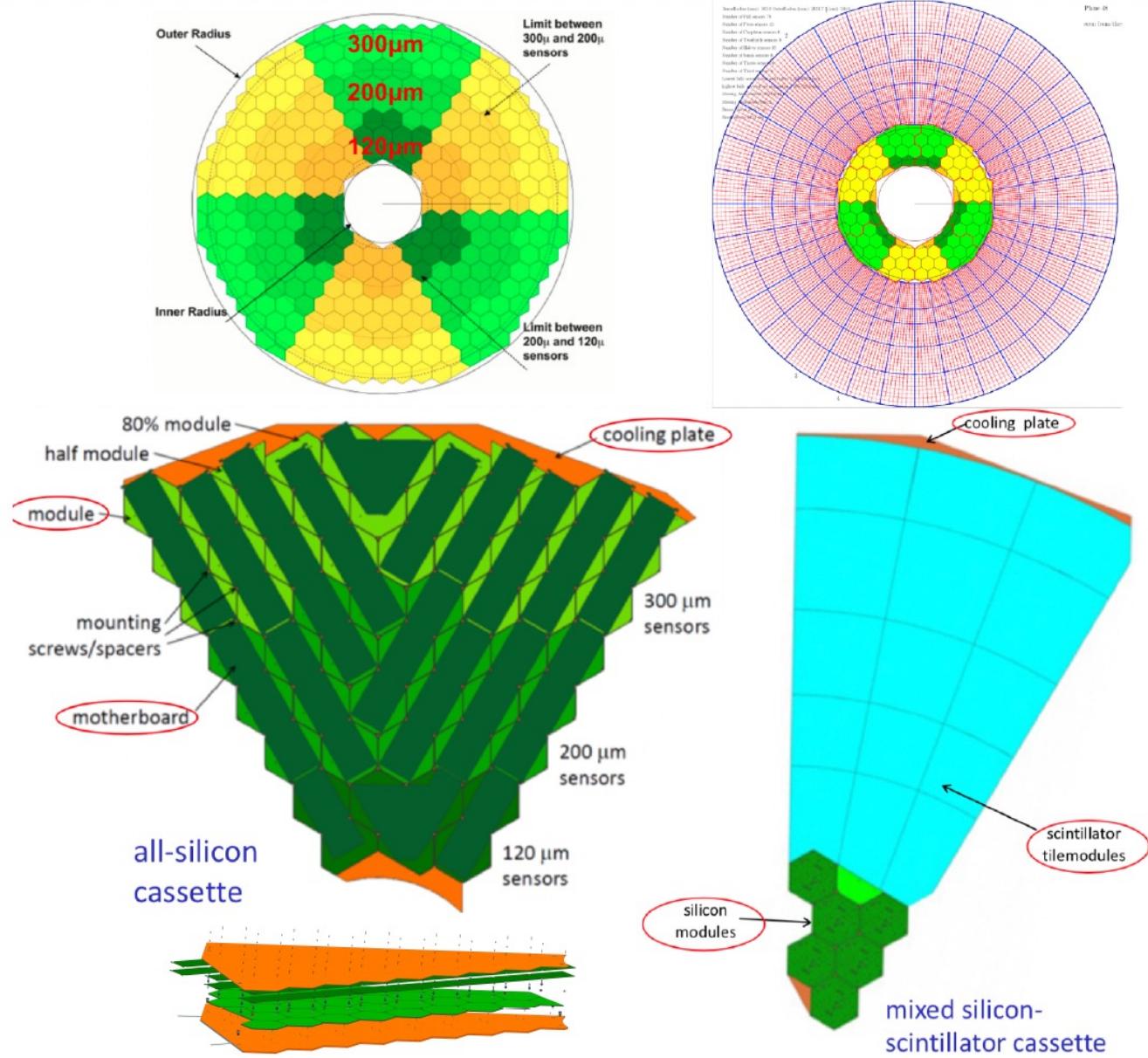
+ 200 PU

- Plots show cells with  $E > \sim 3.5$  MIPs, projected to the front face of the endcap calorimeter
- Concept: identify high-energy clusters, then make timing cut to retain hits of interest
- Design HGCAL to obtain a  $\sim 30\text{ps}$  timing measurement for multi-MIP energy deposits



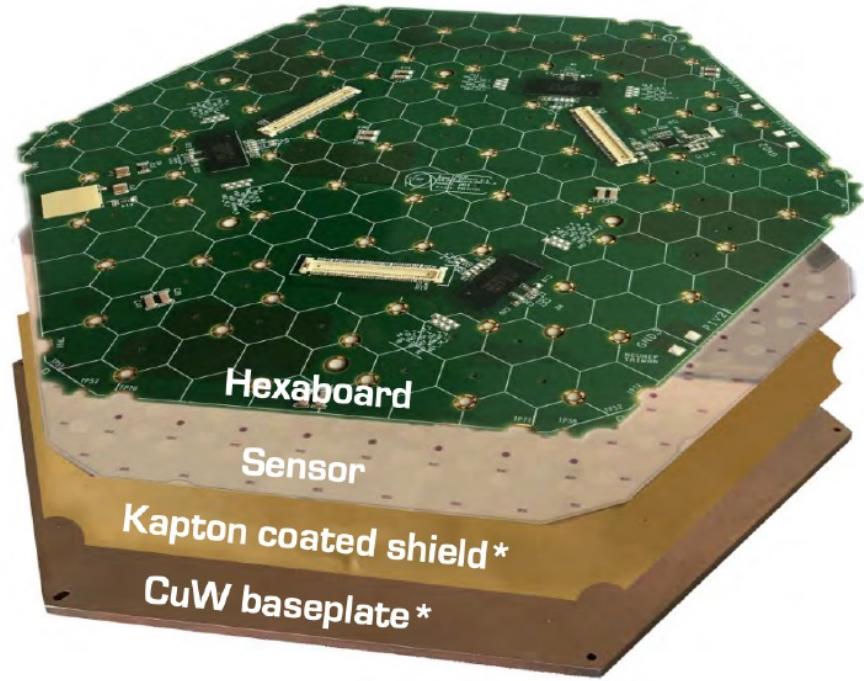
# Lateral Structure, Cassettes

- Silicon and scintillator modules assembled into cassettes
- Supported and cooled by copper cooling plate
- Data from modules collected by motherboards
- Cassettes house all services and DC2DC converters

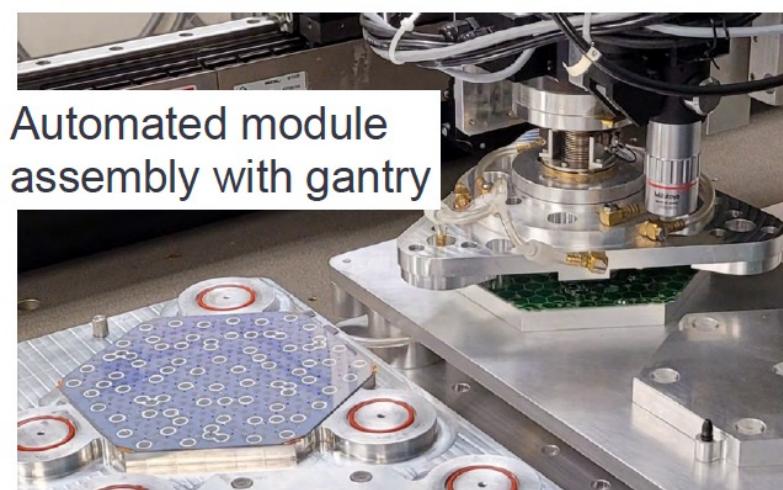


# Silicon Modules

- Glued stack of baseplate, sensor and readout hexaboard
- baseplates are made of CuW in CE-E, PCB in CE-H
- Relative alignment within ~50um achieved with gantry based automated assembly
- Electrical connections are done with wire-bonds

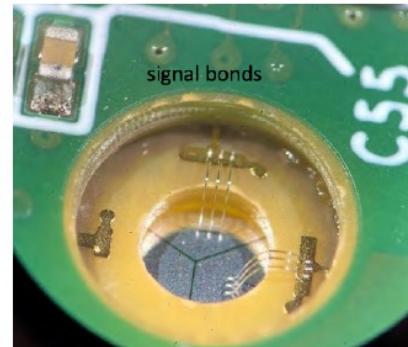


\* In CE-H, PCB baseplate with laminated Kapton™

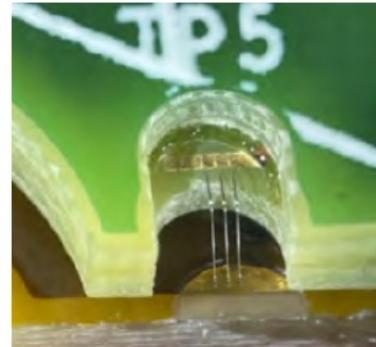


Automated module assembly with gantry

signal bonds



shield bonds



backside HV bonds



# ***HGCAL for the High Luminosity-LHC is a very complex instrument***

# *High purity segmented Ge-detectors for Nuclear physics*

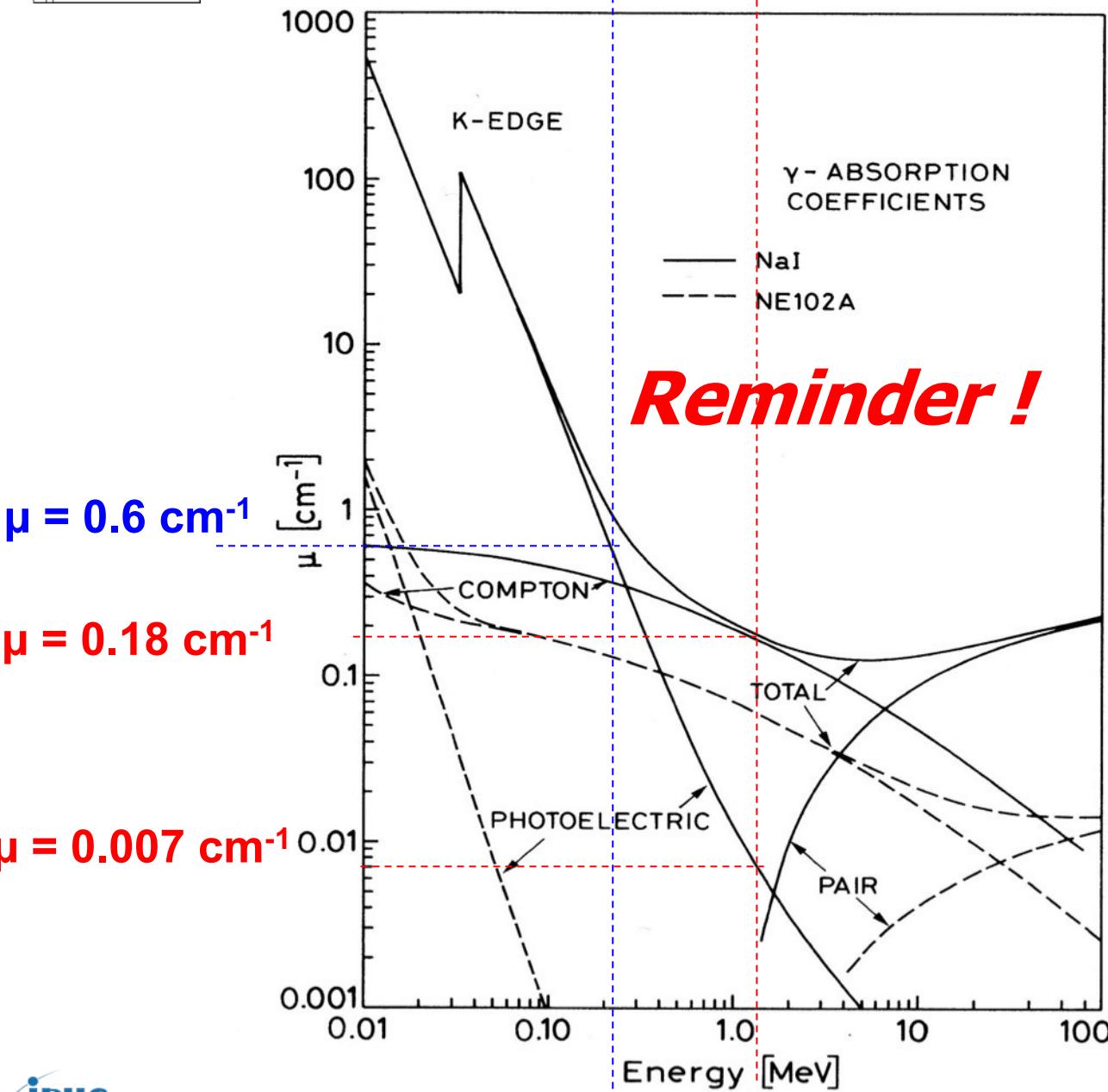


Photo-electric effect

Absorption of  $\gamma$

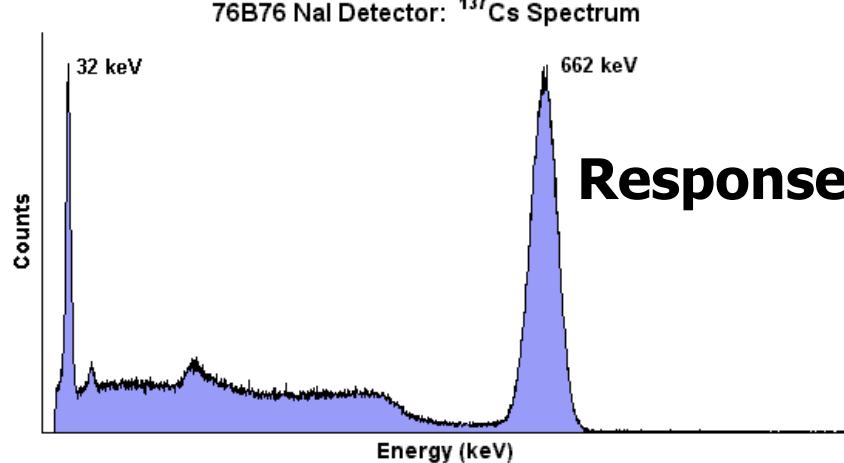
Compton scattering

scattering  $\gamma \rightarrow \gamma'$

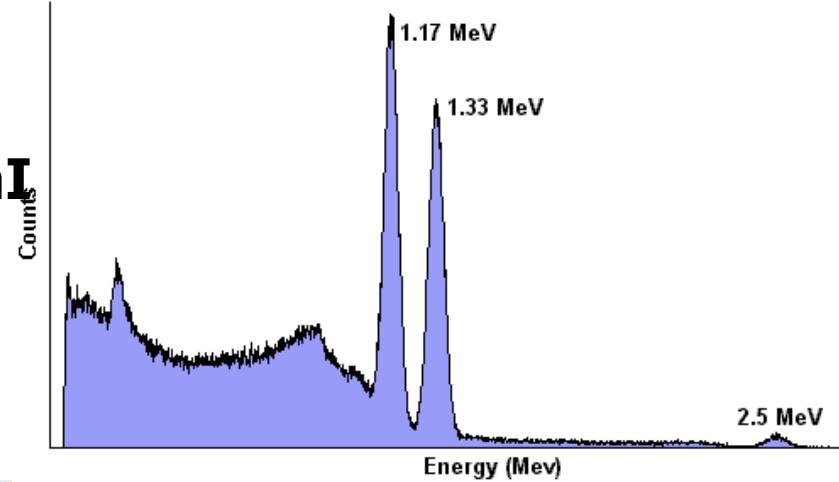
Creation of  $(e^+e^-)$   
pairs

Absorption of  $\gamma$

76B76 NaI Detector:  $^{137}\text{Cs}$  Spectrum

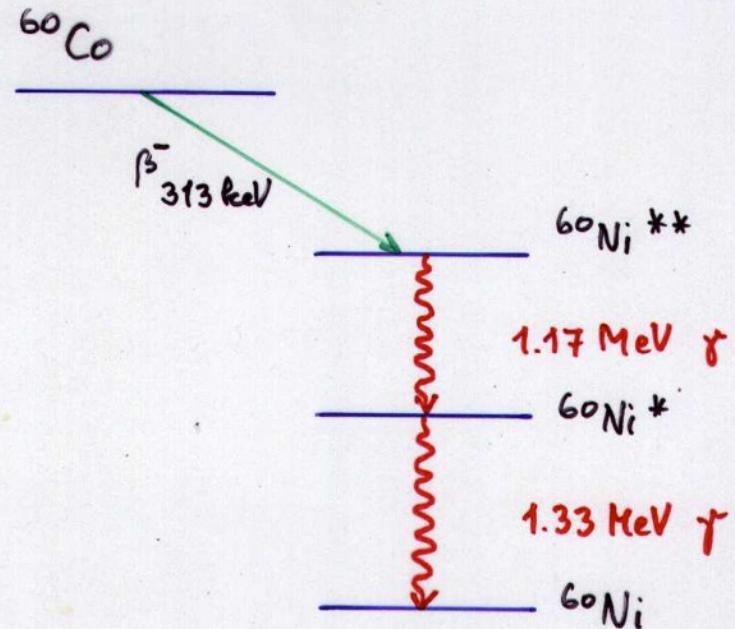
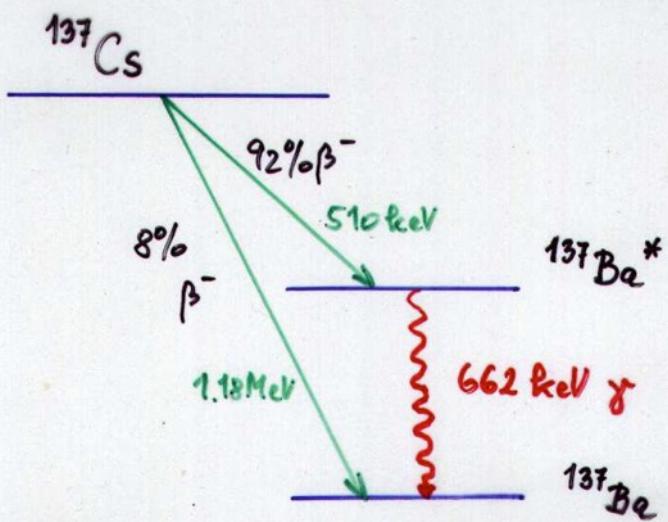


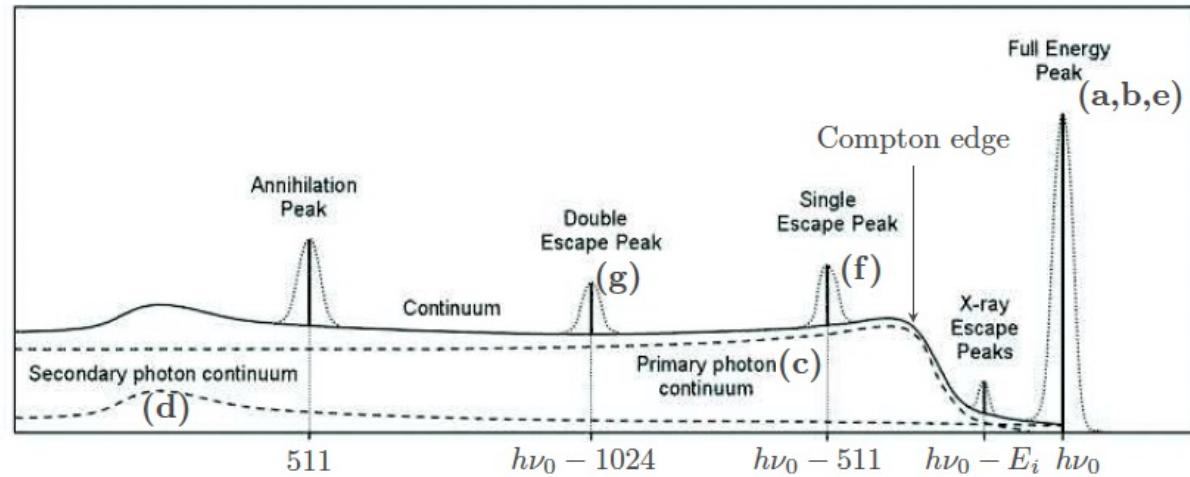
76B76 NaI Detector:  $^{60}\text{Co}$  Spectrum



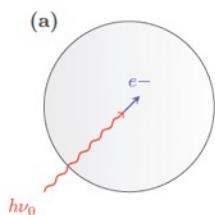
## Response of NaI

Univ. of Tennessee , Dept. of Physics  
& Astronomy

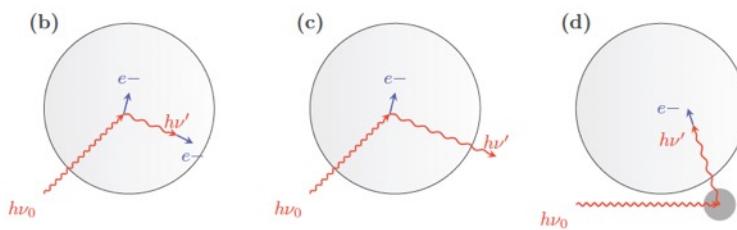




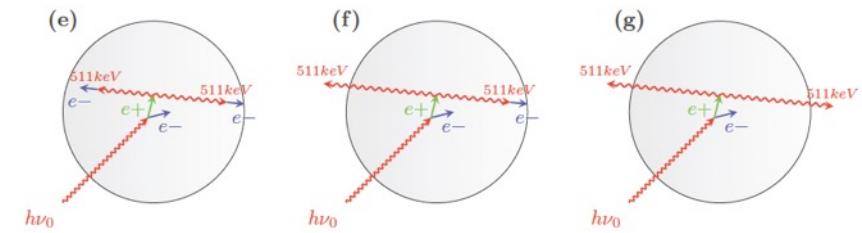
#### PHOTO-ELECTRIC EFFECT

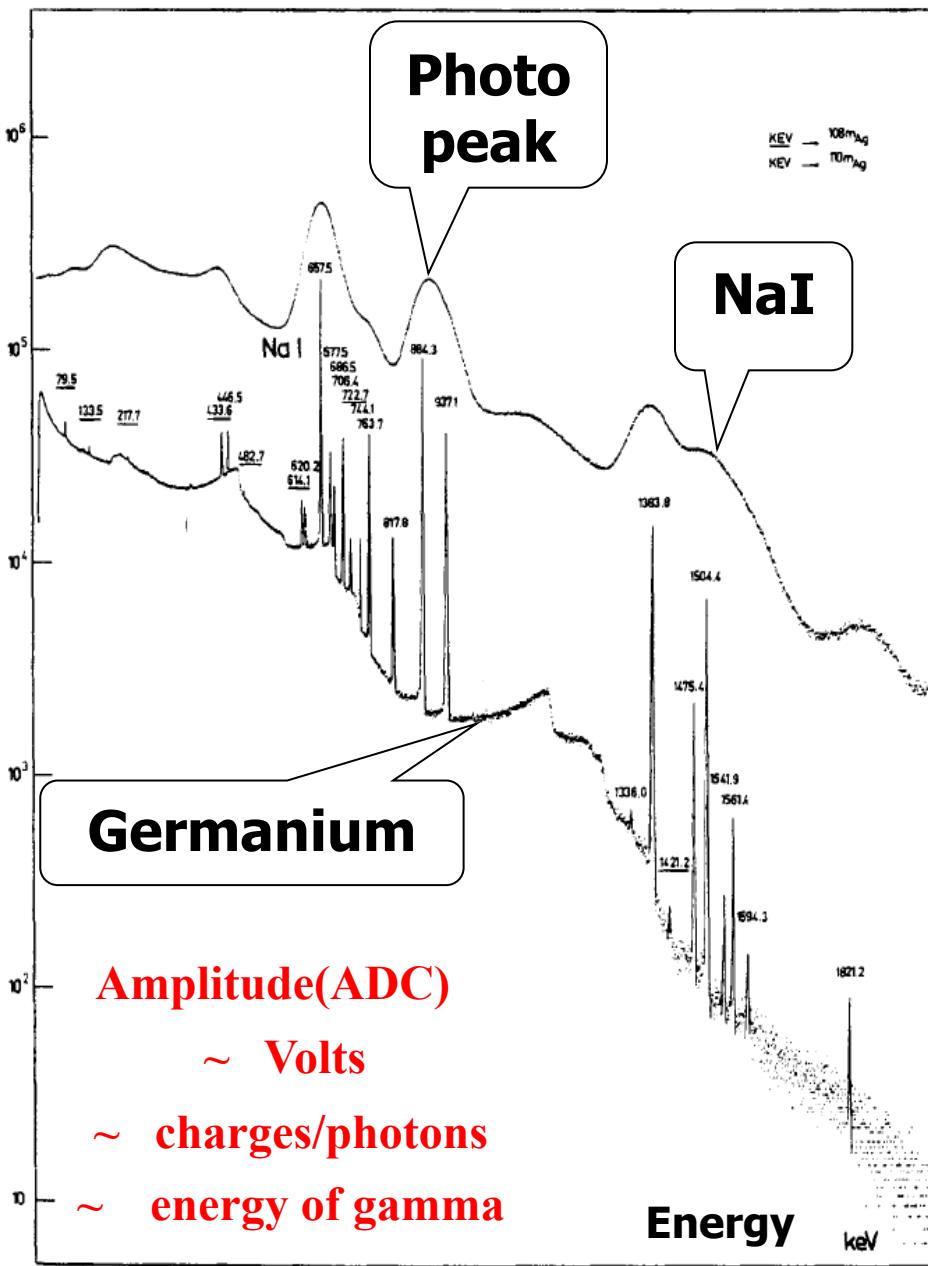


#### COMPTON SCATTERING



#### PAIR CREATION





**Large volume semi-conductor detector**

# Semi-conductor detectors

Material	E <sub>g</sub> [eV]	w [eV]	Mobility (velocity/E)		τ <sub>e</sub> [s]	τ <sub>h</sub> [s]	density	Z [a.m.u]
			μ <sub>e</sub> [cm <sup>2</sup> /Vs]	μ <sub>h</sub> [cm <sup>2</sup> /Vs]				
C (diamond)	5.5	13	1800	1200	2 10 <sup>-9</sup>	2 10 <sup>-9</sup>	3.515	6
Si	1.12	3.61	1350	480	5 10 <sup>-3</sup>	5 10 <sup>-3</sup>	2.33	14
Ge	0.67	2.98	3900	1900	2 10 <sup>-5</sup>	2 10 <sup>-5</sup>	5.32	32
GaAs	1.42	4.70	8500	450	5 10 <sup>-8</sup>	5 10 <sup>-8</sup>	5.32	31,33
CdTe	1.56	4.43	1050	100	1 10 <sup>-6</sup>	1 10 <sup>-6</sup>		48,52
HgI <sub>2</sub>	2.13	4.20	100	—	1 10 <sup>-6</sup>	2 10 <sup>-6</sup>		53,80

$$\frac{dN}{N} = \frac{1}{\sqrt{N}} ; \quad E \sim N; \quad N = \text{numb. of (e,h)})$$

Parameters Values for Materials Used in Fabricating Semiconductor Radiation Sensors

W.Dulinski

[3]

# Inverse Polarisation

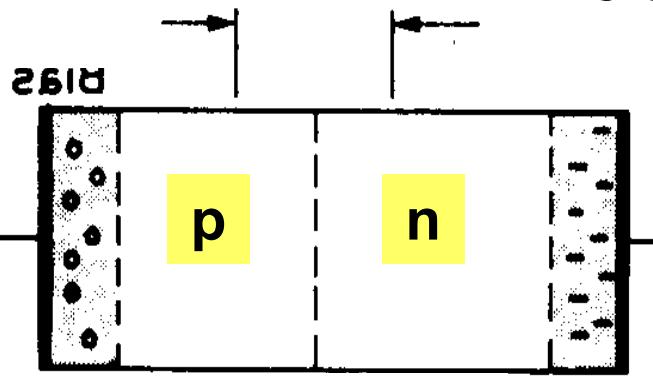
Holes move to « - »

$$d|_{V_{bias}} = x_n + x_p = \sqrt{\frac{2\epsilon(\phi_0 + V_{bias})}{e} \frac{(N_A + N_D)}{N_A N_D}}$$

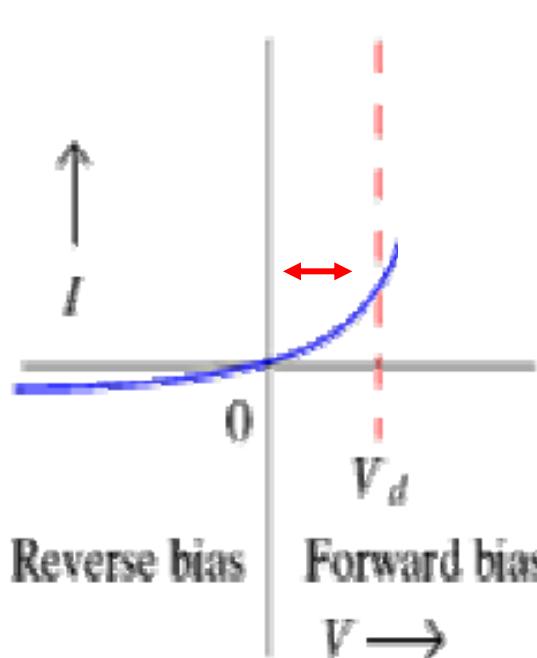
electrons move to contact "+"

$$N_A \gg N_D$$

depletion in n-type



$I_c$



Reverse bias

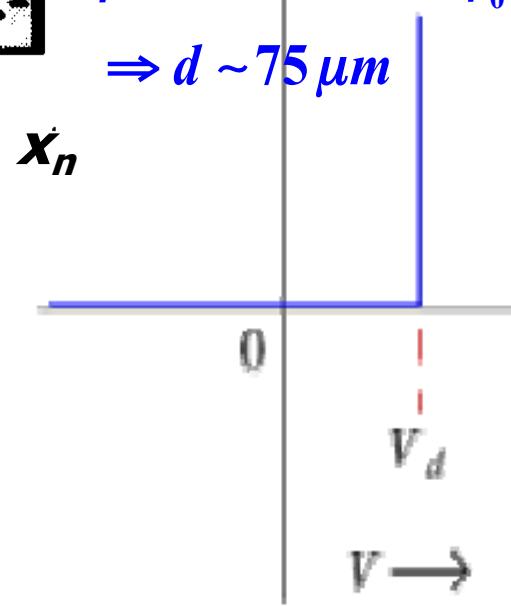
Forward bias

$V \rightarrow$

Real Diode

$d$   
Depletion zone  
 $-x_p$        $x_n$

Forward bias  
— → —  
Reverse bias  
— ← — +



'Ideal' Diode

# Large volume detectors

- Depletion zone

$$d|_{V_{bias}} = x_n + x_p = \sqrt{\frac{2\epsilon(\phi_0 + V_{bias})}{e} \frac{(N_A + N_D)}{N_A N_D}}$$

$$N = N_A \ll N_D; \phi_0 \ll V_{bias}$$

$$d|_{V_{bias}} = \sqrt{\frac{2\epsilon V_{bias}}{eN}} ; N = N_A \text{ ou } N_D = \text{net impurity of material}$$

$$N = 10^{13} \text{ atoms/cm}^3; V_{bias} = 3000 \text{ Volt};$$

$$d|_{V_{bias}=3000 \text{ Volt}} = 2.2 \text{ mm}$$

- High purity :

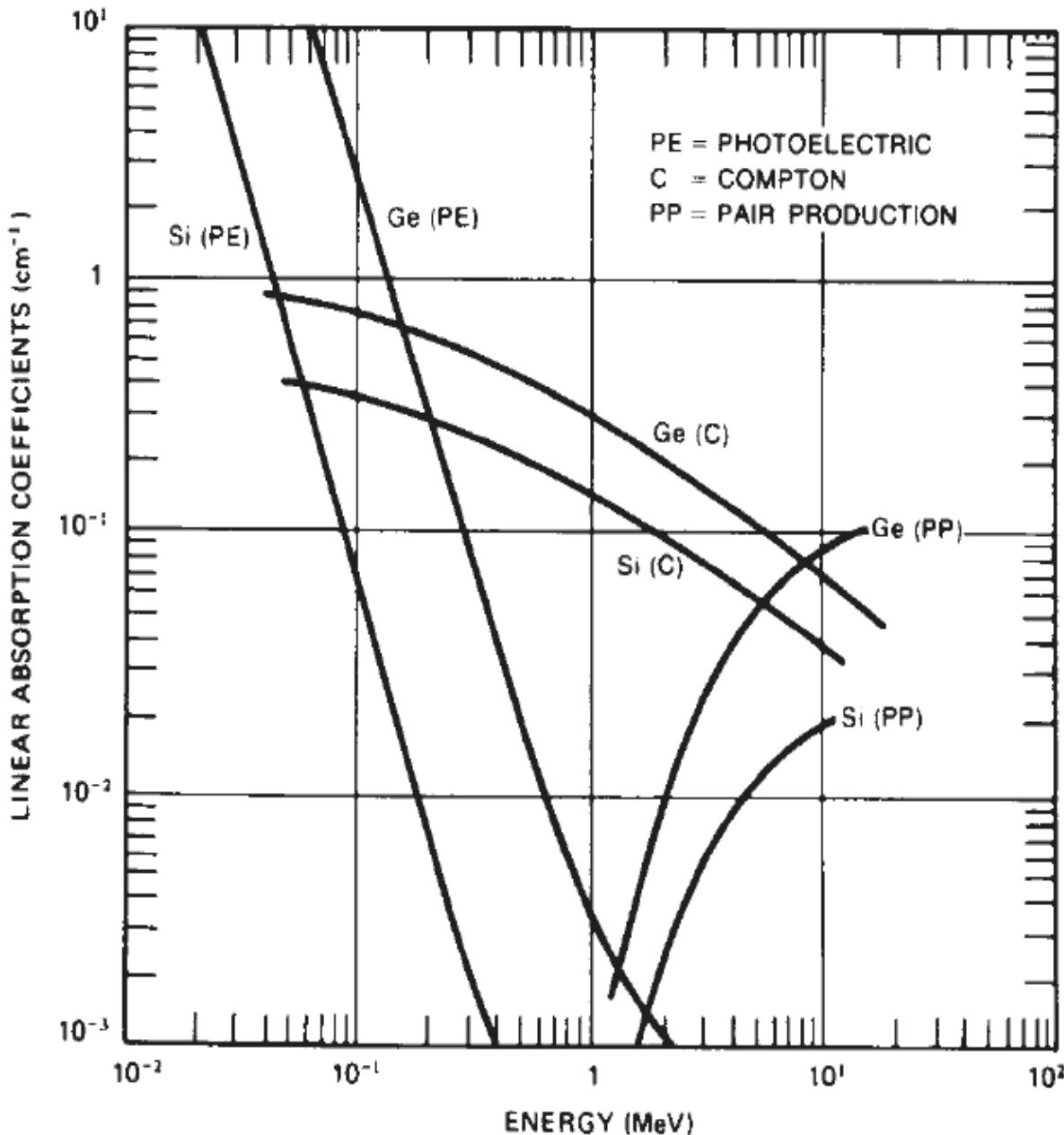
$$N_A \text{ ou } N_D = 10^{10} \text{ atoms/cm}^3; V_{bias} = 1000 \text{ Volt}; \epsilon = 16 \cdot \epsilon_0;$$

$$\epsilon_0 = 8.85 \cdot 10^{-12} \text{ F/m}; F = \text{Coulomb/Volt}; e = 1.6 \cdot 10^{-19} \text{ Coulomb}$$

$$d|_{V_{bias}=1000 \text{ Volt}} = 1.8 \text{ cm}$$

$$d|_{V_{bias}=2000 \text{ Volt}} = 2.5 \text{ cm}$$

$$d|_{V_{bias}=3000 \text{ Volt}} = 3.1 \text{ cm}$$



## High Purity Germanium

### Energy measurement of gammas

( $|N_A - N_D| \cong 10^{10} \text{ cm}^{-3}$ ):

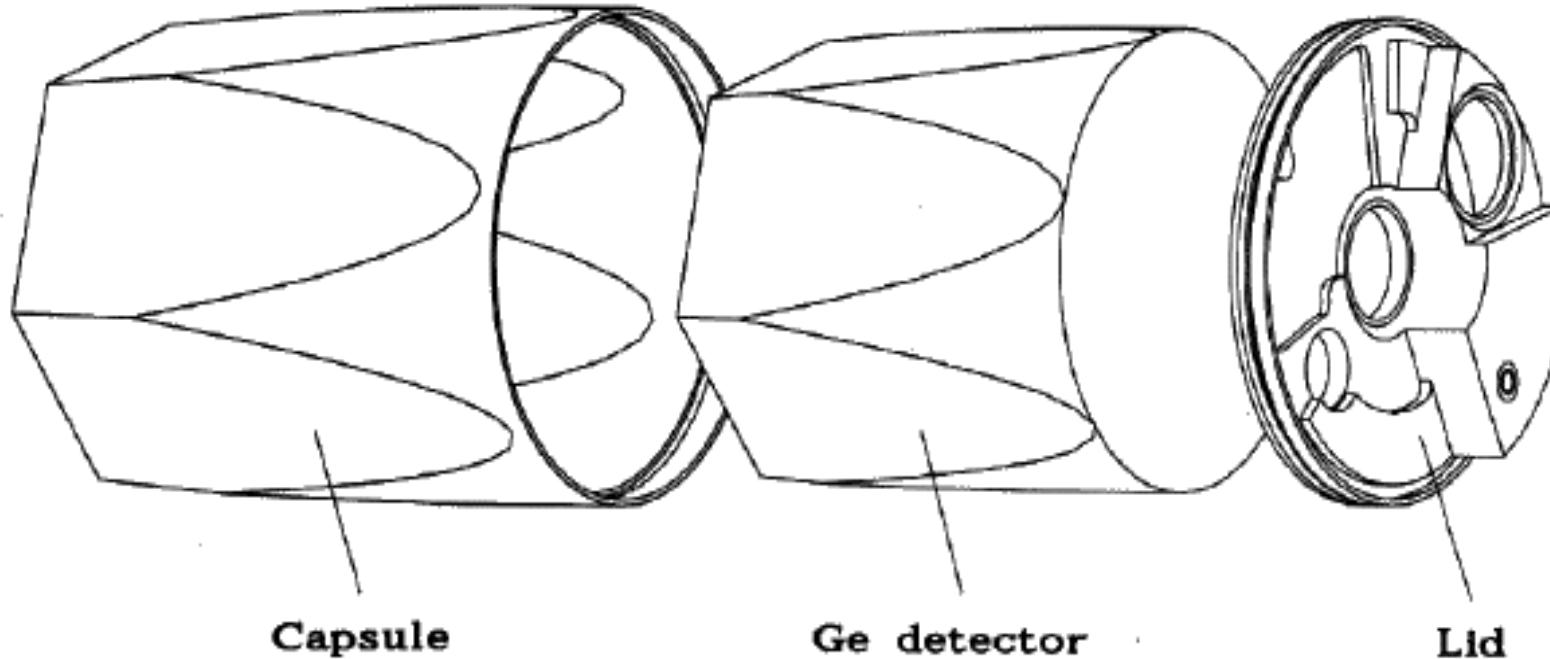
- $E_{\text{gap}} = 0.74 \text{ eV} \Rightarrow$   
operation temperature  
:  $T = 77 \text{ K}$
- $w_{\text{eh}} = 2.98 \text{ eV}$   
 $\Rightarrow$  excellent resolution
  - $E_{\gamma} = 1 \text{ MeV}, dE \cong 1 \text{ keV}$
  - “High” photo peak efficiency

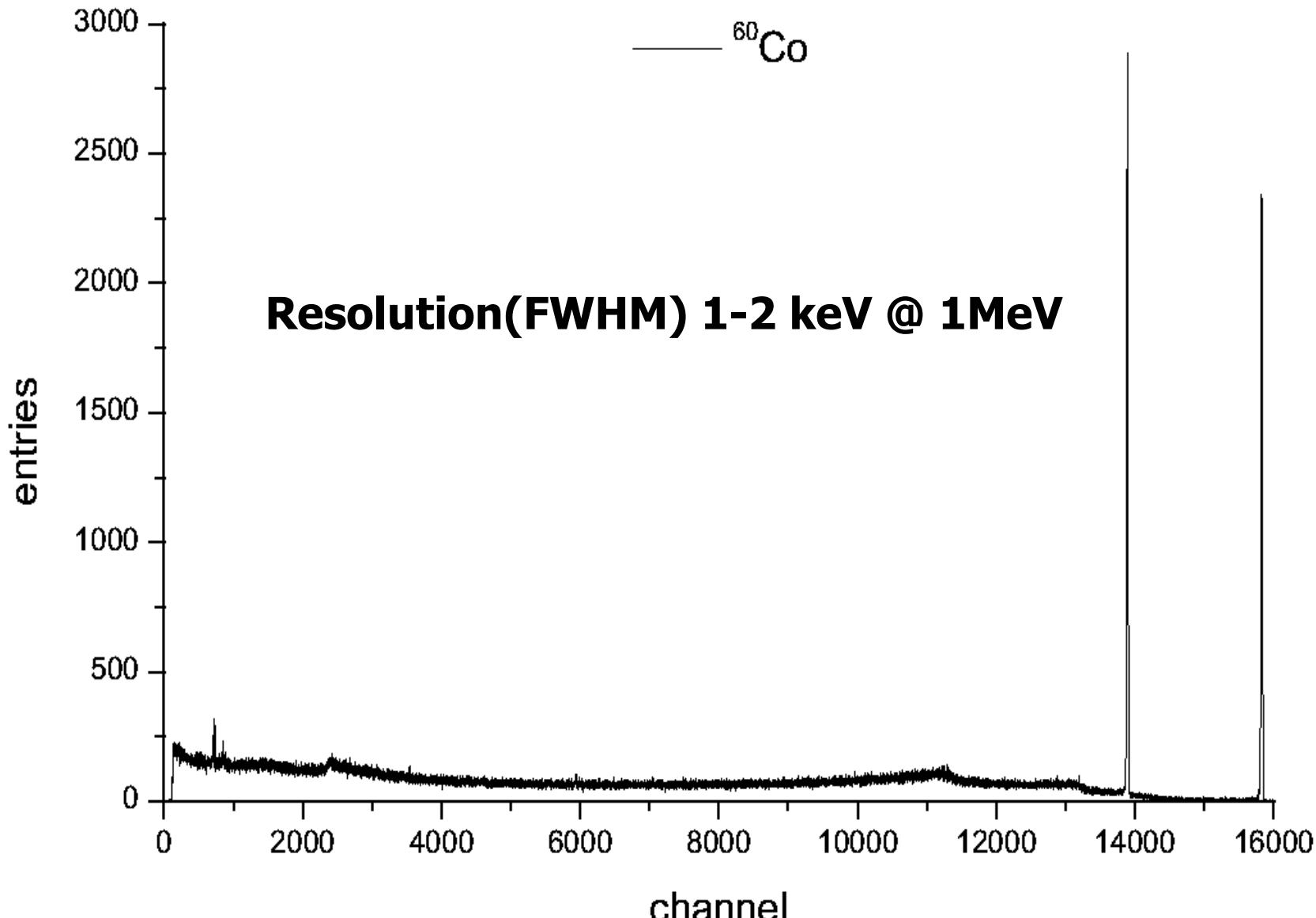
# Germanium detectors

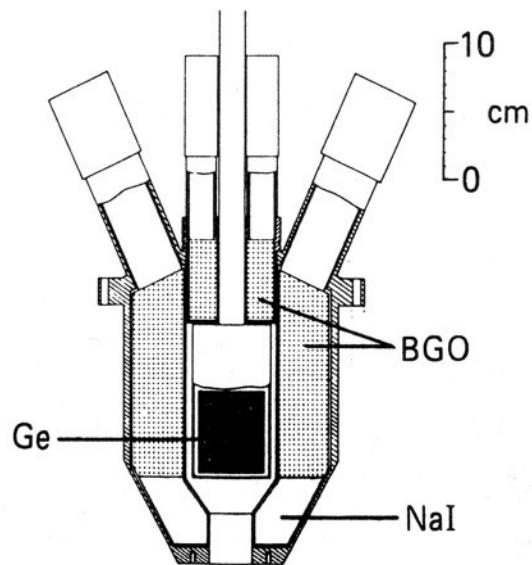
Operation temperature:  $T = 77\text{K}$  (Liquid Nitrogen)

Configuration : co-axial

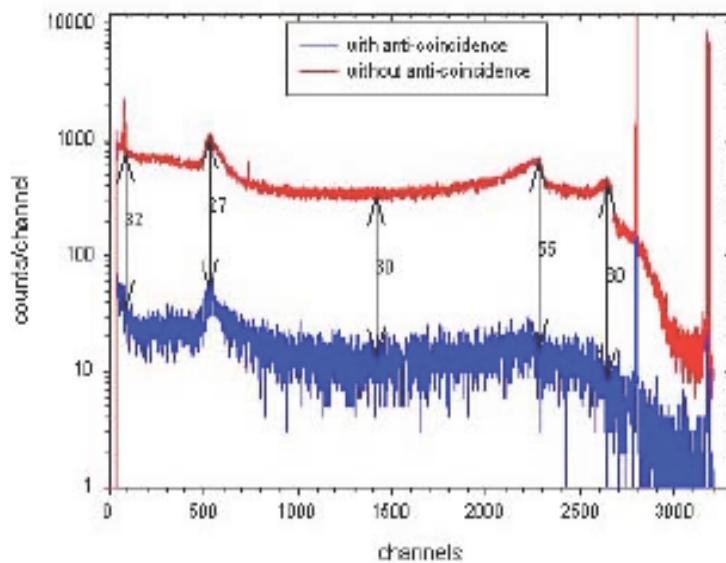
Electronics is mounted very close to the Crystal



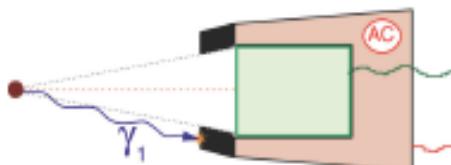




## incidence : système anti-Compton

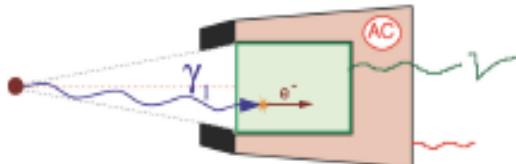


### Événement Collimaté



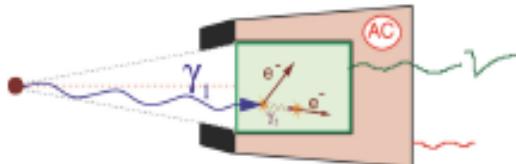
Pas de mesure

### Effet photoélectrique



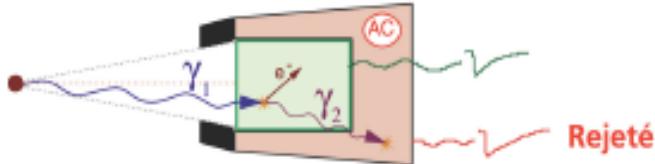
Validé

### Compton interne



Validé

### Echappement Compton



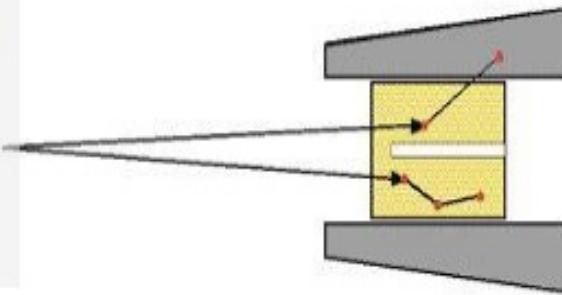
Rejeté

# The idea of $\gamma$ -ray tracking

## Compton Shielded Ge

$\epsilon_{ph}$  ~ 10%  
 $N_{det}$  ~ 100

$\Omega$  ~ 40%  
 $\theta$  ~ 8°



large opening angle  
means poor energy  
resolution at high  
recoil velocity.

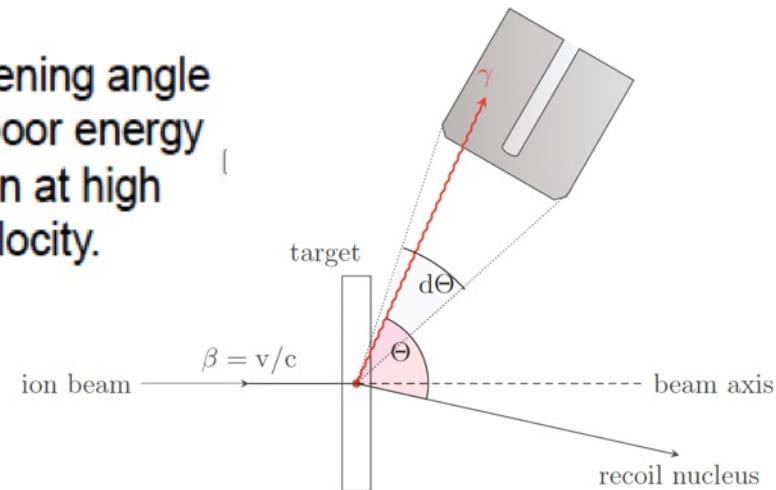


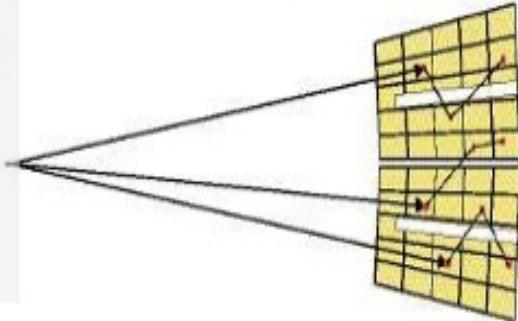
Figure 1.12: Doppler broadening

Previously scattered gammas were wasted.  
Technology is available now to track them.

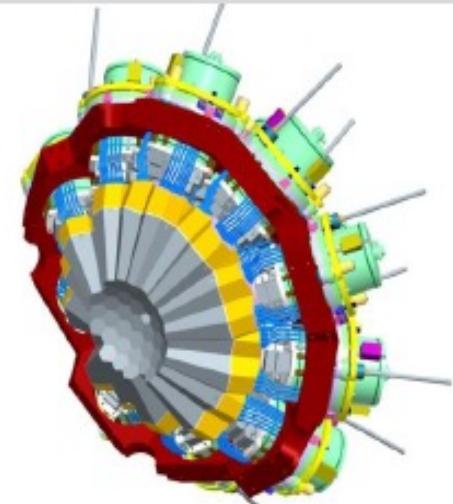
## Ge Tracking Array

$\epsilon_{ph}$  ~ 50%  
 $N_{det}$  ~ 100

$\Omega$  ~ 80%  
 $\theta$  ~ 1°



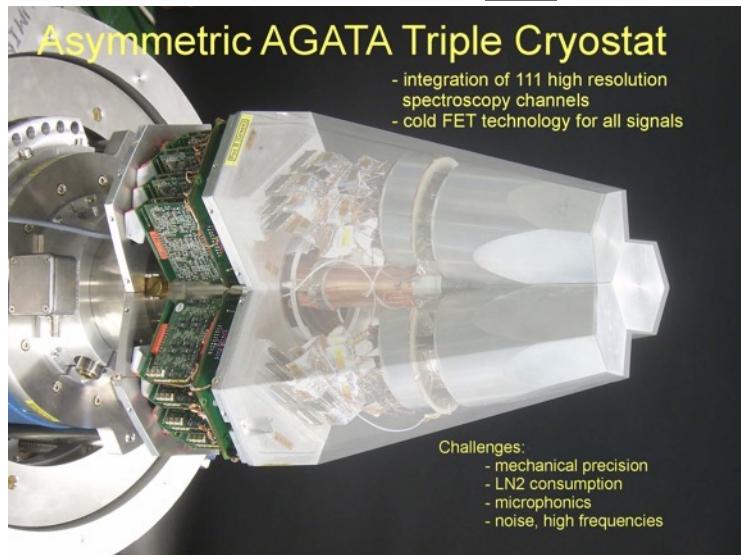
Combination of:  
•segmented detectors  
•digital electronics  
•pulse processing  
•tracking the  $\gamma$ -rays



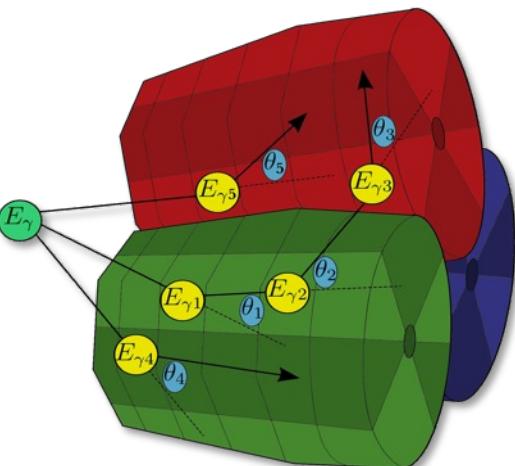
# What is AGATA?



13 Countries, > 40 Institutions



- **Solid Sphere of Ge material: Solid angle coverage  $\sim 82\%$**
- **36-fold segmentation of crystal**
  - **Track each gamma interaction through the crystal**
  - **Reconstruct and disentangle gammas**



Rates	3 MHz ( $M_\gamma = 1$ )	300 kHz ( $M_\gamma = 30$ )
Efficiency	43% ( $M_\gamma = 1$ )	28% ( $M_\gamma = 30$ )
Peak/Total	58% ( $M_\gamma = 1$ )	49% ( $M_\gamma = 30$ )
Angular Resolution	$\sim 1^\circ$	
FWHM (1MeV), v/c = 50%	$\sim 6\text{keV}$	

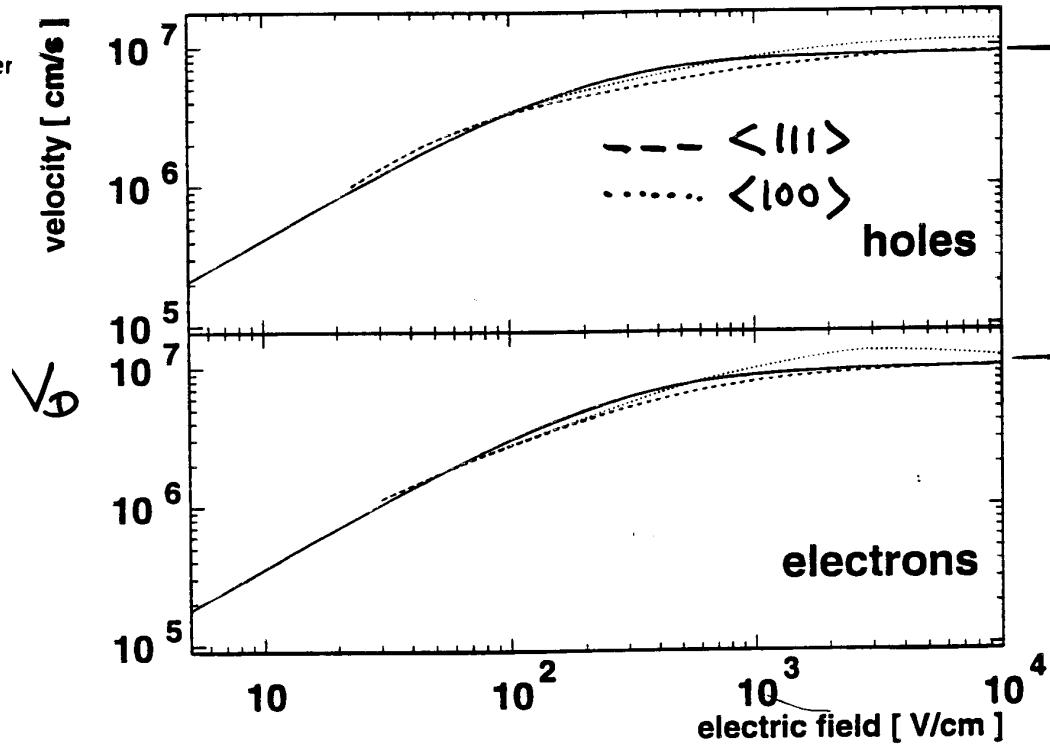
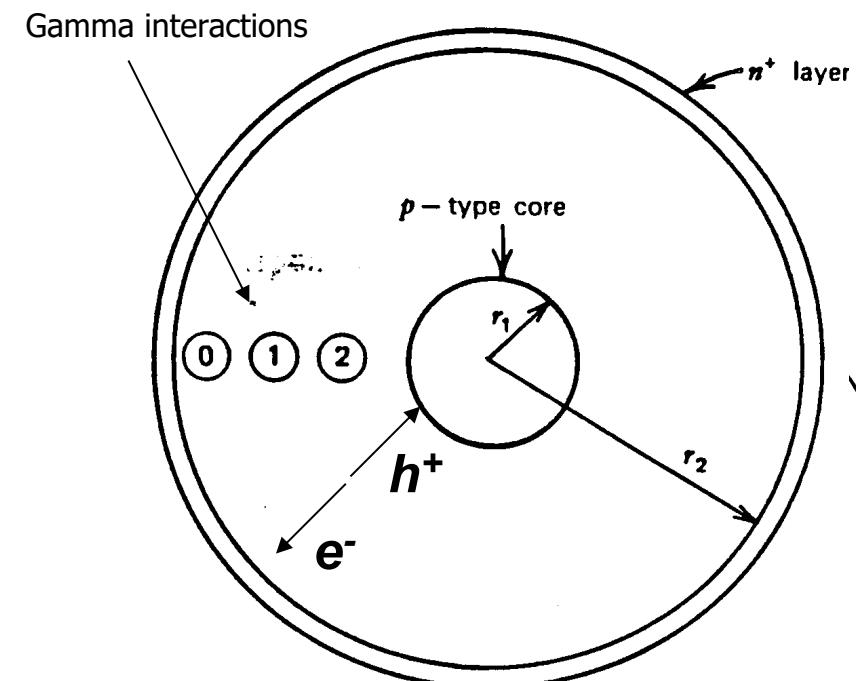
<b>180 hexagonal crystals:</b>	<b>3 shapes</b>
<b>3 fold clusters (cold FET):</b>	<b>60 all equal</b>
<b>Inner radius (Ge):</b>	<b>23.5 cm</b>
<b>Amount of germanium:</b>	<b>362 kg</b>
<b>36-fold segmentation</b>	<b>6480 segments</b>



# signal formation in

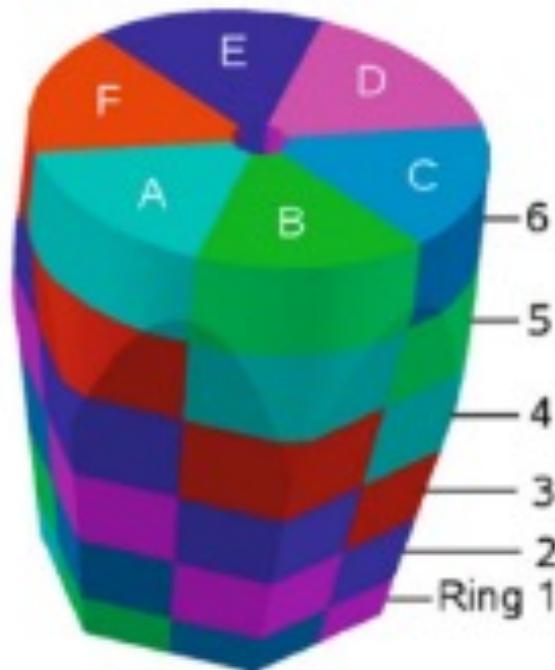
## Ge-HP

### Cylindrical geometry



# Segmentation of High Purity Ge crystal

Divide the electrodes on the surface of the detector



Weighting field shows how the segmentation works

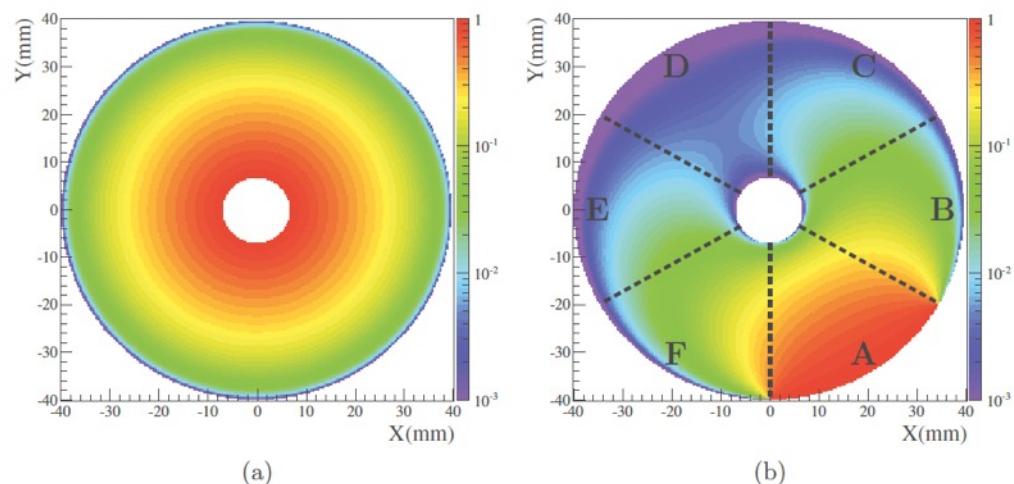


Figure 2.2: Weighting-potential distributions of the Core (a) and of segment A (b). Calculation conditions are the following: readout electrode at unit potential, all other electrode at zero potential, no space charge inside the material.

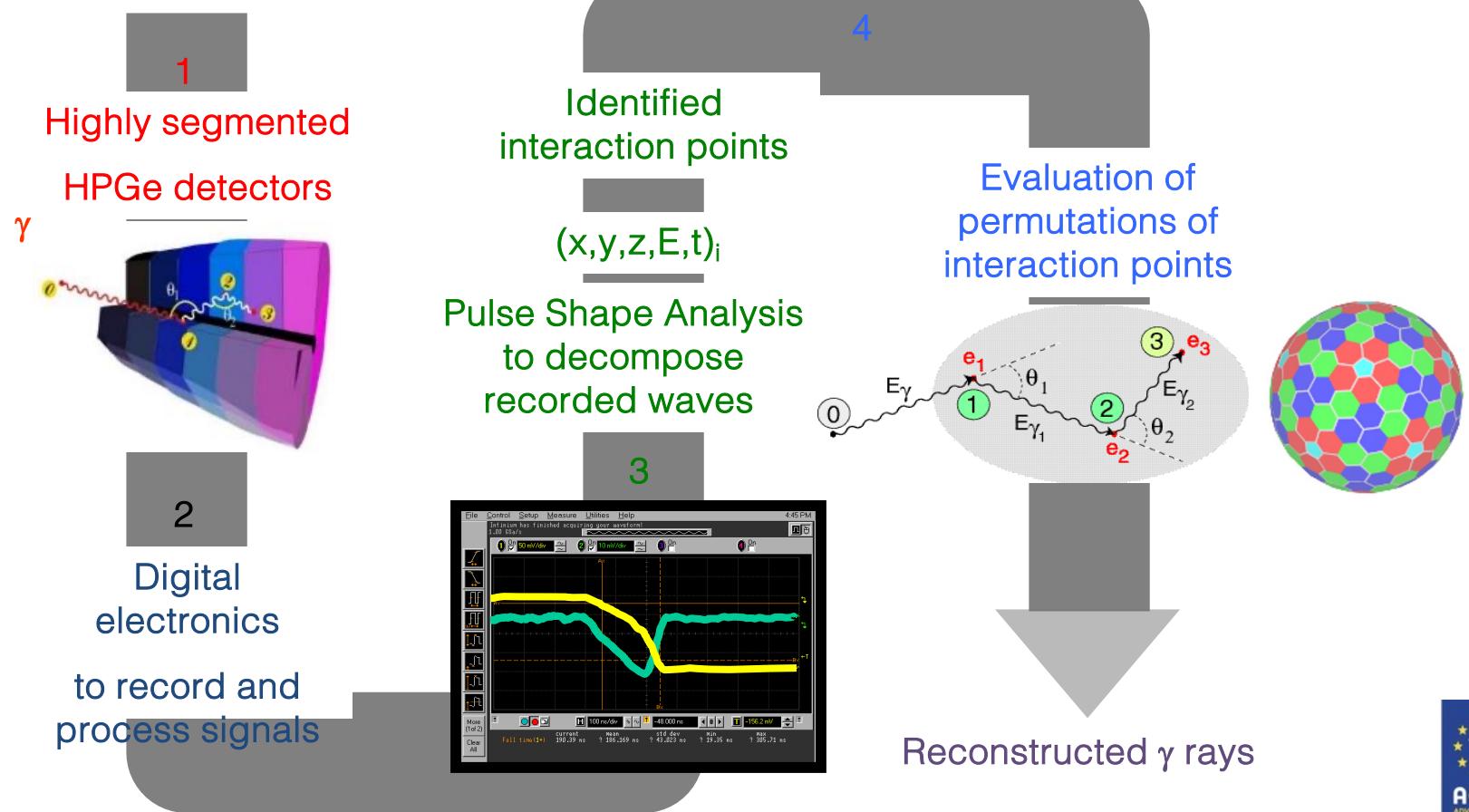
$$Q(t) = -q \cdot [\phi_w(x_h(t)) - \phi_w(x_e(t))]$$

$$i(t) = q \cdot [E_w(x_h(t)) \cdot v_h(t) - E_w(x_e(t)) \cdot v_e(t)]$$

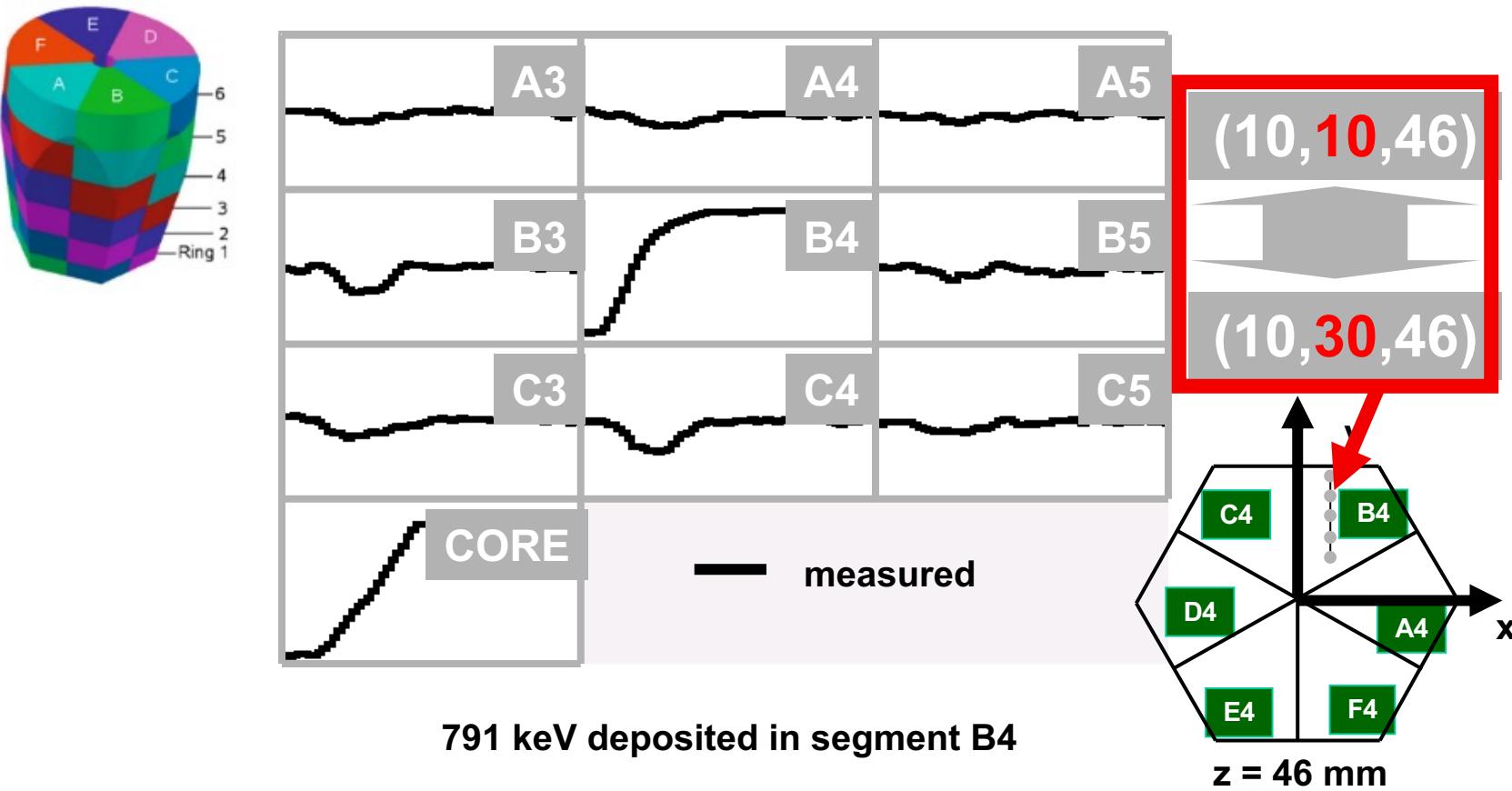
$\phi_w$  and  $E_w$  are the weighting potential and the weighting field.

Michaël Ginsz, PhD thesis 2017

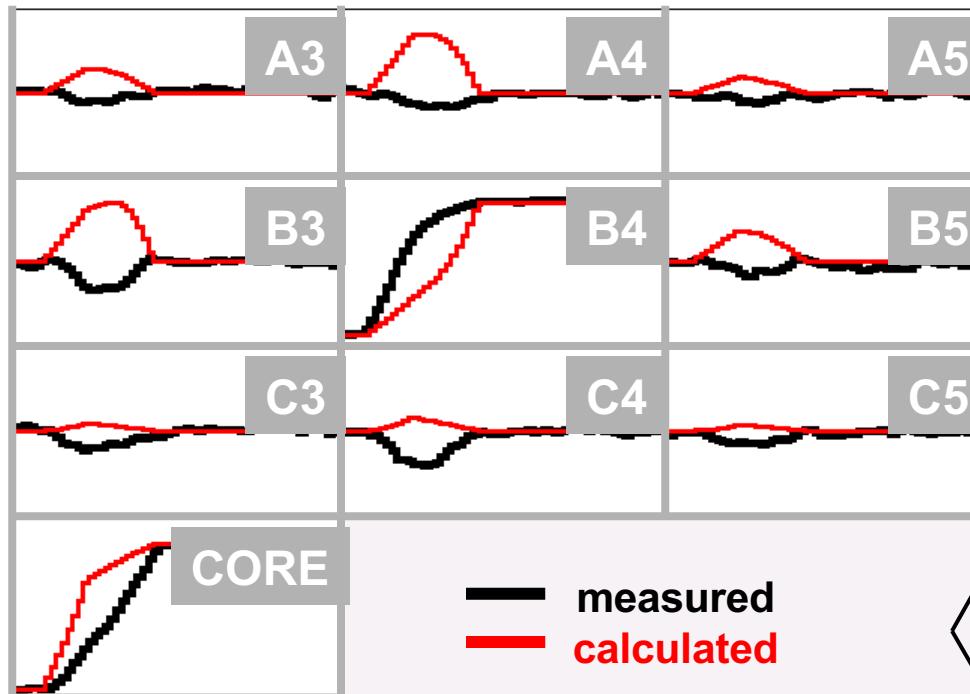
# AGATA Tracking Concept



# Pulse Shape Analysis Concept

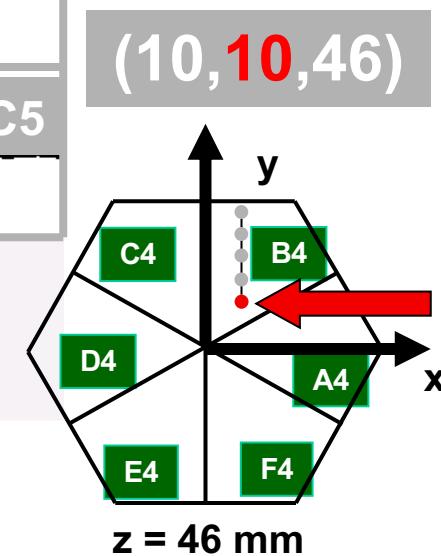


# Pulse Shape Analysis Concept

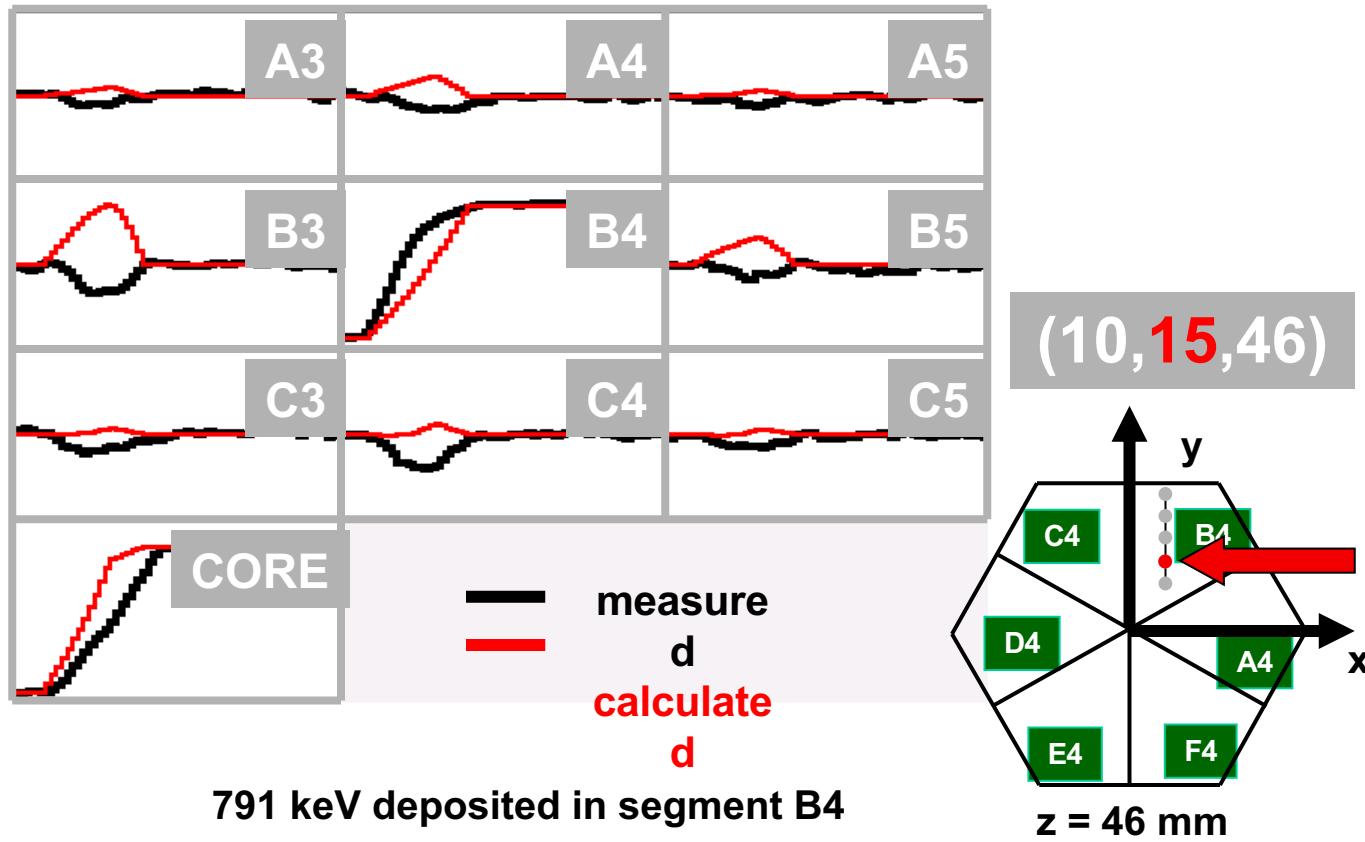


791 keV deposited in segment B4

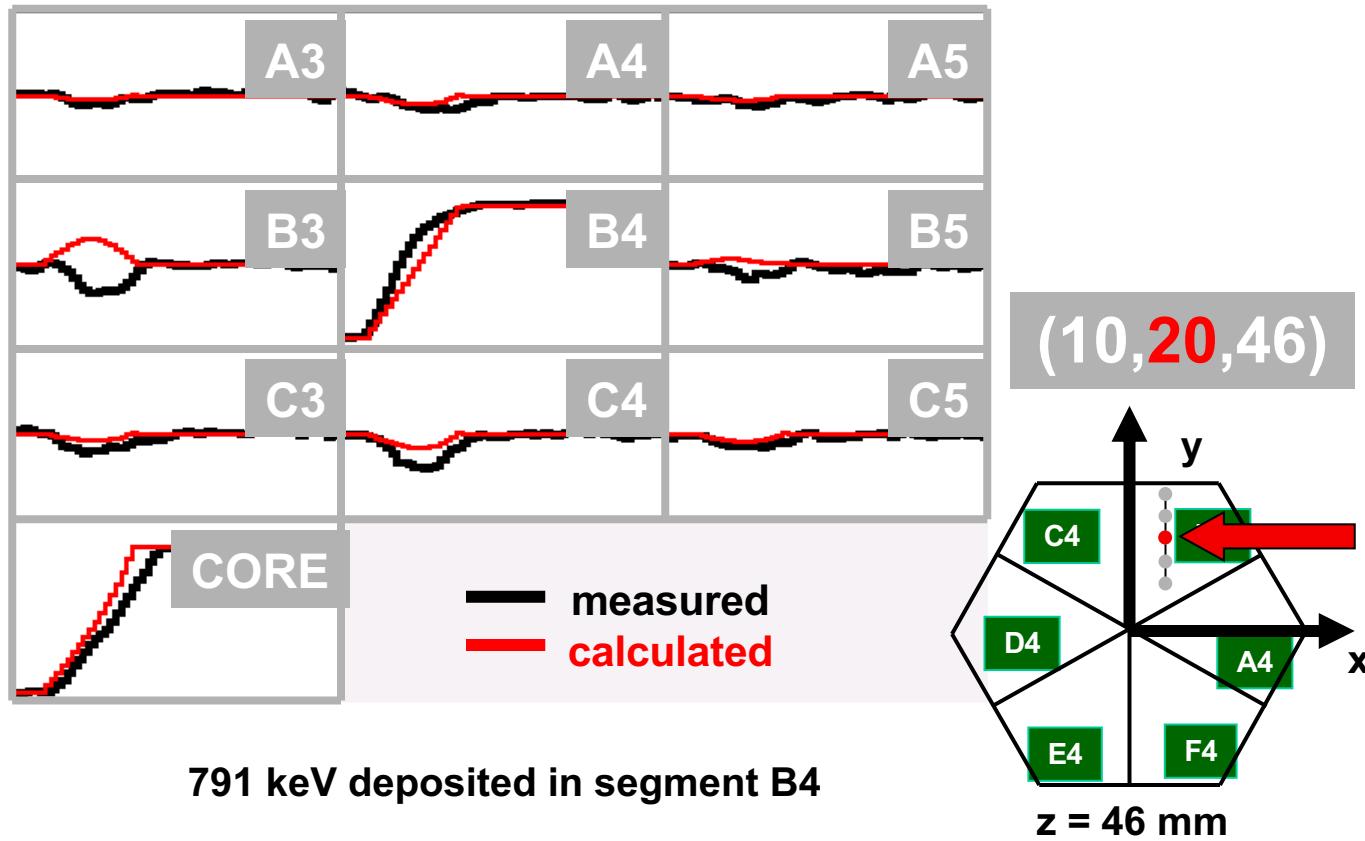
Calculated from Electric  
field simulation



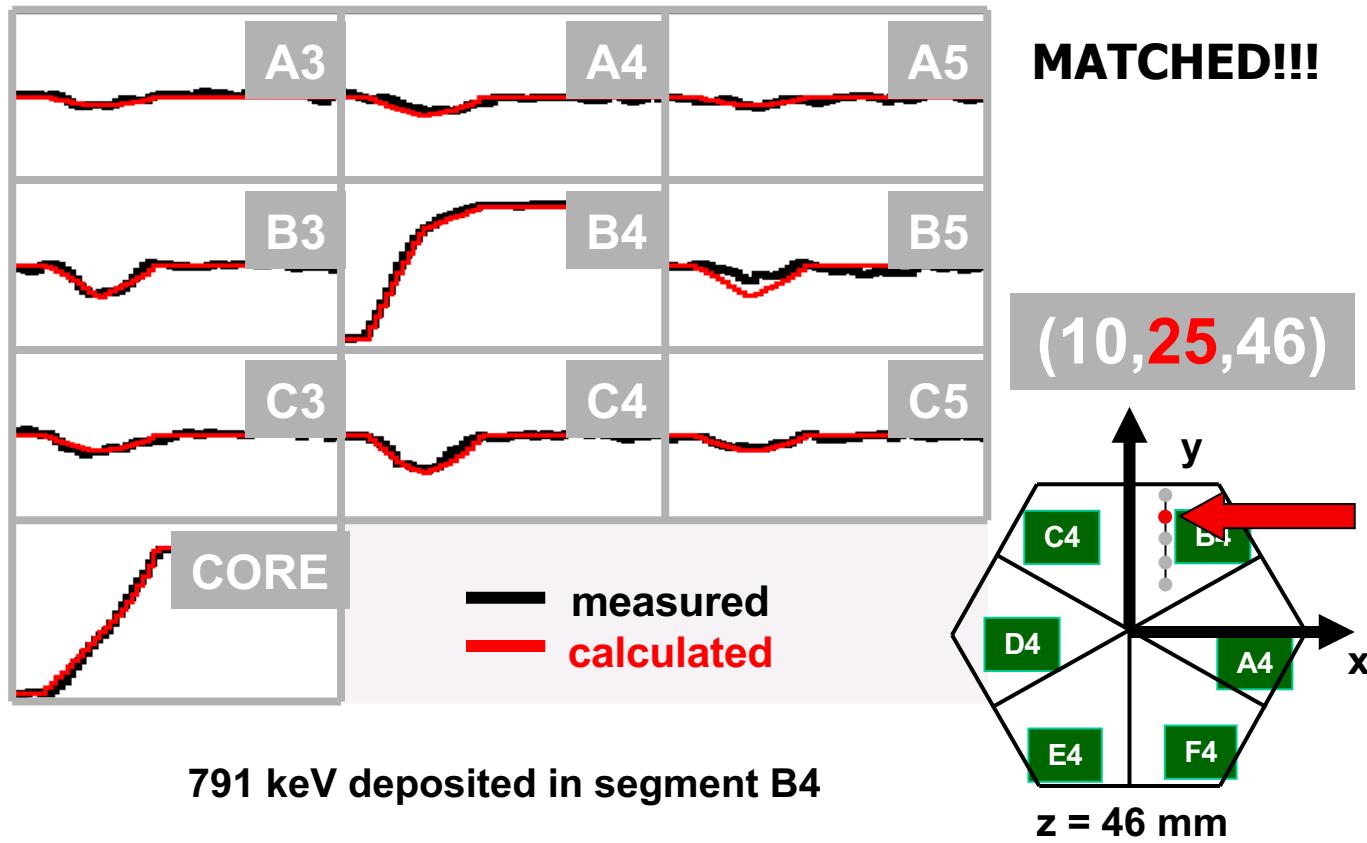
# Pulse Shape Analysis Concept



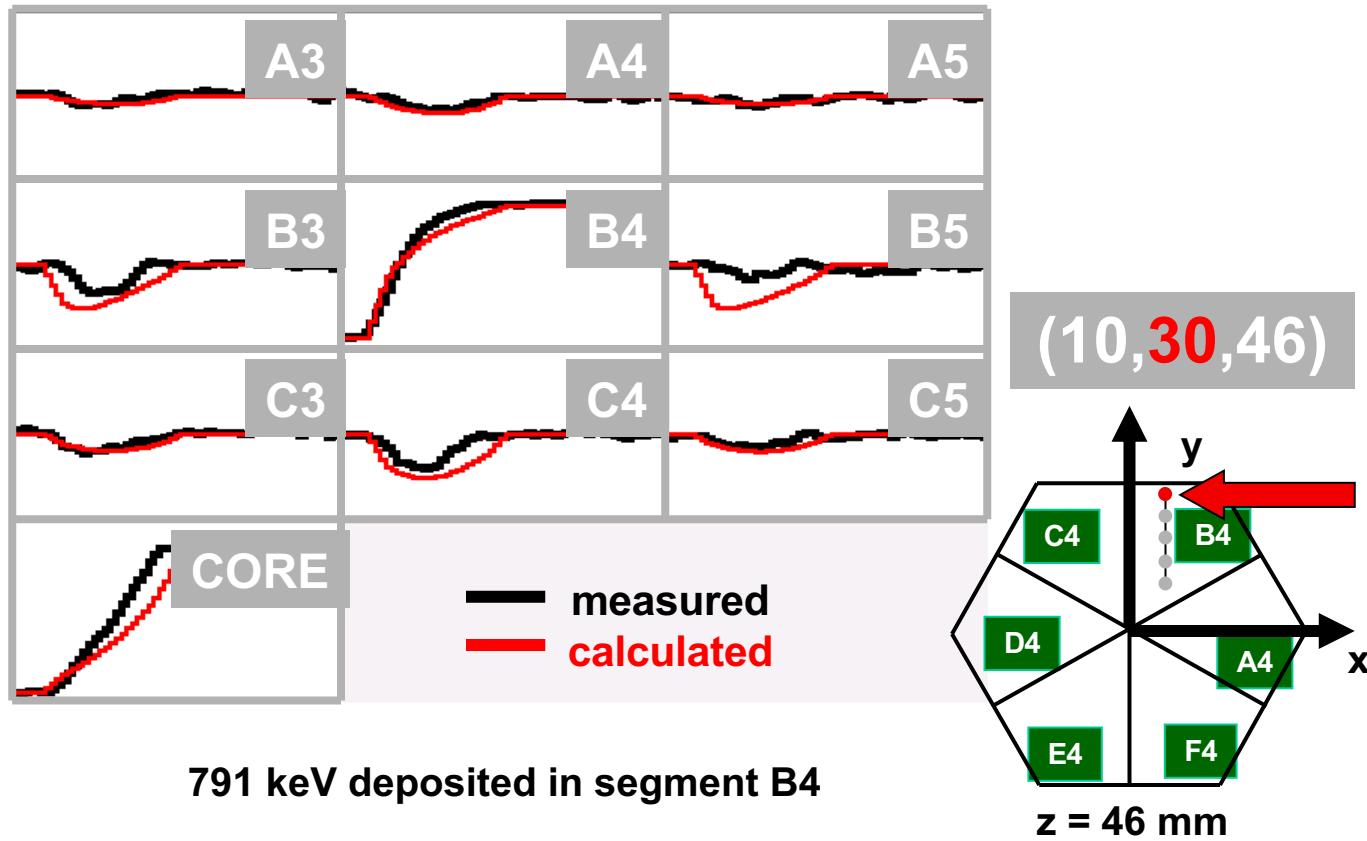
# Pulse Shape Analysis Concept



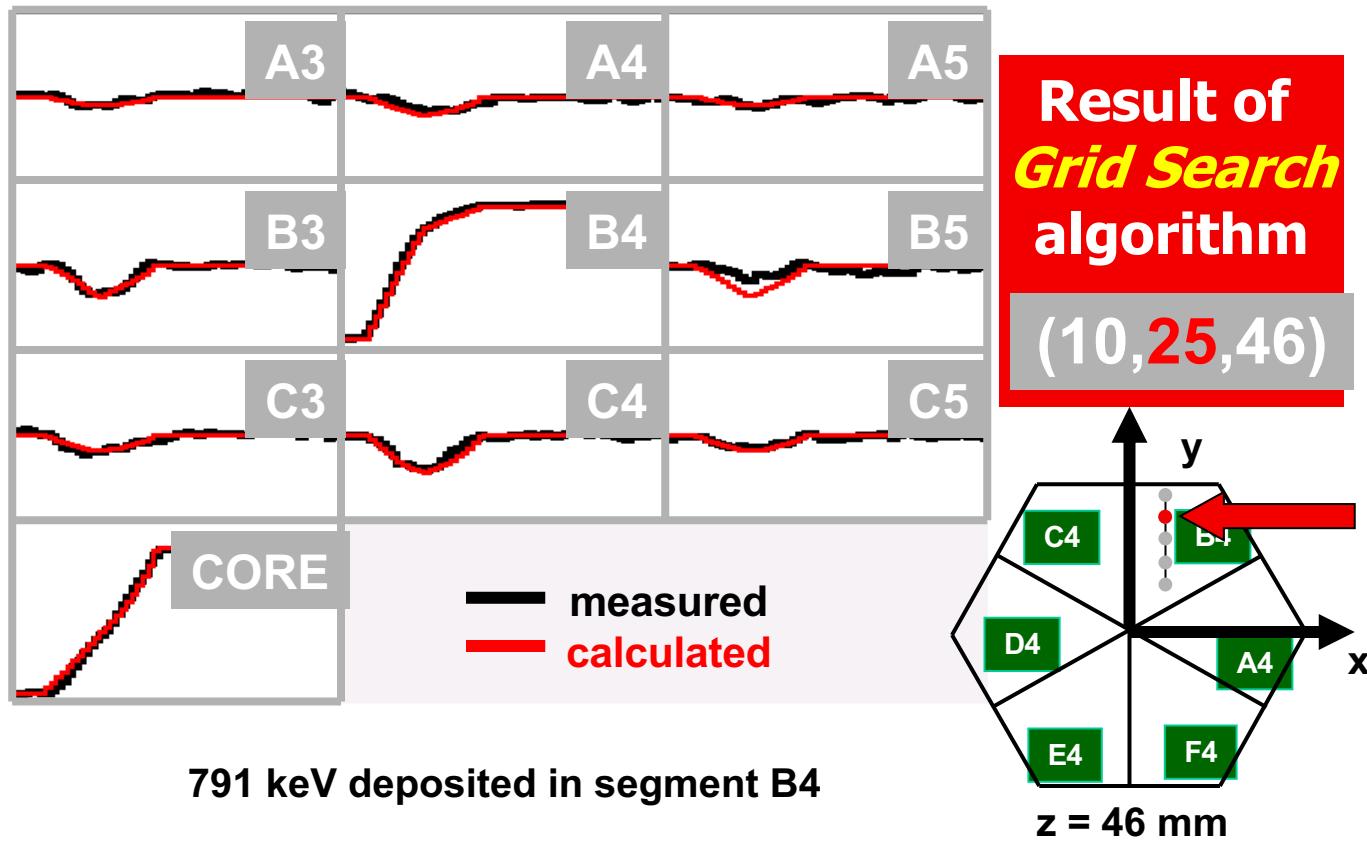
# Pulse Shape Analysis Concept



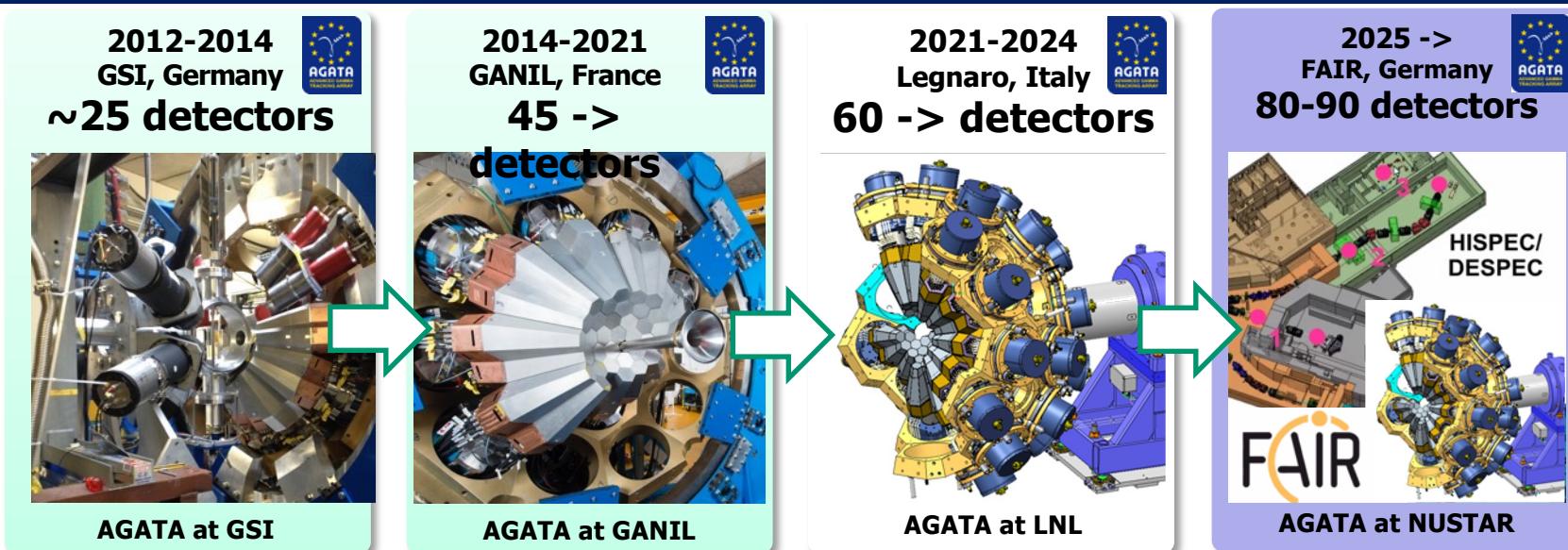
# Pulse Shape Analysis Concept



# Pulse Shape Analysis Concept



# Evolution of AGATA



Reaccelerated RIBs:

- Coulomb Excitation, Direct Reactions, Deep Inelastic, Fusion
- Direct and inverse kinematics  $\beta \sim 10\%$

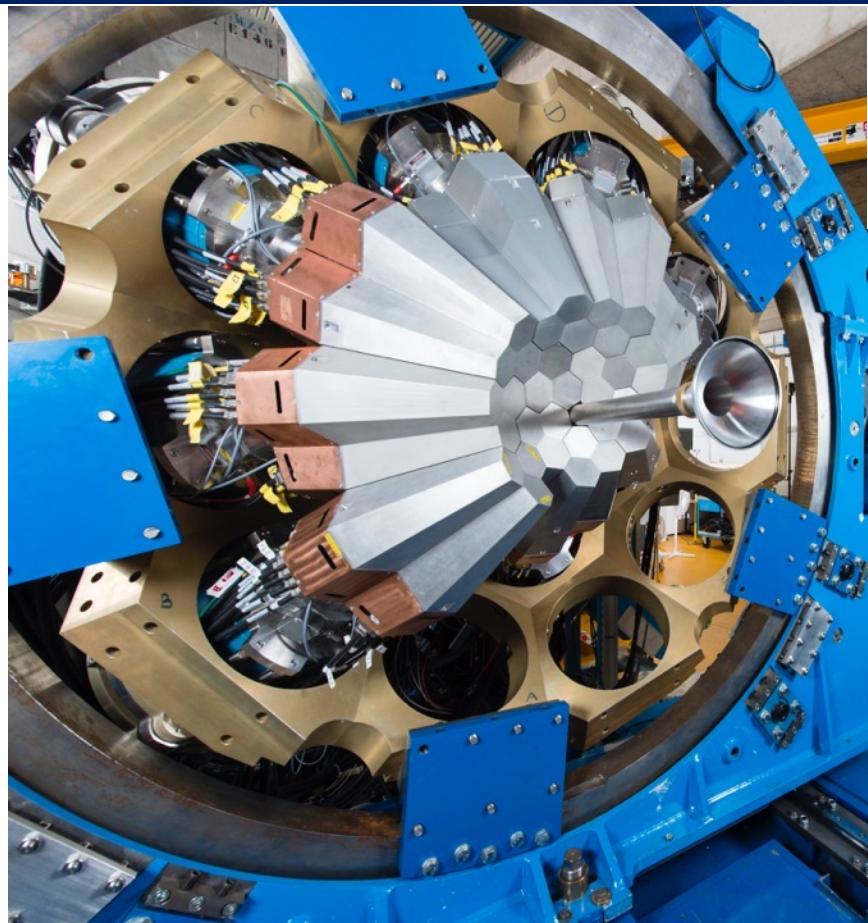
In-flight RIBs:

- Relativistic Coulomb Excitation, Knockout, Fragmentation.
- $\beta \sim 50\%$

They had about 60 detectors for AGATA by end 2023



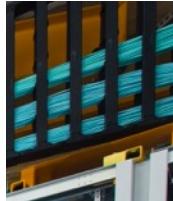
# Evolution of AGATA



2014-2021

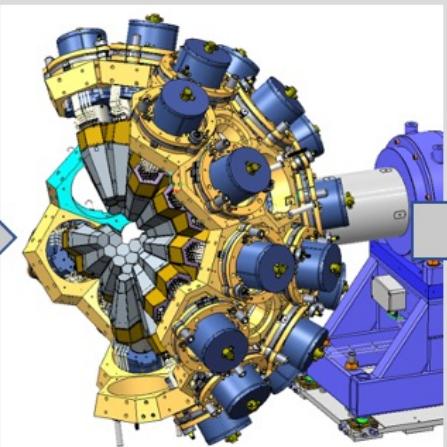
GANIL, France

45 ->  
detectors



2021-2024  
Legnaro, Italy

60 -> detectors



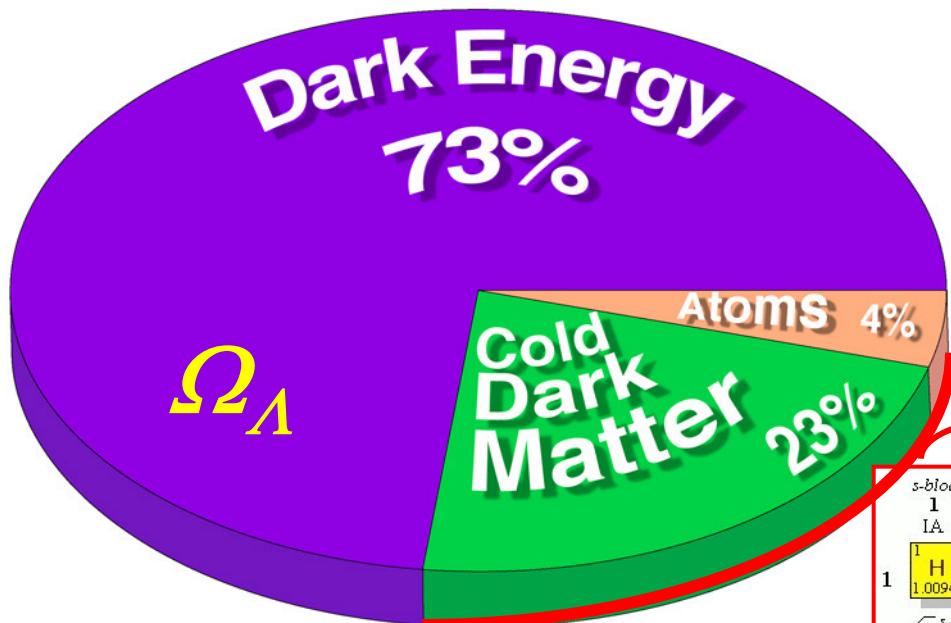
AGATA at LNL

# **Conclusions**

*(nuclear detectors)*

- **High Z Scintillators are used for gamma spectroscopy, particular for anti Compton spectrometers**
- **Low Z (organic)-Scintillators used for particle detection/stopping**
- **Semiconductors: Si used for charged particle spectroscopy (alpha, protons, ... Fission fragments)**
- **Semiconductors: HP-Ge for high resolution and high efficient Gamma spectroscopy**

We (and all of chemistry) are a small minority in the Universe.



s-block		Transition Metals												p-block						
	New Designation	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	
	Original Designation	I	IIA	IIIB	IVB	VB	VIB	VIIB	VIIIB	VIIIB	IB	IIB	IIIA	IVA	V	VIA	VIIA	VIIIA		
1	H	1.0094	2	Li	Be	Na	Mg	Al	Si	P	Cl	Ar	He							
2		6.941	9.0122	11	12	22.990	24.305	13	14	15	16	17	18	19.0026	18.998	18.999	18.998	18.999		
3				Sc	Ti	V	Cr	Mn	Fe	Co	Ni	Cu	Zn	B	C	O	F	Ne		
4				44.956	47.88	50.942	51.996	54.938	55.847	58.933	58.69	63.546	65.39	10.81	12.011	14.007	15.999	18.998	20.179	
5				39.098	40.08	41	42	43	44	45	46	47	48	13	14	15	16	17	18	
6				37	38	39	40	41	42	43	44	45	46	49	50	51	52	53	54	
7				Rb	Sr	Y	Zr	Nb	Mo	Tc	Ru	Rh	Pd	Ag	Ga	Ge	As	Se	Br	
8				85.468	87.62	88.906	91.224	92.906	95.94	(98)	101.07	102.91	106.42	107.87	112.41	114.82	118.71	121.75	127.60	131.29
9				55	56	57	58	59	60	61	62	63	64	65	66	67	68	69	70	
10				Cs	Ba	to 71	72	73	74	75	76	77	78	79	80	81	82	83	84	
11				132.91	137.33		178.49	180.95	183.85	186.21	190.2	192.22	195.08	196.97	200.59	204.38	207.2	208.98	210)	222)
12				87	88	89	104	105	106	107	108	109	110							
13				Fr	Ra	to 103	105	106	107	108	109	110								
14				(223)	226.03	(261)	(262)	(263)	(262)	(265)	(266)	(267)								
15																				
16																				
17																				
18																				

(Mass Numbers in Parentheses are from the most stable of common isotopes.)

**Metals**

**Rare Earth Elements**

Lanthanide Series

Actinide Series

**f-block**

Phases

Solid

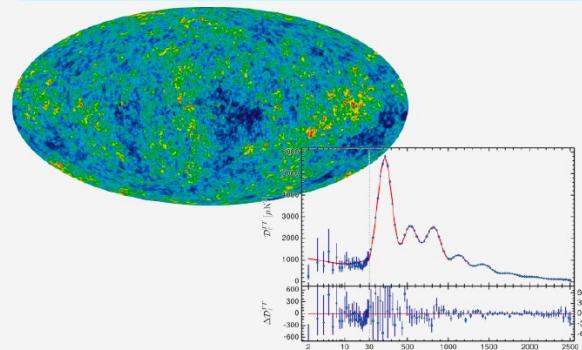
Liquid

Gas

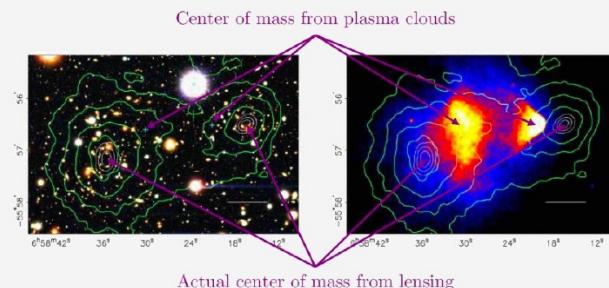
# Dark Matter ?

## Dark Matter Evidence

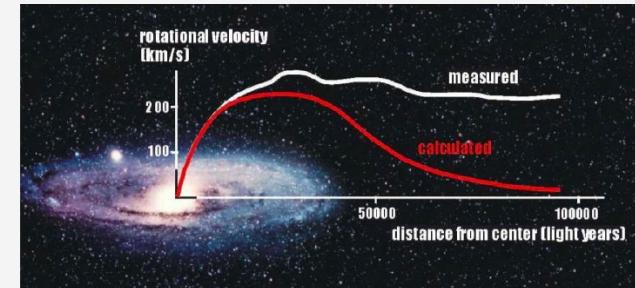
Cosmic Microwave Background



Bullet Cluster



Rotation curves



... non-atomic (if not PBH) – non-luminous – stable – neutral – massive – non-relativistic ...

...

Axions / ALPs  
~meV

Sterile  $\nu$   
~keV

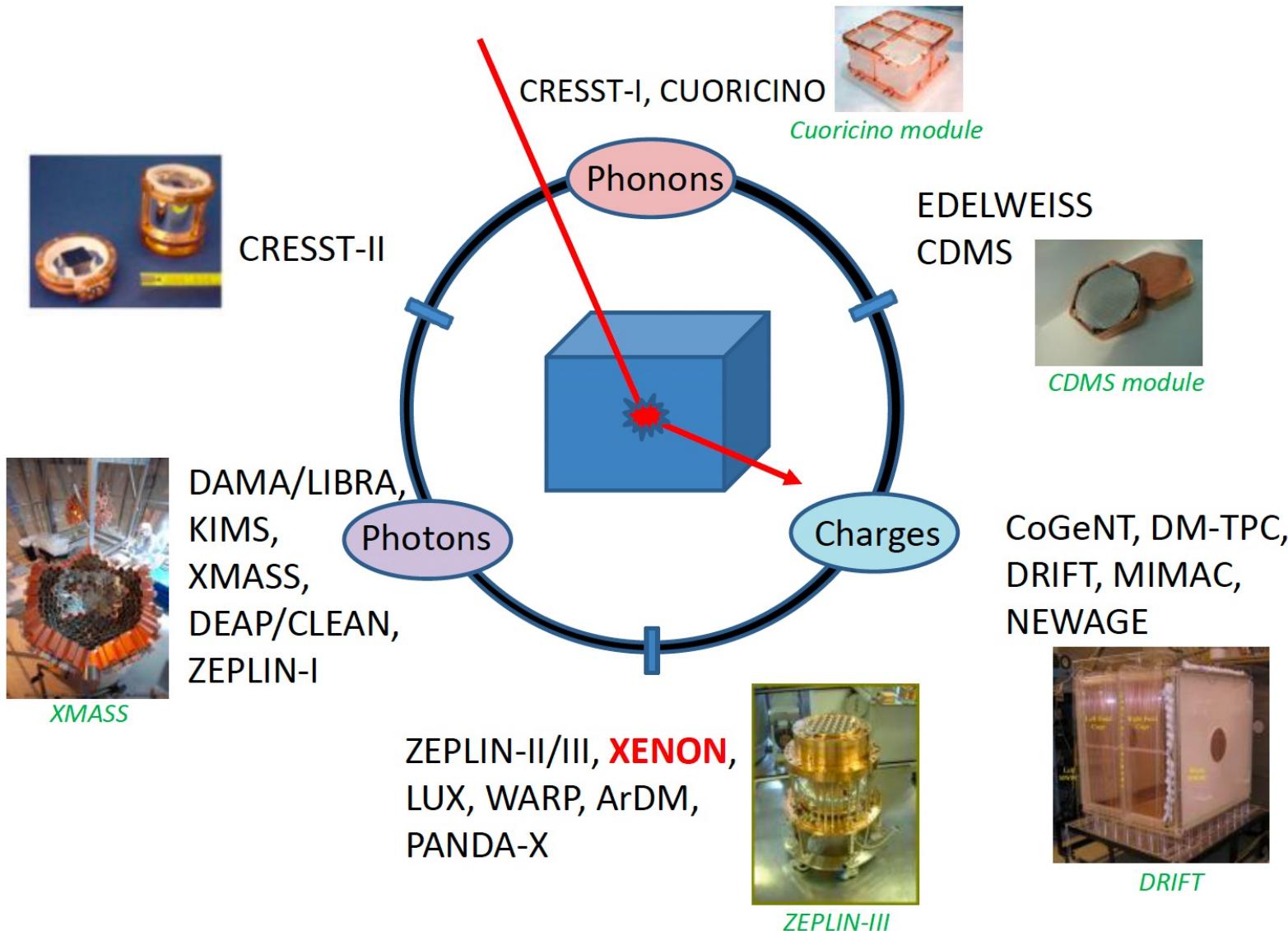
WIMPs  
~GeV

Primordial Black Holes

...

mass

# Direct Dark Matter Search Modalities



# A double phase liquid xenon TPC

Dark Matter and Axion Searches - Belina von Krosigk

Most recent results >1 GeV: LZ, XENONnT



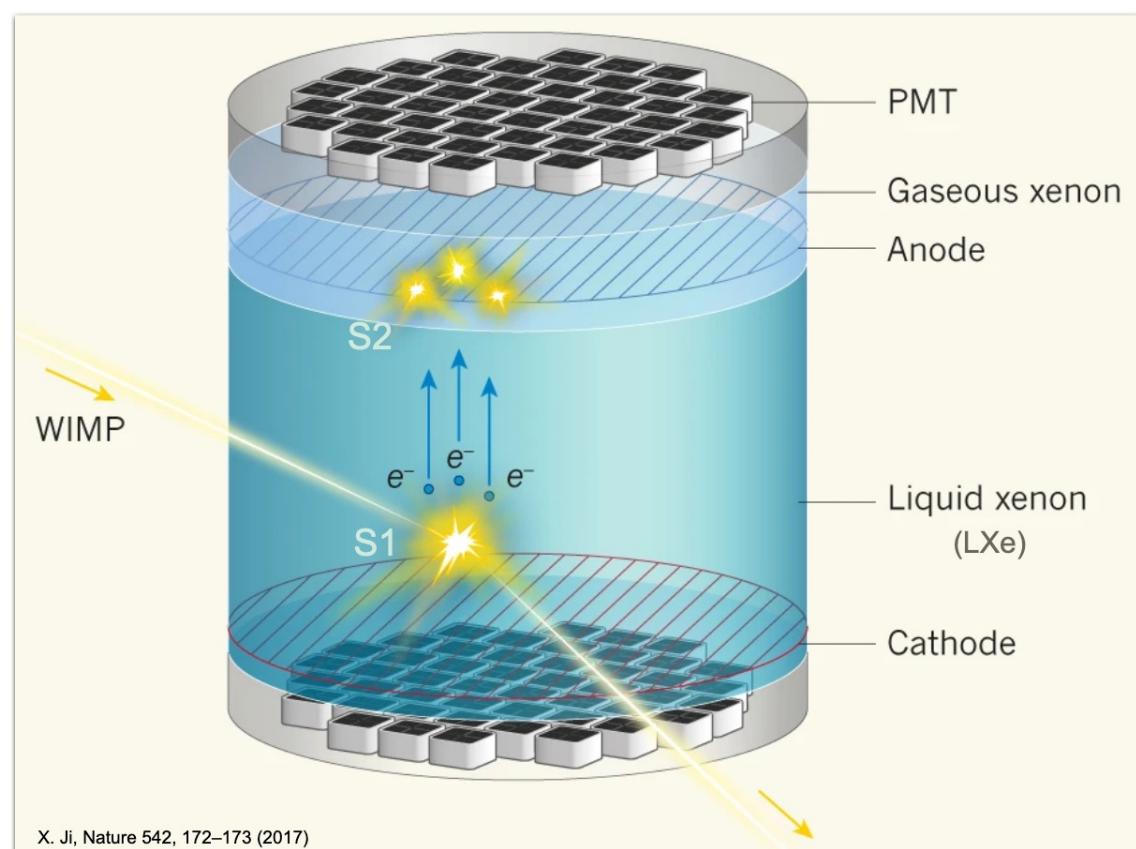
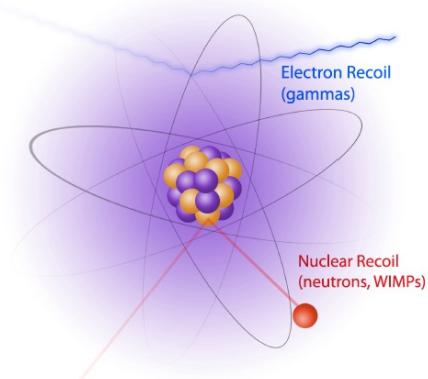
12

LZ:

5.5 t fiducial mass, LXe

XENONnT:

4.2 t fiducial mass, LXe

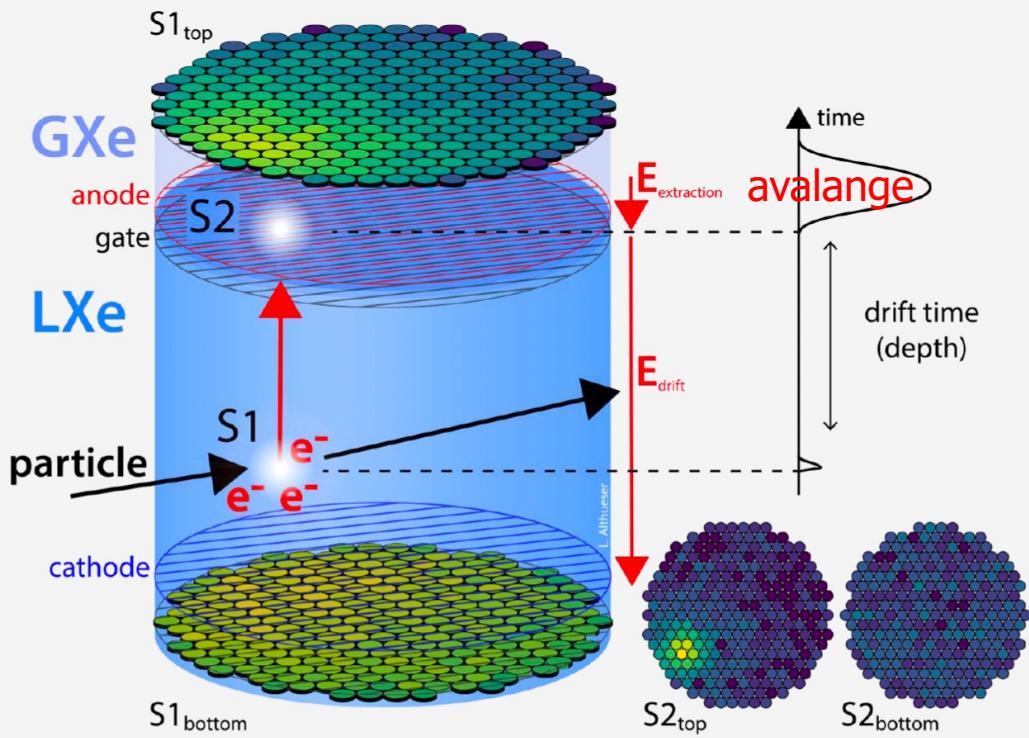


X. Ji, Nature 542, 172–173 (2017)

# A double phase liquid xenon TPC

Latest results from XENONnT

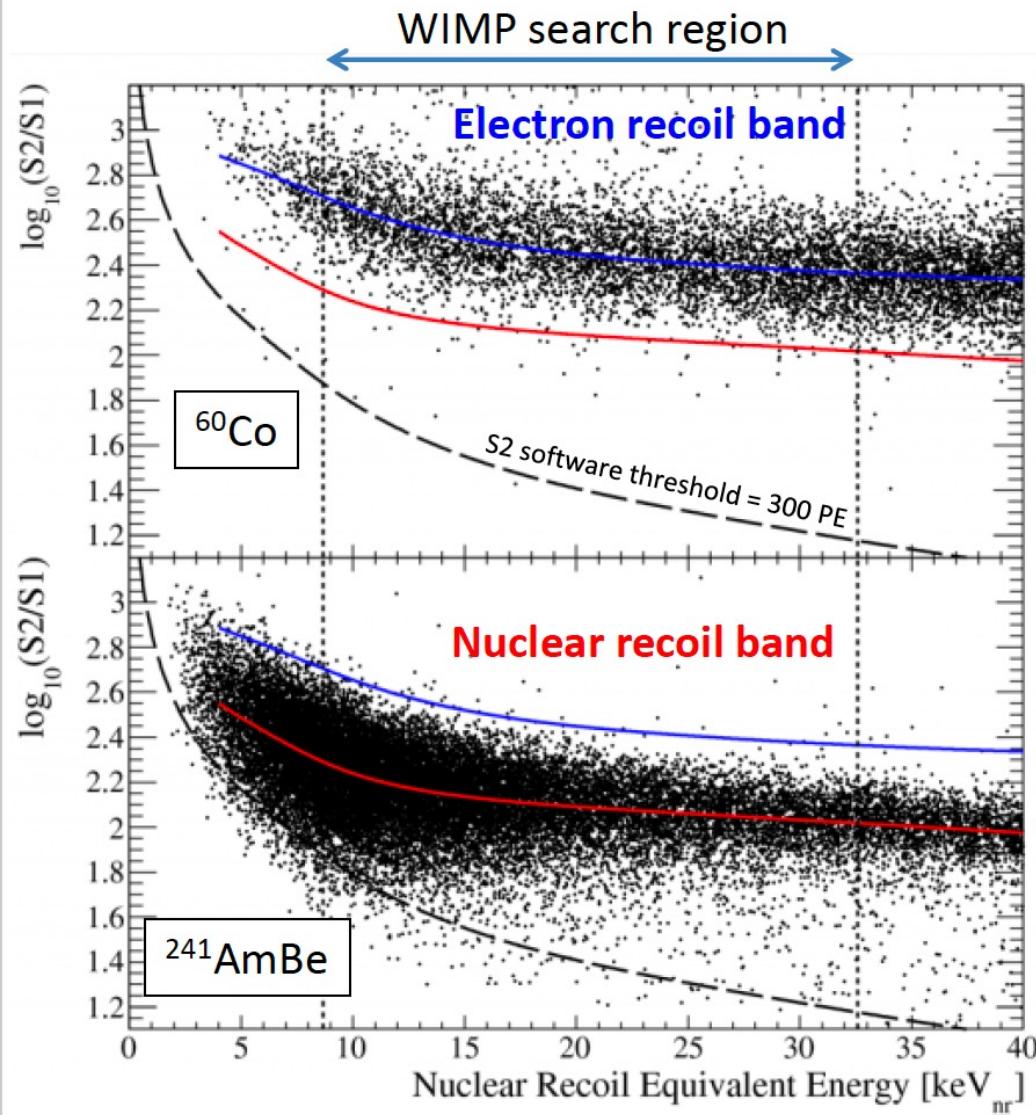
## Working Principle



Working principle of dual-phase liquid noble gas time projection chambers (TPCs)

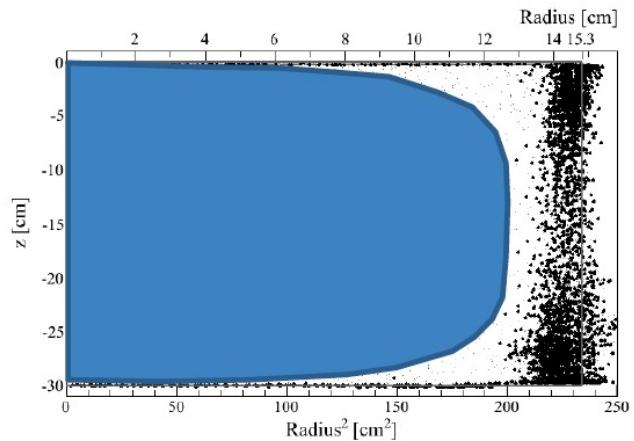
- Prompt light signal (S1)
- Secondary light in GXe from drifted charges (S2)
- Energy reconstruction using the combined S1 and S2 signal
- Position reconstruction
  - z from S1-S2-delay time
  - x-y from S2 hit pattern

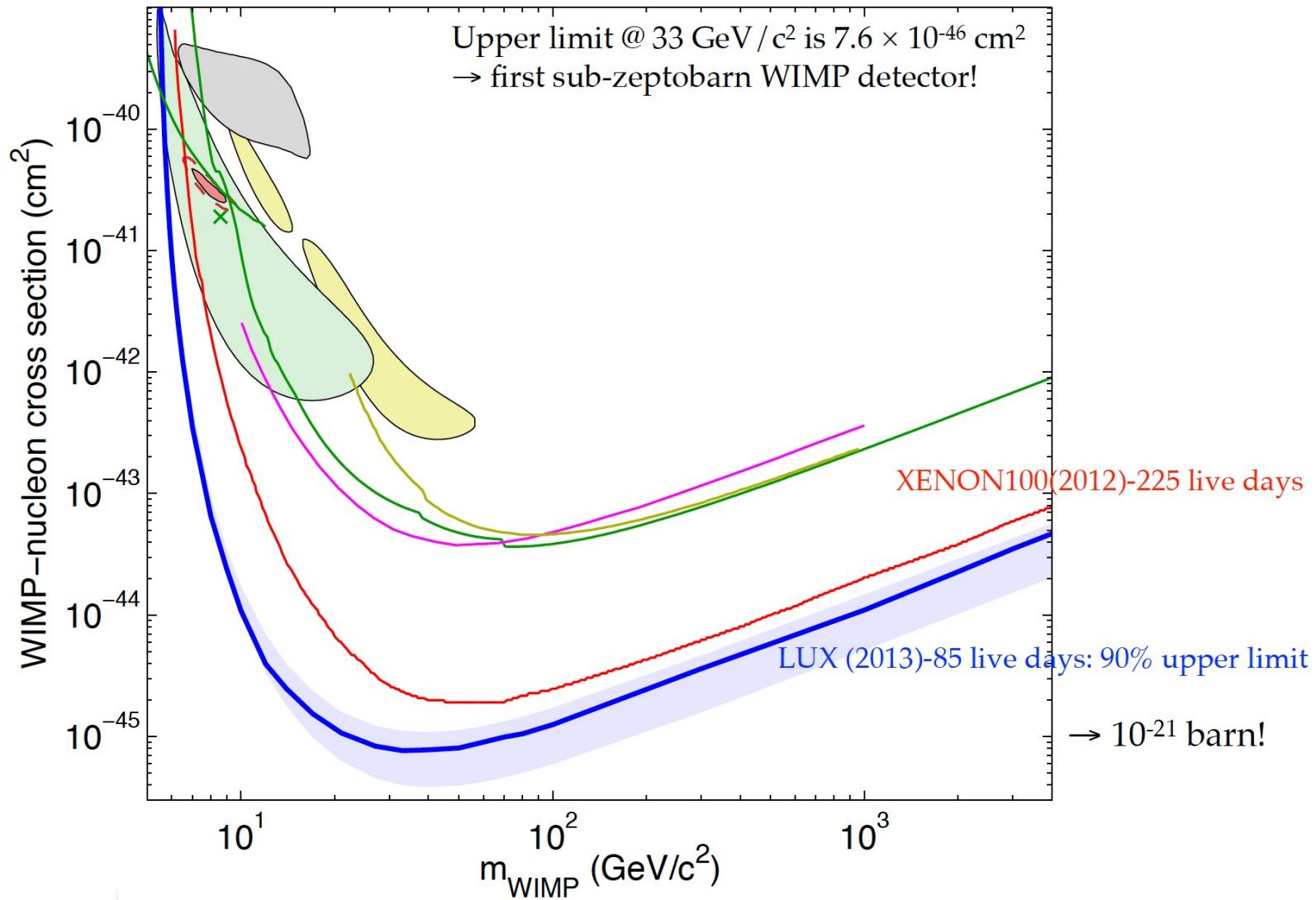
# Background discrimination

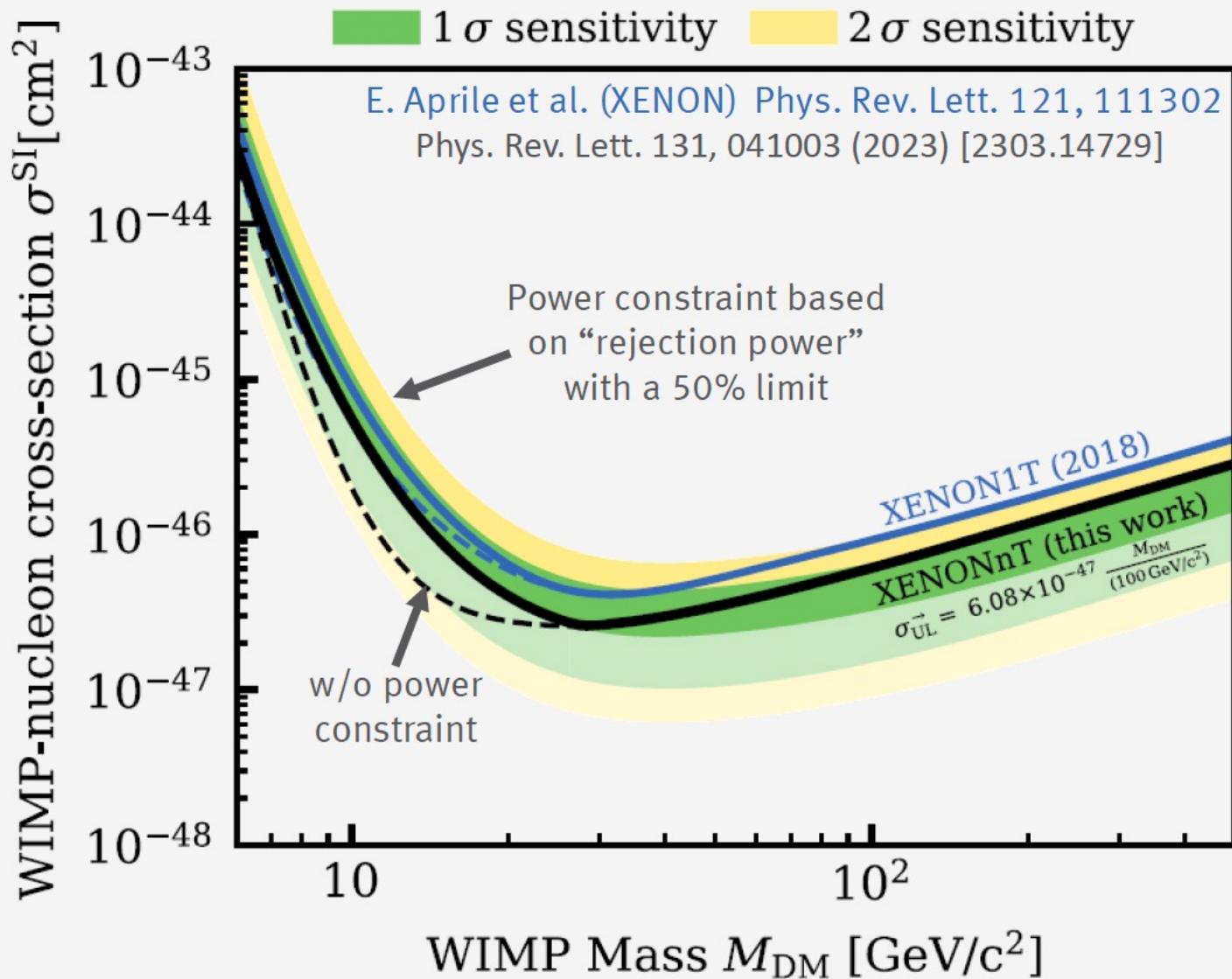


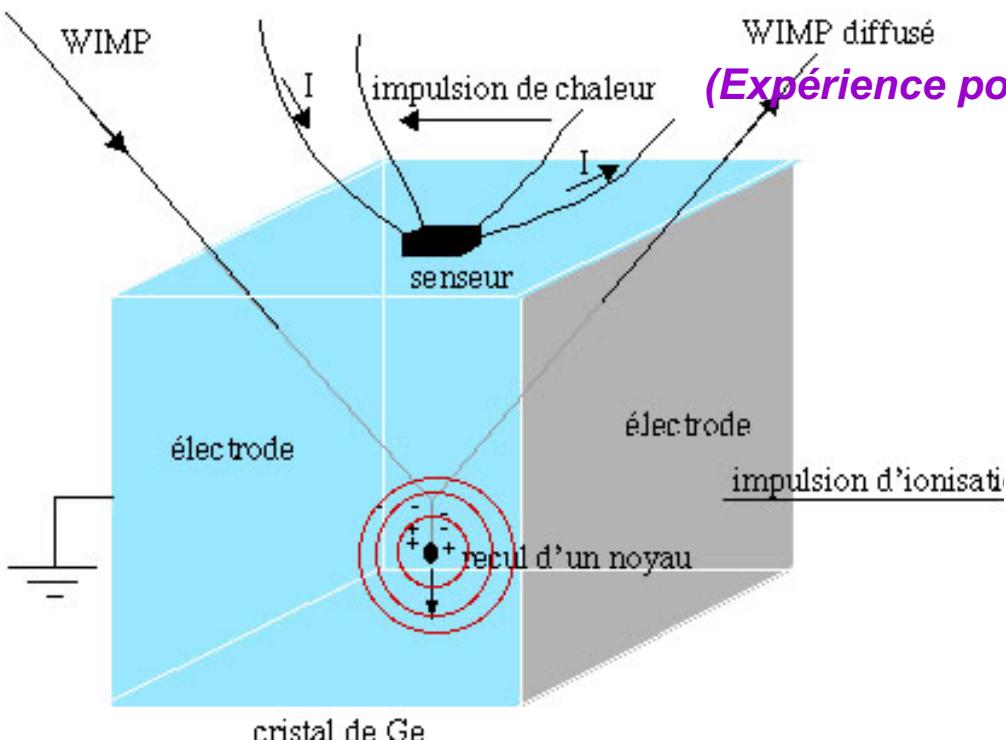
Identification of recoil species by S2/S1 ratio

- from  $^{60}\text{Co}$   $\gamma$ -ray source and  $^{241}\text{AmBe}$  neutron source
- selecting single scattered events





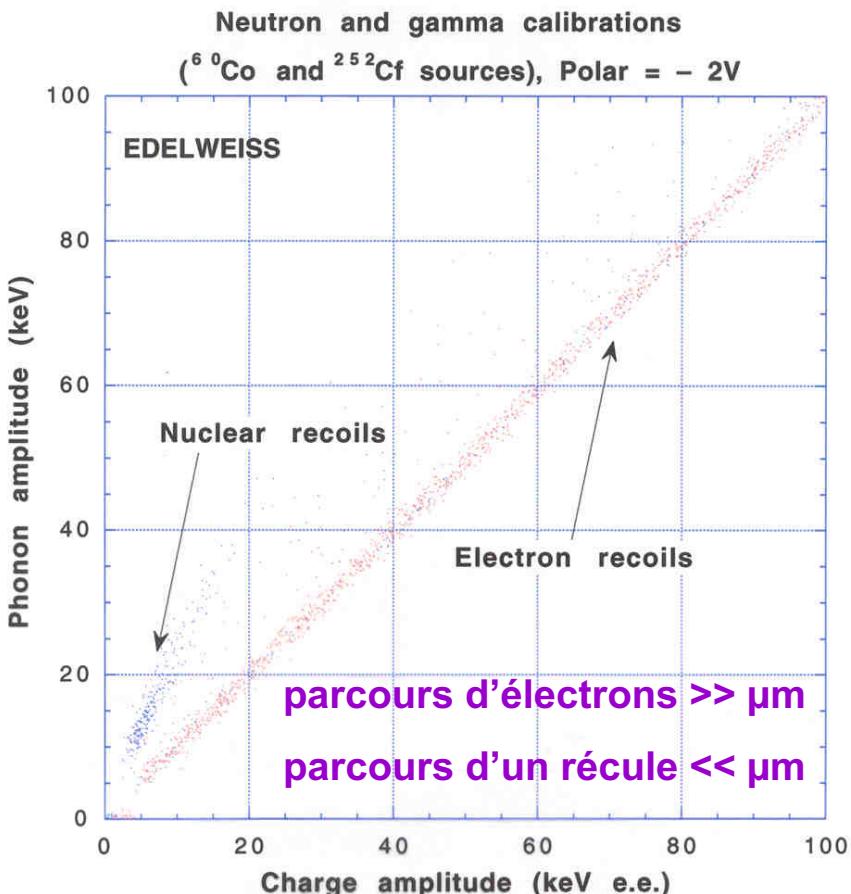




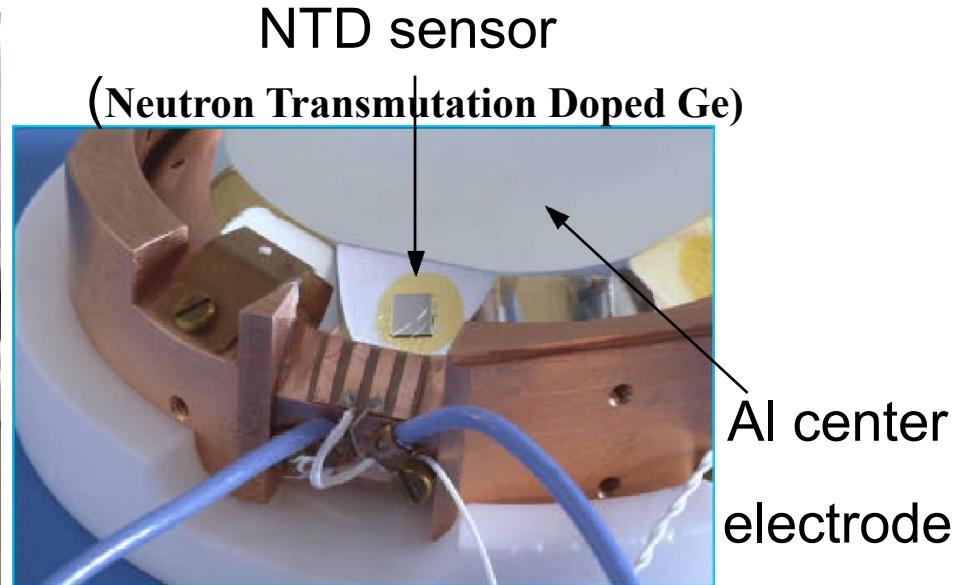
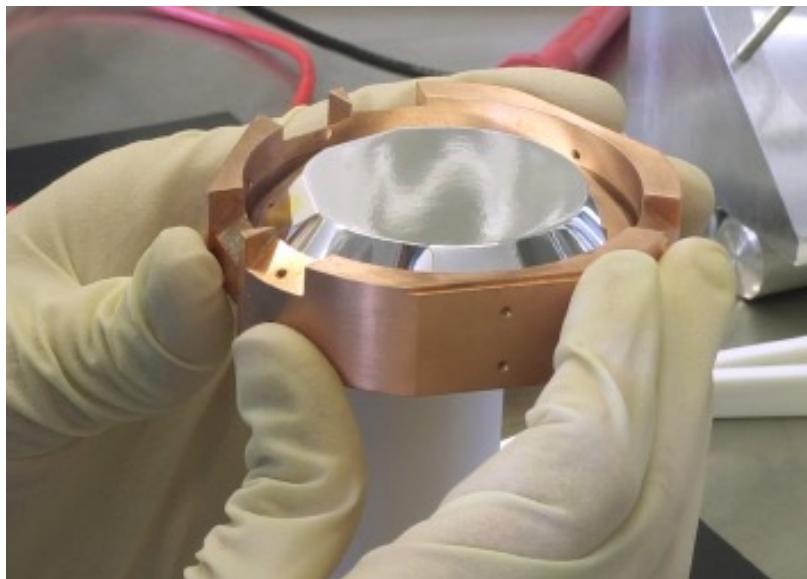
- **Ge crystals of up to 1Kg**
- **Very rare events about 1 event/Kg/year**
- **Recoil of some keV**
- **Heat changes of**
  - $\Delta T \approx \text{few mK} \Rightarrow \text{cryostat}({}^3\text{He}-{}^4\text{He})$
  - Operation temperature of 10 milli-Kelvin

# EDELWEISS

(*Expérience pour Déetecter Les Wimps en Site Souterrain*)



# Ge ionization – phonon detectors I



- bolometer mass: 320 g
- 100nm sputtered Al layer as electrode (center + guard ring)
- 60nm Ge(Si) amorphous layer below electrode
- NTD temperature sensor glued on sputtered gold pad on guard ring electrode
- electrical contacts/heat links via gold wire bonding ( $\varnothing=25\mu\text{m}$ )
  - operating temperature  $T=17.00 \pm 0.01\text{mK}$

# Ionisation&heat: pulses & signals

## Ge-NTD detector in EDELWEISS:

$E \sim 10 \text{ keV}_{\text{ee}}$

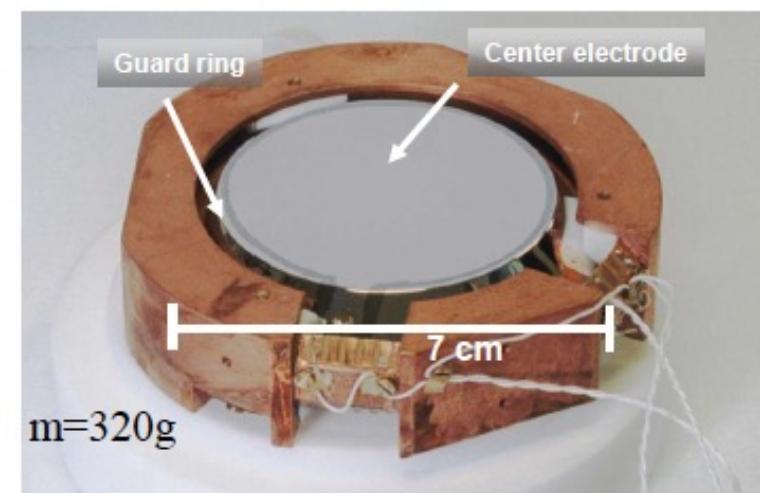
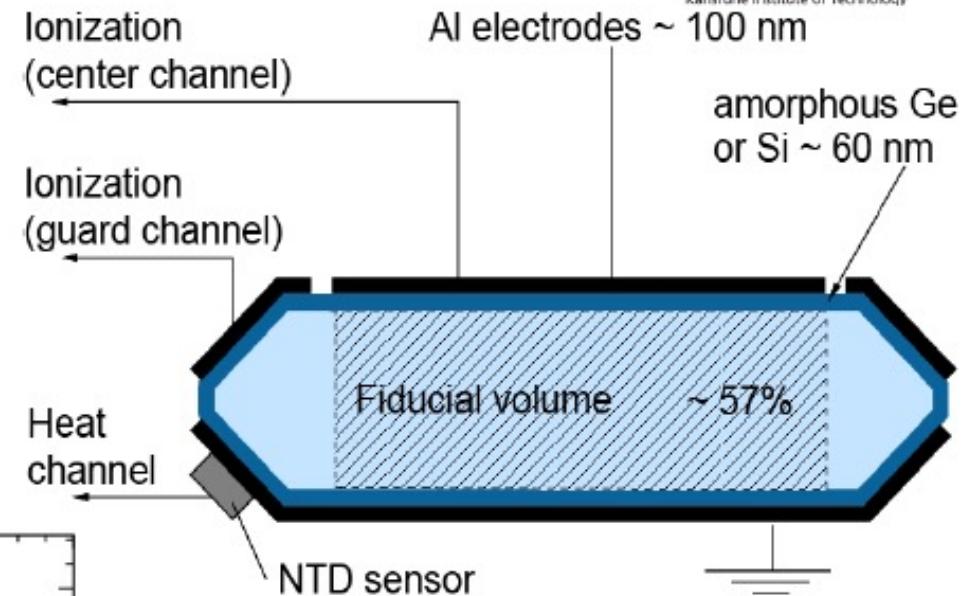
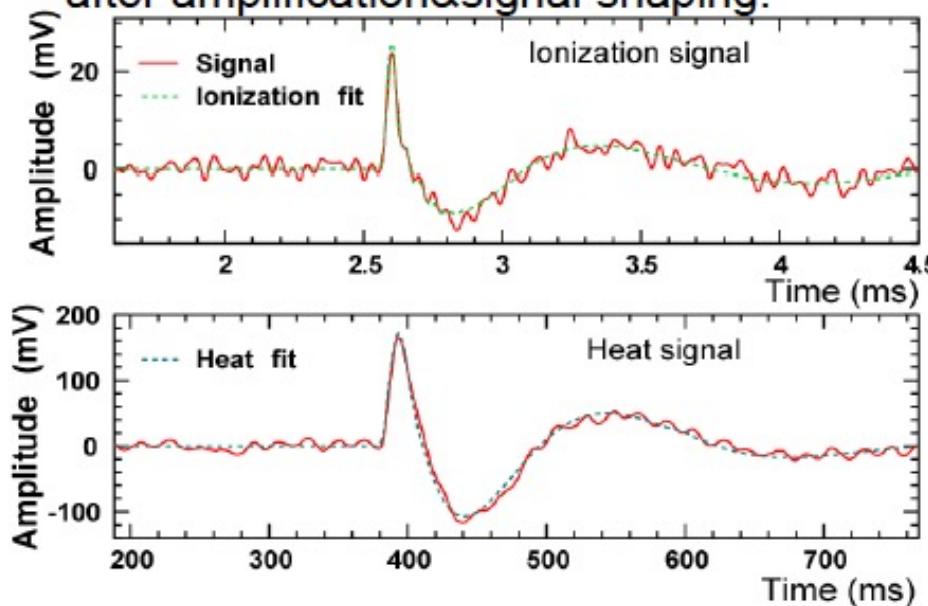
heat:  $\Delta T = 1.3 \mu\text{K}$ ;  $\Delta U = 1 \mu\text{V}$

$t_{\text{rise}} \sim 10 \mu\text{s}-10 \text{ ms}$ ;  $t_{\text{fall}} \sim 100 \text{ ms}$

ionisation:  $\Delta U = 0.5 \text{ mV}$

$t_{\text{rise}} \sim 100 \text{ ns}-1 \mu\text{s}$ ;  $t_{\text{fall}} \sim 100 \mu\text{s}$

## after amplification&signal shaping:



## ionization – phonon signal plane

$^{73}\text{Ge}(n,n'\gamma) 68.8 \text{ keV}$

13.3 keV

n/ $\gamma$  discrimination

> 99.9%

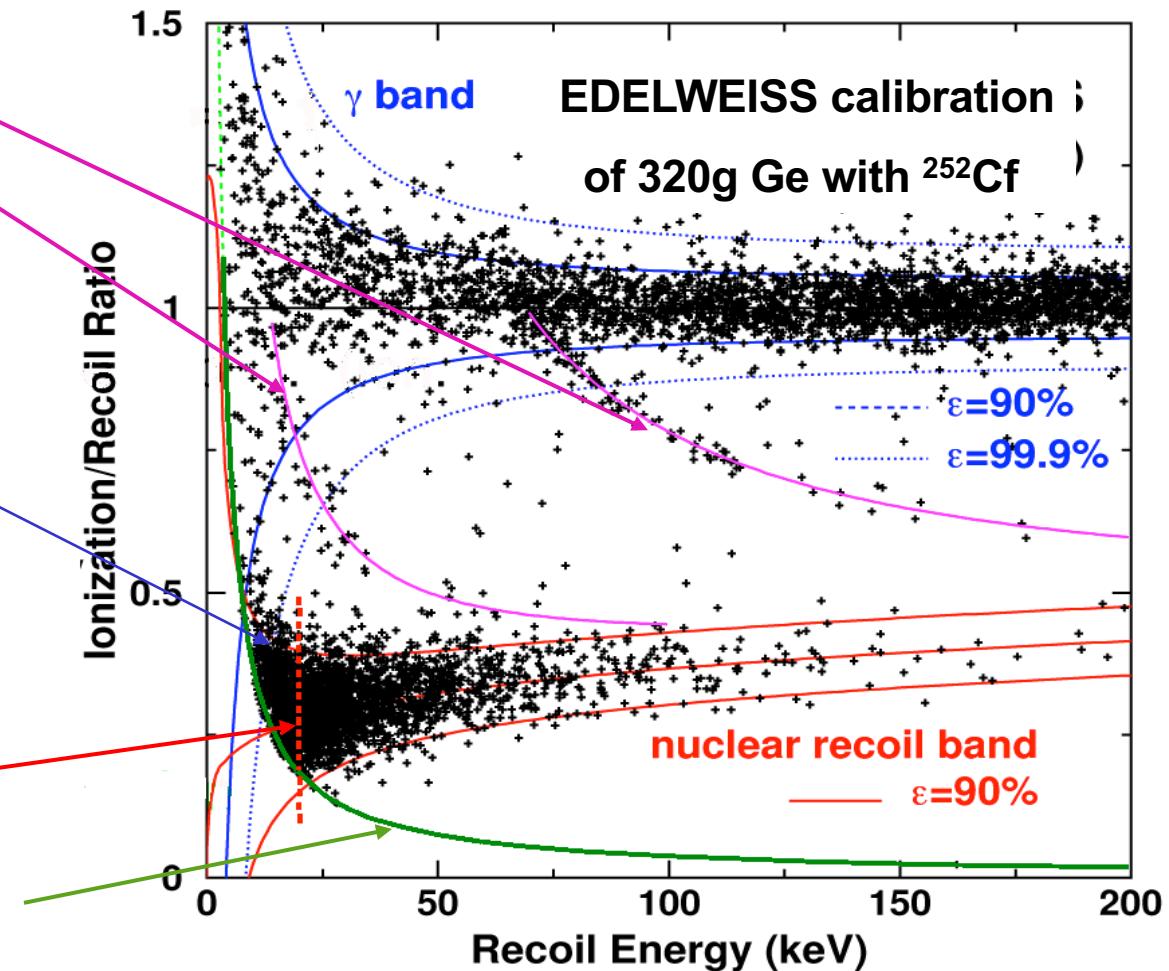
for  $E_r > 15 \text{ keV}$

Recoil threshold

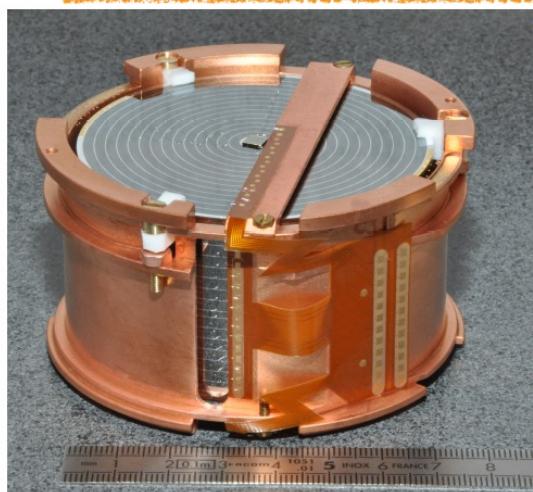
20 keV

Ionization threshold

3.7 keV



# Ex. of instrument : EDELWEISS-III



## 36 \* FID-800

- ◆ **Ge 820 g**
- ◆ High impedance Ge-NTD thermometer (neutron doped Ge crystals)
- ◆ 4 sets of Al electrodes for charge collection
  - Simultaneous measurement of **ionization & heat**
  - Background active rejection

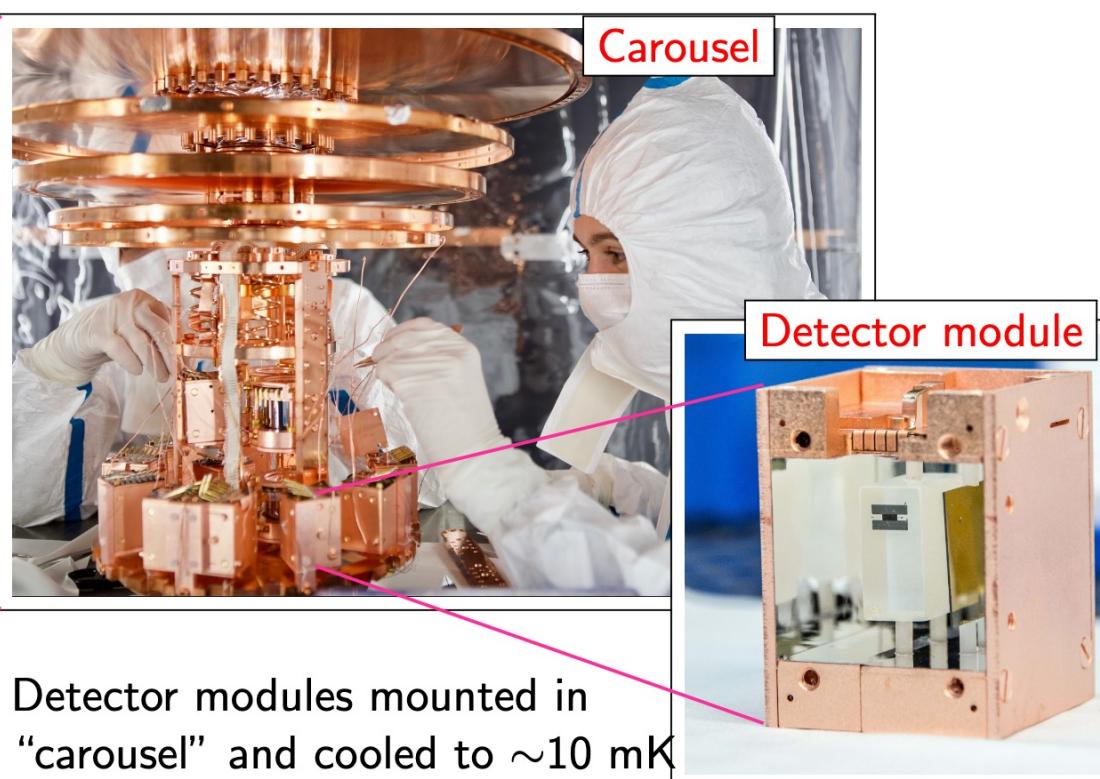
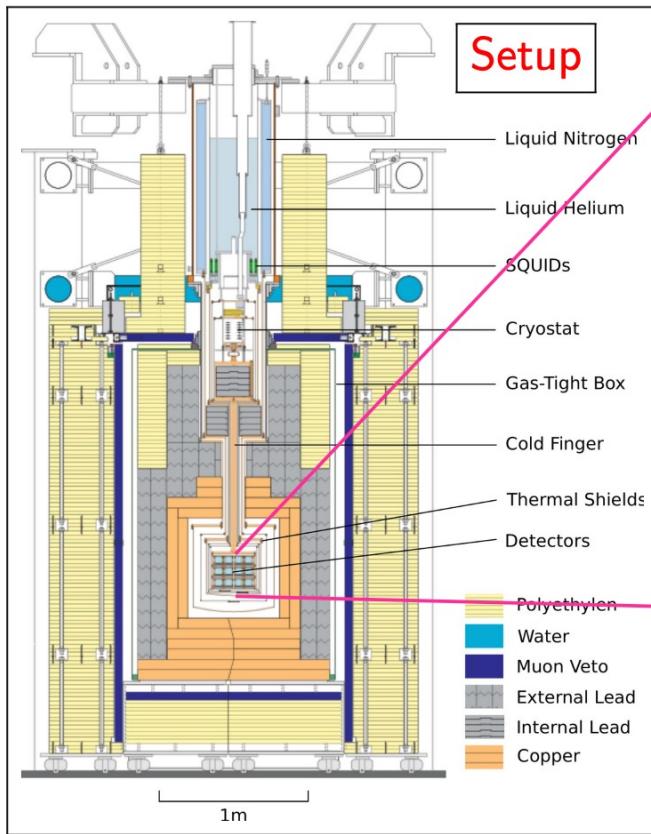


**Running 2013-2023**

- ◆ **10mK Cryostat** + 40 tons of shielding (PE + Pb) @ LSM
- ◆ **3000 coax. cables (6 km)**
- ◆ **350 Si-JFET transistors@ 120K**
- ◆ **36\*2 « Bolometers Boxes » @ 300K**

# The CRESST experiment

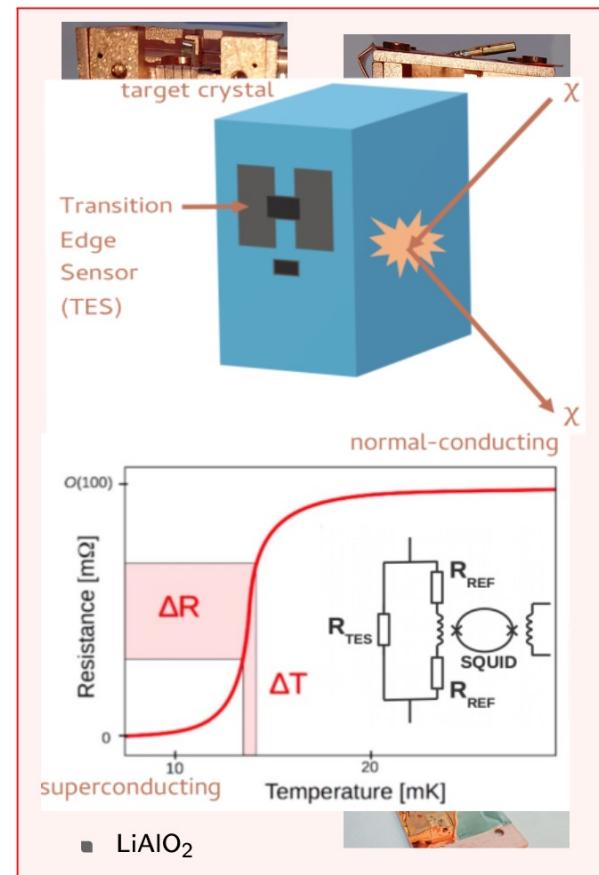
- Protected from backgrounds by layers of shielding (PE, Pb, Cu) and an active muon veto



- Detector modules mounted in “carousel” and cooled to  $\sim 10$  mK

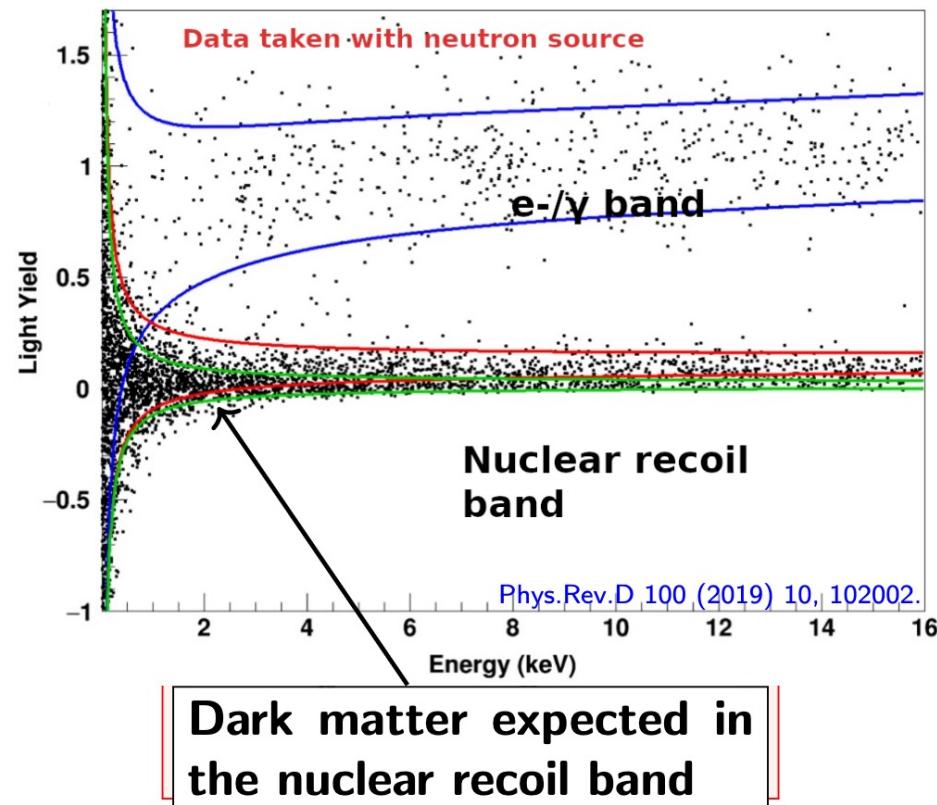
# CRESST-III detectors

- Cryogenic scintillating detectors
- Measure phonon and light
- CaWO<sub>4</sub> traditionally used as target material
- Capable of using range of target materials ( $\sim 2 \times 2 \times 1 \text{ cm}^3$ ): CaWO<sub>4</sub> (24 g), Al<sub>2</sub>O<sub>3</sub> (16 g), LiAlO<sub>2</sub> (10 g), Si (9 g)
- Thin light detector ( $2 \times 2 \times 0.04 \text{ cm}^3$ ): Si or silicon-on-sapphire (SOS)
- Sensors: W-TES directly evaporated on the crystals
- Particle interaction → energy deposition → temperature rise → resistance change read out by SQUID



# CRESST-III detectors

- Cryogenic scintillating detectors
- Measure phonon and light
- CaWO<sub>4</sub> traditionally used as target material
- **Capable of using range of target materials** ( $\sim 2 \times 2 \times 1 \text{ cm}^3$ ): CaWO<sub>4</sub> (24 g), Al<sub>2</sub>O<sub>3</sub> (16 g), LiAlO<sub>2</sub> (10 g), Si (9 g)
- Thin light detector ( $2 \times 2 \times 0.04 \text{ cm}^3$ ): Si or silicon-on-sapphire (SOS)
- Particle interaction → energy deposition → temperature rise → resistance change read out by SQUID
- Separation between e/γ background and nuclear recoil from two channel measurements



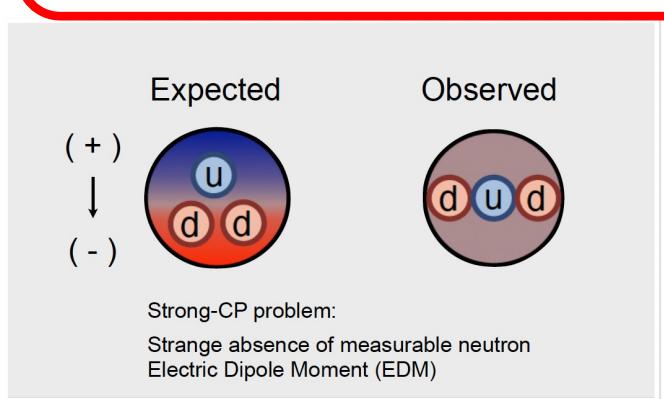
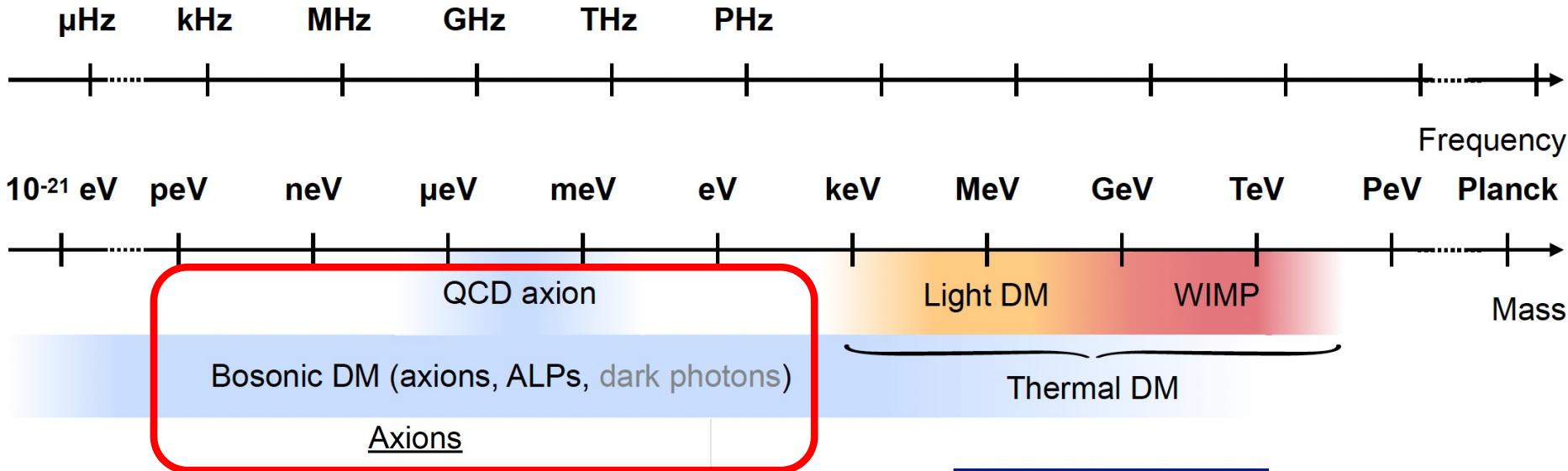
# Dark matter searches

Dark Matter and Axion Searches - Belina von Krosigk

8



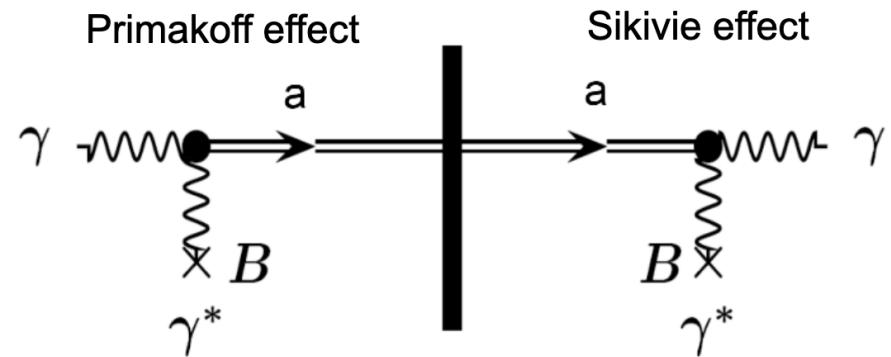
## Mass ranges of some beyond SM particles



Direct DM search experiments

# Axions and Axion-like particles (ALPs)

- Proposed as solution to strong CP problem
- Motivated by astrophysical observations:
  - Stellar evolution
  - TeV transparency
- Very weak interaction, good candidate for dark matter
- The main mechanism for detection of light weight axions is through its coupling to photons



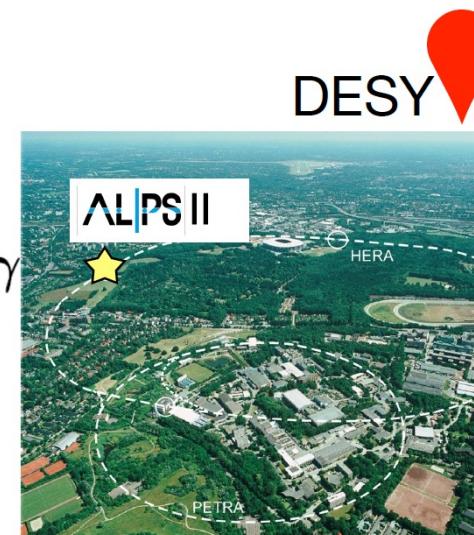
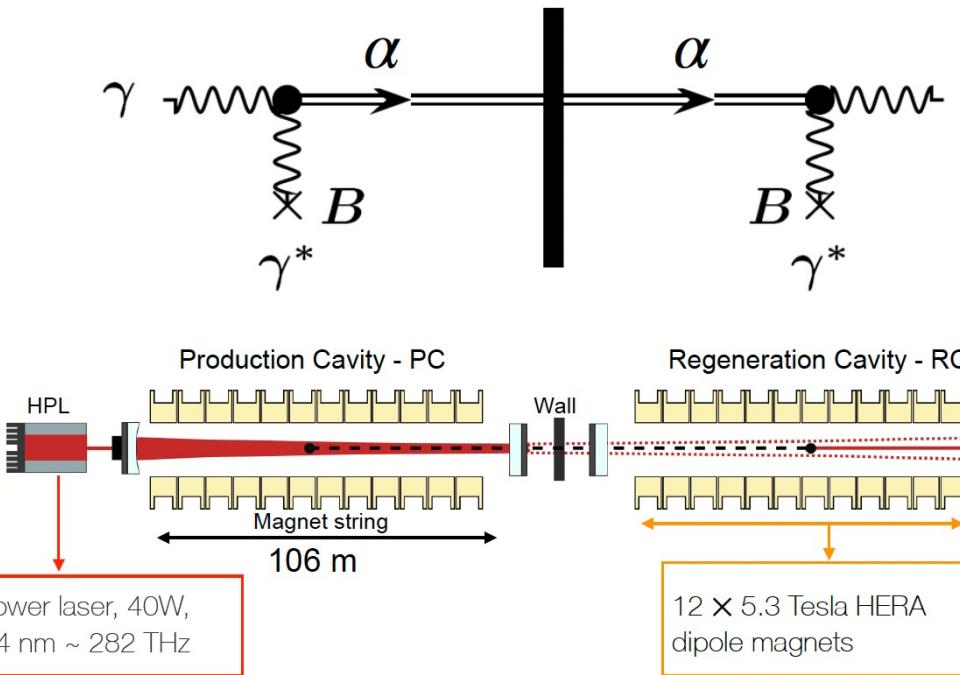
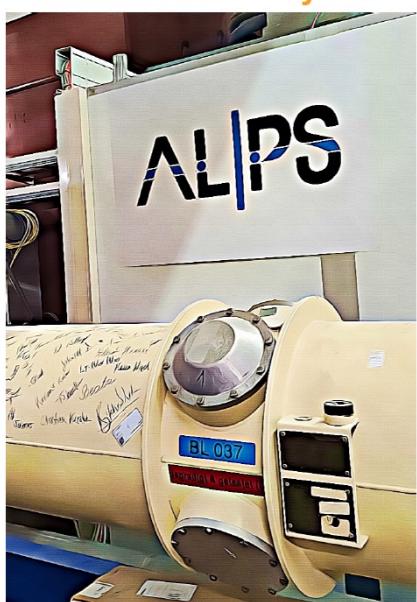
## Light Shining through a Wall (LSW)

Model independent approach,  
independent of dark matter paradigm

# Axions and Axion-like particles (ALPs)

## Any Light Particle Search II

The axion factory



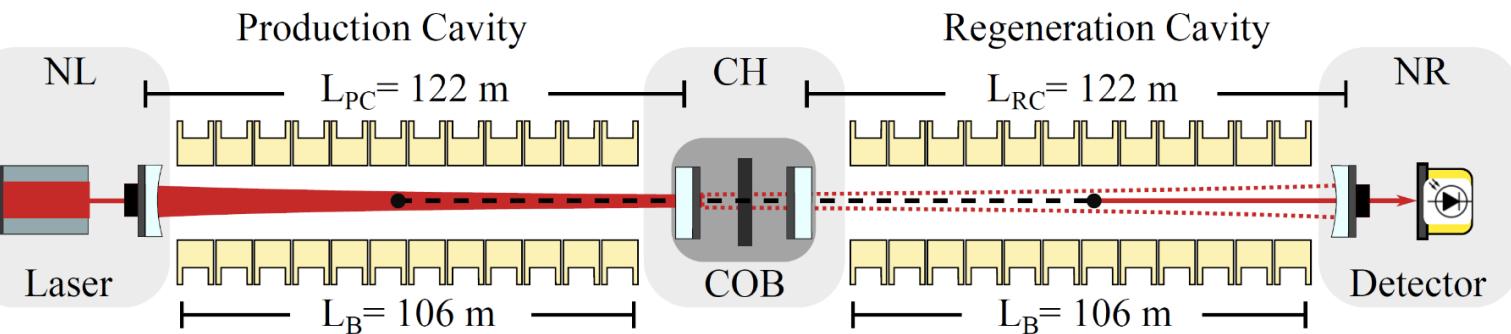
$\beta$ : power buildup R  
 $\eta$ : quantum efficiency

$$n_{\text{signal}} \approx \frac{1 \text{ photon}}{37 \text{ hours}} \cdot \left( \frac{P_{\text{PC}}}{150 \text{ kW}} \right) \left( \frac{\beta_{\text{RC}}}{10,000} \right) \left( \frac{\eta}{0.9} \right) \left( \frac{g_{a\gamma\gamma}}{2 \times 10^{-11} \text{ GeV}^{-1}} \right)^4 \left( \frac{B}{5.3 \text{ T}} \right)^4 \left( \frac{L}{106 \text{ m}} \right)$$

**DESY.** EPS 2023 | Axion and ALP search with the Any Light Particle Search II experiment at DESY | 24th Aug. 023 | Isabella Oceano

## Any Light Particle Search II (ALPS II)

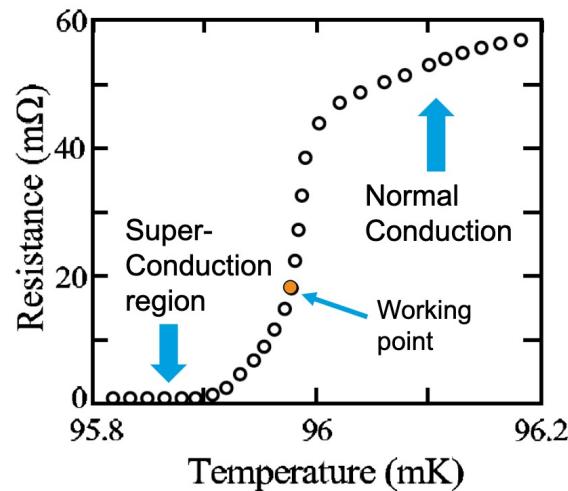
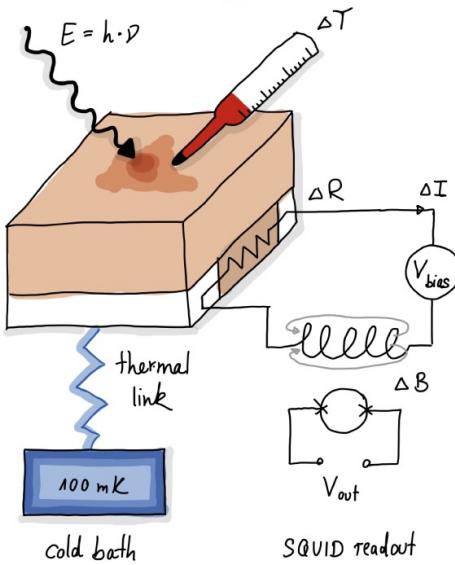
Initial Science Run started on 23.05.2023



**ALPS II** might produce a rate in the order of 1 reconverted photon per day

# TES Single Photon Detection

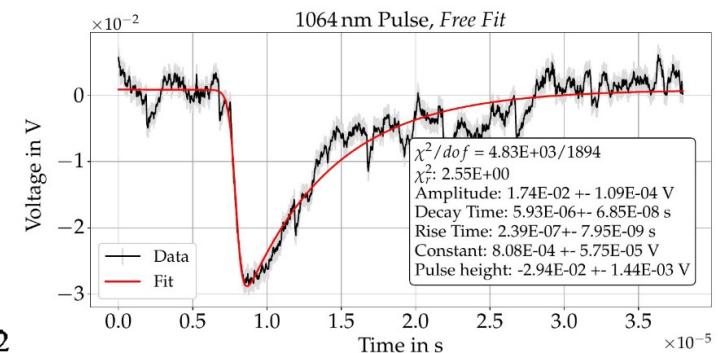
## Transition Edge Sensors



K. Irwin, G. Hilton, Transition-edge sensors, in: Cryogenic Particle Detection, Springer Berlin Heidelberg, Berlin, Heidelberg, 2005, pp. 63–150, [http://dx.doi.org/10.1007/10933596\\_3](http://dx.doi.org/10.1007/10933596_3).

- Cryogenic microcalorimeters
- Operated at superconducting transition temperature
- Read-out using Superconducting Quantum Interference Devices (SQUIDs)

- Incident photon leads to temperature increase
- Small temperature increase leads to large variation in resistance



Courtesy of Rikhav Shah

- Change in resistance is measured in changing current
- Signal is proportional to photon energy
- Energy resolution ≤ 10%
- DM signal expected to look like photon

## Requirements for ALPS II:

- Sensitivity to very low rates (1-2 photons a day)
- Low energy photon detection (1064nm equivalent to 1.16eV)
- Long term stability (~20 days)
- Low background rate: < 7.7 × 10<sup>-6</sup> cps
- ~ 1 photon (1064nm-like) every 2 days
- High detection efficiency

# TES as Dark Matter Detector

## Current Challenges

### TES @ ALPS II Status

- Optimized infrastructure (setup, analysis) for signals at 1064 nm → **1.165 eV**
- Limited knowledge about response to other wavelengths

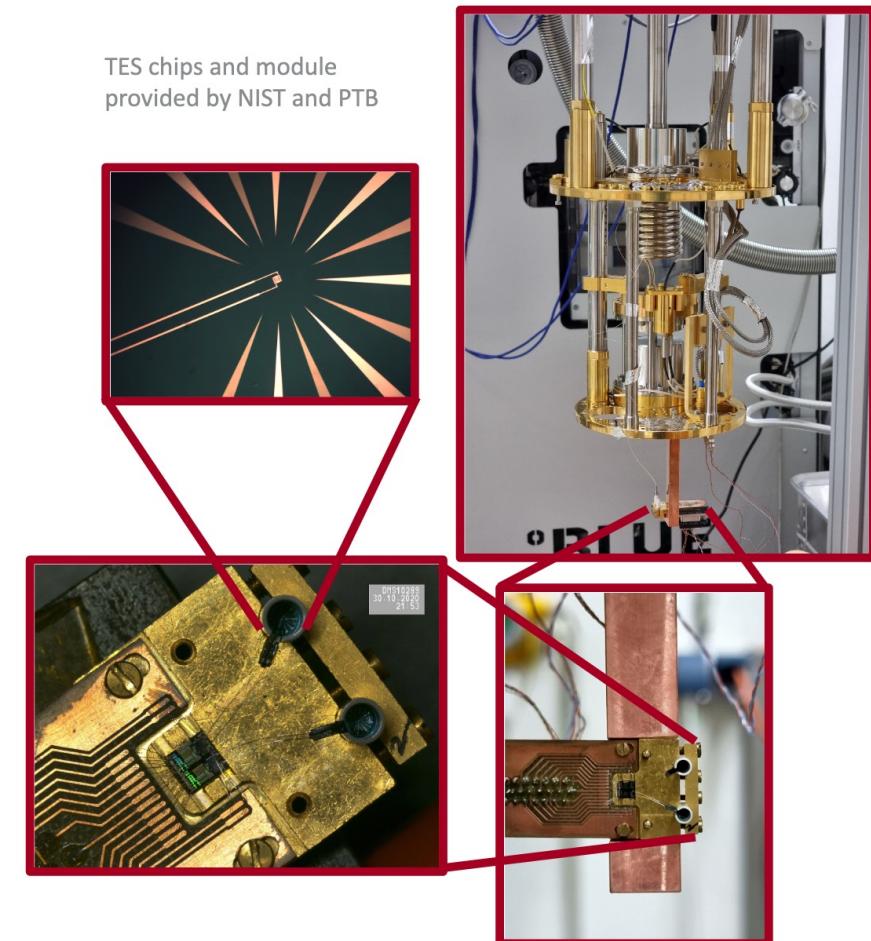
### Challenge/Goal

- Determine TES response at different (lower, sub – eV) energies
- Calibration measurements currently prepared using different wavelengths (880 nm – 2000 nm)

Low background (electronic noise, radioactivity, cosmic backgrounds)  
 → currently:  $6.9 \times 10^{-6}$  cps<sup>1</sup>  
 (intrinsic background for 1.165 eV signals)

- Further investigate intrinsic backgrounds
- Investigate alternative TES modules with lower noise background

TES chips and module provided by NIST and PTB



<sup>1</sup> R. Shah et al., PoS, EPS-HEP2021, 801 (2022)

# Résumé

- This was a very short and limited snapshot of some of the many ideas and developments on detectors.
- There are many more ideas for sensors and experiments
- Just to mention a few:
  - Kinematic Inductance Detector (KID)
  - Superconductor QUantum Interference Device (SQUID)
  - Nano-dots, nano wires, graphene.....
  - ...



